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TPS650932 SLVSE36 – AUGUST 2017

TPS650932 Simple and Flexible Wide Input Voltage PMIC for Computing

1 Device Overview

1.1 Features

- 5 Reconfigurable Voltage Regulators:
 - 4 Step-Down Controllers Using External Power MOSFETs:
 - V_{IN} Range from 4.5 V to 24 V
 - Continuous Output Current 20 A+ Using External Power MOSFETs
 - Frequency Selectable for Highest Efficiency or Ultra-Small Layout
 - 1 Step-Down Converter with Internal Power MOSFETs:
 - V_{IN} Range from 3 V to 3.6 V
 - Up to 2.7 A of Continuous Output Current
 - Differential Output-Voltage Sensing
 - Individual Enables and Power Goods for Flexible Sequence
 - Sleep-Mode Dynamic-Voltage Scaling and Decay to 0-V Feature
 - Ultra-Low Quiescent Current Mode (ULQ)
- 3 Fixed LDO Voltage Regulators:
 - LDO1: Fixed Output Voltage LDO for DDRx VTT $(V_{OUT} = VINLDO1S/2)$

1.2 Applications

- NVDC or Non-NVDC; 2, 3, or 4 Series-Cell Li Battery-Powered Products
- Tablet, Ultrabook, 2-in-1, and Notebook Computers

1.3 Description

 Up to 1 A of Continuous Output Current, DC+AC Accuracy ±5%, 2-A peak
 DC2: 2.2 V Always On Fixed Output Valta

Support &

Community

- LDO3: 3.3-V Always-On Fixed Output Voltage LDO, DC Accuracy ±1%, < 40 mA
 - 3.3-V Load Switch for EC_VCC or ADC Rail
- LDO5: 5-V Always-On Fixed Output Voltage LDO, DC Accuracy ±1%, < 100 mA
 - Automatic Switch to 5-V Regulator for Higher Efficiency
- 7 Power Good Comparators and Sequence Logic for External Voltage Regulators, Load Switches, or LDOs
- Power-Button With Programmable Response Time
- 3 General-Purpose Level Shifters
- Backup Battery and LDO Selector for RTC Domain
- Power-Source Monitoring for Adapter and 2
 Batteries
- Board Temperature Monitoring
- 1-Hz EC-Wake Clock Output
- Advanced System-Reset Control
- I²C Interface: Standard-Mode (100 kHz), Fast-Mode (400 kHz), Fast-Mode Plus (1000 kHz)
- Mobile PCs, All-In-Ones, Mobile Internet Devices, and Industrial Computing

The TPS650932 device is a single-chip solution, power-management IC (PMIC) designed specifically for the latest Intel Cannon Lake processors targeted for tablets, ultrabooks, and notebooks with NVDC or non-NVDC power architectures, using 2S, 3S, or 4S Lithium-Ion battery packs. The device can provide a power solution based on Intel Reference Designs.

Five highly-efficient step-down voltage regulators (VRs) and a sink-source LDO are used along with power-up sequence logic managing external load switches to provide the proper power rails, sequencing, and protection—including DDR3 and DDR4 memory power. The regulators support dynamic voltage scaling (DVS) for maximum efficiency including connected standby. The high-frequency voltage regulators use small inductors and capacitors to achieve a small solution size. Output power is adjustable on the controllers to scale across processor skews and applications. An I²C interface allows simple control by the embedded controller (EC).

The device is available in a 7×7 nFBGA package (ZAJ). The ZAJ package can be used in Type-4 PCB boards for the smallest area implementation.

An IMPORTANT NOTICE at the end of this data sheet addresses availability, warranty, changes, use in safety-critical applications, intellectual property matters and other important disclaimers. PRODUCTION DATA.

SLVSE36-AUGUST 2017

TEXAS INSTRUMENTS

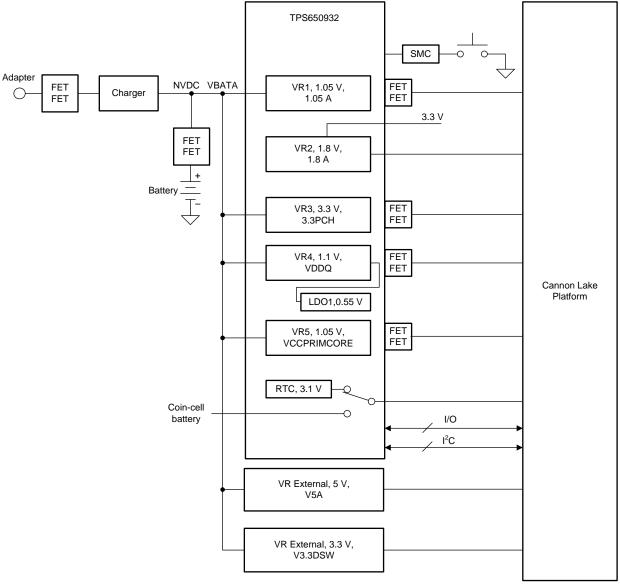
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Device Information⁽¹⁾

PART NUMBER	PACKAGE	BODY SIZE (NOM)	
TPS650932	nFBGA (168)	7.00 mm x 7.00 mm	

(1) For all available packages, see the orderable addendum at the end of the data sheet.

1.4 Simplified System Diagram



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Figure 1-1. Simplified System Diagram

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XAS

STRUMENTS

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2 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

DATE	REVISION	NOTES
August 2017	*	Initial release.
•		

3 Voltage Regulator and Power-Good Comparator Logic Assignment

Table 3-1 lists the voltage regulator and power-good comparator logic assignments for Cannon Lake Platforms.

	PREM (SPLIT LOW VO	POWER-GOOD	
REGULATOR OR COMPARATOR	Cannon Lake PLATFORM POWER-SYSTEM VOLTAGE RAIL	OUTPUT VOLTAGE (V _O) OR COMPARATOR INPUT	OUTPUT SETTING ⁽¹⁾
VR1	V1.05A	1.05 V	PP
VR2	V1.8A	1.8 V	PP
VR3	3.3PCH	3.3 V	PP
VR4	VDDQ	1.2 V, 1.35 V, 1.1 V	OD
VR5	VCCPRIMCORE	1.05 V	PP
LDO1	VTT	1/2 of VDDQ	—
External regulator A	VCCIO (optional)	0.95 V	_
External regulator B	V5A_DS3	_	_
Power-good comparator logic A	V3.3A_DSW enable Sense external-load switch	3.3 V	PP
Power-good comparator logic B	V1.8U_2.5U enable Sense external-load switch	1.8 V	PP
Power-good comparator logic C	V5A_DS3 enable Sense external regulator B	5 V	PP
Power-good comparator logic D	VCCIO enable Sense external load switch	Level mode 0.85 V	PP
Power-good comparator logic E	V3.3S sense external-load switch	3.3 V	PP
Power-good comparator logic F	V1.8S sense external-load switch	Output of VR2	PP
Power-good comparator logic G	V1.05S sense external-load switch	Output of VR1	OD
Power-good comparator logic H	Unavailable Used in level-shifter mode	Window mode 1.2V	OD

(1) PP = Push pull, OD = Open drain

4



4 Pin Configuration and Functions

Figure 4-1 shows the 168-pin ZAJ New Fine-Pitch Ball-Grid Array package.

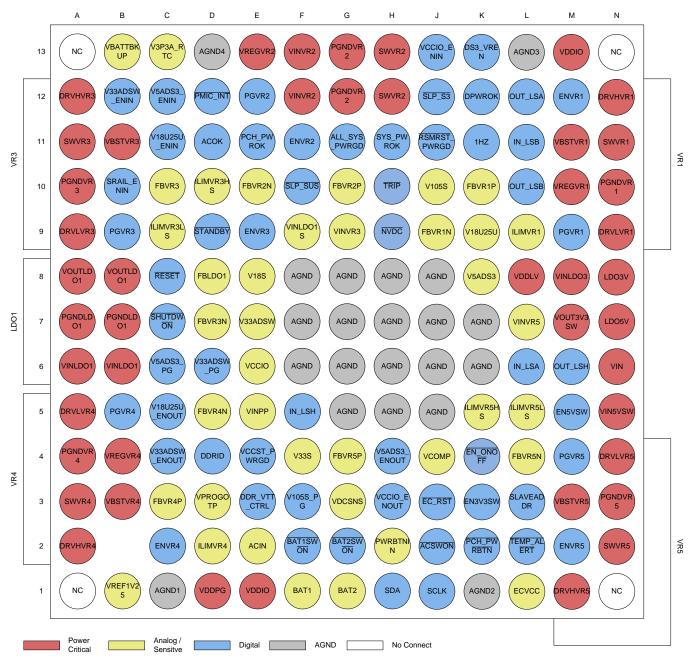


Figure 4-1. 168-Pin ZAJ nFBGA (Top View)



4.1 Pin Attributes

Pin Attributes—ZAJ Package

NO. NAME No A1 NC NC No No connect pin. Solder this pin to the PCB for mechanical strength. A2 DRVHVR4 O VR VR4 high-side gate-drive output for the external-power FET A3 SWUR4 I VR VR4 write-in-dee connection A4 PCNDVR4 O VR VR4 town ground A5 DRVLVR4 O VR VR4 town suppy A7 PGNDLDO1 I VR LDO1 power ground A8 VOUTLDO1 O VR LDO1 output voltage. The voltage of this pin equals ½: x VINLDO1SNS. A9 DRVLVR3 O VR VR3 power ground A11 SWVR3 I VR VR3 power ground A12 DRVHVR3 O VR VR3 power ground A11 SWVR3 I VR VR3 power ground A12 DRVHVR3 O VR VR3 power ground A11 SWVR3 I VR VR4 bottine-supptin to the PCB for mechanical strength.		PIN		PIN I/O TYPE ⁽¹⁾			DESCRIPTION	
A2 DRVHVP4 O VR VR4 high-side gate-drive output for the external-power FET A3 SWVR4 I VR VR4 switch-node connection A4 PCNDVF4 O VR VR4 gover ground A5 DRVLVF4 O VR VR4 Low side gate drive output for the external-power FET A6 VINLDO1 I VR LDO1 output voltage. The voltage of this pin equals ½ x VINLDO1SNS. A7 PGNDUR3 O VR VR2 loop output voltage. The voltage of this pin equals ½ x VINLDO1SNS. A9 DRVLVR3 O VR VR3 low side gate drive output for the external-power FET A10 PGNDVR3 - VR VR3 by switch-node connection Atternal-power FET A11 SWVR3 I VR VR3 switch-node connection For mechanical strength. B1 VREF1V25 O AS Decoupling capacitor connection for the internal voltage reference B3 VSTVR4 I VR VR4 bowstrap pin For weak bowstrap pin B4 VREGVR4 I VR LDO1	NO.	NAME	1/O	ITPE	DESCRIPTION			
A3 SWVR4 I VR VR4 switch-node connection A4 PGNDVR4 - VR VR4 power ground A5 DRVLVR4 O V/R VR4 power ground A5 DRVLD01 I VR VR4 Low side gate drive output for the external-power FET A6 VINLD01 I VR LD01 output voltage. The voltage of this pin equals ½ × VINLD01SNS. A9 DRVLVR3 O VR VR4 Low side gate drive output for the external-power FET A10 PGNDVDR3 - VR VR3 power ground A11 SWVR3 I VR VR3 switch-node connection A12 DRVLVR3 O VR VR3 switch-node connection A13 NC NC - No connect pin. Solder this pin to the PCB for mechanical strength. B1 VREF1V25 O AS Decoupling capacitor connection for the internal voltage reference B3 VBSTVR4 I VR VR4 40 volve-supply plut. This pin is an open-drain output. B4 VREGVR4 I VR VR4 5V drive-supply plut. This pin is a push-pull output. B5	A1	NC	NC		No connect pin. Solder this pin to the PCB for mechanical strength.			
A4 PGNDVR4 — VR VR4 power ground A5 DRVLVR4 O VR VVR4 Low side gate drive output for the external-power FET A6 VINLDO1 I VR LDO1 input supply A7 PGNDLDO1 — VR LDO1 power ground A8 VOUTLDO1 O VR LDO1 output voitage. The voitage of this pin equals ½ × VINLDO1SNS. A9 DRVLVR3 O VR VR3 low side gate drive output for the external-power FET A10 PGNDVR3 — VR VR3 switch-node connection A11 SWKP3 I VR VR3 beweir ground A12 DRVHVR3 O VR VR3 beweir ground A11 SWKP3 I VR VR3 beweir ground B1 VREF1V25 O AS Decoupling capacitor connection for the internal voitage reference B3 NC NC VR VR4 bootstrap pin VR4 bootstrap pin B4 VREGVR4 I VR VR4 power-good comparator output. This pin is an open-drain o	A2	DRVHVR4	0	VR	VR4 high-side gate-drive output for the external-power FET			
A5 DRVLVR4 O VR VR4 Low side gate drive output for the external-power FET A6 VINLDO1 I VR LOO1 input supply A7 PGNDLDO1 - VR LOO1 output voltage. The voltage of this pin equals ½ × VINLDO1SNS. A8 VOUTLDO1 O VR LOO1 output voltage. The voltage of this pin equals ½ × VINLDO1SNS. A9 DRVLVR3 O VR VR3 power ground A11 SWVR3 - VR VR3 power ground A12 DRVLVR3 O VR VR3 power ground A12 DRVLVR3 O VR VR3 power ground A12 DRVHVR3 O VR VR3 bigh-side gate-drive output for the external-power FET A13 NC NC - As connect pin. Solder this pin to the PCB for mechanical strength. B1 VREF1V25 O AS Decouping capacitor connection for the internal voltage reference B3 VBSTVR4 I VR VR4 5/V drive-supply input. This pin is shorted on the PCB with LDO5V and is shared with UD5V B4	A3	SWVR4	Ι	VR	VR4 switch-node connection			
A6 VINLDO1 I VR LDO1 input supply A7 PGNDLDO1 - VR LDO1 output voltage. The voltage of this pin equals ½ × VINLDO1SNS. A9 DRVLVR3 O VR VR3 cov side gate drive output for the external-power FET A10 PGNDVR3 - VR VR3 switch-node connection A11 SWVR3 I VR VR3 switch-node connection A12 DRVHVR3 O VR VR3 switch-node connection A13 NC NC - No connect pin. Solder this pin to the PCB for mechanical strength. B1 VREGVR4 I VR VR4 5-V drive-supply input. This pin is shorted on the PCB with LDO5V and is shared with VR3. B5 PGVR4 O D VR4 5-V drive-supply input. This pin is an open-drain output. B6 VINLDO1 I VR LDO1 output voltage. The voltage of this pin equals ½ × VINLDO1SNS. B9 PGVR3 O D VR4 bower-good comparator output. This pin is a push-pull output. B10 SRAIL_ENIN I D Enable for power-good comparators A, which monitors V33ADSW B11 VBSTVR3 I <t< td=""><td>A4</td><td>PGNDVR4</td><td>_</td><td>VR</td><td>VR4 power ground</td></t<>	A4	PGNDVR4	_	VR	VR4 power ground			
A7 PGNDLDO1 — VR LDO1 power ground A8 VOUTLD01 O VR LDO1 output voltage. The voltage of this pin equals ½ × VINLDO1SNS. A9 DRVLVR3 O VR VR3 Low side gate drive output for the external-power FET A10 PGNDVR3 I VR VR3 power ground A11 SWVR3 I VR VR3 power ground A12 DRVHVR3 O VR VR3 switch-node connection A11 SWVR3 I VR VR3 box size gate-drive output for the external-power FET A13 NC NC — Na connect pin. Solder this pin to the PCB for mechanical strength. B1 VREF1V25 O AS Decoupling capacitor connection for the internal voltage reference B3 VBSTVR4 I VR VR4 Sv drive-suppi input. This pin is shorted on the PCB with LDO5V and is shared with VR3. B4 VREGVR4 I VR LDO1 input supply B7 PGNDLDO1 — VR LDO1 input supply B7 PGNDLD01 O VR LDO1 output voltage. The voltage of this pin equals ½ × VINLDO1SNS.	A5	DRVLVR4	0	VR	VR4 Low side gate drive output for the external-power FET			
A8 VOUTLDO1 O VR LDO1 output voltage. The voltage of this pin equals ½ × VINLDO1SNS. A9 DRVLVR3 O VR VR3 power ground A10 PGNDVR3 — VR VR3 power ground A11 SWVR3 I VR VR3 power ground A12 DRVHVR3 O VR VR3 switch-node connection A13 NC NC — No connect pin. Solder this pin to the PC8 for mechanical strength. B1 VREF1V25 O AS Decoupling capacitor connection for the internal voltage reference B3 VBSTVR4 I VR VR4 bootstrap pin B4 VREGVR4 I VR VR4 bootstrap pin B5 PGVR4 O D VR4 power-good comparator output. This pin is an open-drain output. B6 VINLDO1 I VR LDO1 input supply B7 PGNR4 O D VR8 power-good comparator output. This pin is a push-pull output. B1 VSETKPR3 I VR LDO1 input supply D	A6	VINLDO1	Ι	VR	LDO1 input supply			
A9 DRVLVR3 O VR VR3 Low side gate drive output for the external-power FET A10 PGNDVR3 VR VR3 power ground A11 SWVR3 I VR VR3 switch-node connection A11 SWVR3 I VR VR3 switch-node connection A12 DRVHVR3 O VR VR3 switch-node connection for the external-power FET A13 NC NC - No connect pin. Solder this pin to the PCB for mechanical strength. B1 VREFIV25 O AS Decoupling capacitor connection for the internal voltage reference B3 VBSTVR4 I VR VR4 5-V drive-supply input. This pin is shorted on the PCB with LDOSV and is shared with VR3. B5 PGVR4 O D VR4 power-good comparator output. This pin is an open-drain output. B6 VINLDO1 I VR LDO1 input supply B7 PGNDLDO1 - VR LDO1 output voltage. The voltage of this pin equals ½ × VINLDO1SNS. B9 PGVR3 O D VR3 power-good comparator output. This pin is a push-pull ou	A7	PGNDLDO1	_	VR	LDO1 power ground			
A10 PGNDVR3 — VR VR3 power ground A11 SWVR3 I VR VR3 witch-node connection A12 DRVHVR3 O VR VR3 high-side gate-drive output for the external-power FET A13 NC NC NC — No connect pin. Solder this pin to the PCB for mechanical strength. B1 VREF1V25 O AS Decoupling capacitor connection for the internal voltage reference B3 VBSTVR4 I VR VR4 bootstrap pin B4 VREGVR4 I VR VR4 bover-good comparator output. This pin is an open-drain output. B6 VINLDO1 I VR LDO1 input supply B7 B7 PGNDLD01 - VR LDO1 output voltage. The voltage of this pin equals ½ × VINLDO1SNS. B9 PGVR3 O D VR3 power-good comparator output. This pin is a push-pull output. B11 VBSTVR3 I VR LDO1 output voltage. The voltage of this pin equals ½ × VINLDO1SNS. B12 V33ADSW ENIN I D Enable for power-good comparators E, F and G, which monitor the S raits: V33S, V185, and V10SS B13	A8	VOUTLDO1	0	VR	LDO1 output voltage. The voltage of this pin equals $\frac{1}{2} \times \text{VINLDO1SNS}$.			
A11 SWVR3 I VR VR3 switch-node connection A12 DRVHVR3 O VR VR3 high-side gate-drive output for the external-power FET A13 NC NC — No connect pin. Solder this pin to the PCB for mechanical strength. B1 VREF1V25 O AS Decoupling capacitor connection for the internal voltage reference B3 VBSTVR4 I VR VR4 bootstrap pin B4 VREGVR4 I VR VR4 bower-good comparator output. This pin is an open-drain output. B6 VINLDO1 I VR LDO1 input supply B7 PGNDLDO1 — VR LDO1 output voltage. The voltage of this pin equals ½ × VINLDO1SNS. B9 PGVR3 O D VR3 power-good comparator output. This pin is a push-pull output. B10 SRAIL_ENIN I D Enable for power-good comparators E, F and G, which monitor the S rails: V33S, V18S, and V10SS B11 VBSTVR3 I VR VR3 bootstrap pin B12 V33ADSW_ENIN I D Enable for power-good comparator A, which monitors V33ADSW B13 VBATTBKUP I <td< td=""><td>A9</td><td>DRVLVR3</td><td>0</td><td>VR</td><td>VR3 Low side gate drive output for the external-power FET</td></td<>	A9	DRVLVR3	0	VR	VR3 Low side gate drive output for the external-power FET			
A12 DRVHVR3 O VR VR3 high-side gate-drive output for the external-power FET A13 NC NC NC Nc connect pin. Solder this pin to the PCB for mechanical strength. B1 VREF1V25 O AS Decoupling capacitor connection for the internal voltage reference B3 VBSTVR4 I VR VR4 5-V drive-supply input. This pin is shorted on the PCB with LDOSV and is shared with VR3. B4 VREGVR4 I VR VR4 5-V drive-supply input. This pin is shorted on the PCB with LDOSV and is shared with VR3. B5 PGVR4 O VR LDO1 input supply B6 VINLDO1 I VR LDO1 output voltage. The voltage of this pin equals ½ × VINLDO1SNS. B9 PGVR3 O VR3 power-good comparator output. This pin is a push-pull output. B10 SRAIL_ENIN I D Enable for power-good comparator A, which monitors V33ADSW B11 VBSTVR3 I VR VR4 bosttrap pin B12 V33ADSW_ENIN I D Enable for power-good comparator A, which monitors V33ADSW B13 VBATTBKUP I AS RTC backup batteny-supply connection	A10	PGNDVR3		VR	VR3 power ground			
A13 NC NC — No connect pin. Solder this pin to the PCB for mechanical strength. B1 VREF1V25 O AS Decoupling capacitor connection for the internal voltage reference B3 VBSTVR4 I VR VR4 bootstrap pin B4 VREGVR4 I VR VR4 5-V drive-supply input. This pin is shorted on the PCB with LDOSV and is shared with VR3. B5 PGVR4 O D VR4 power-good comparator output. This pin is an open-drain output. B6 VINLDO1 I VR LDO1 input supply B7 PGNDLD01 - VR LDO1 output voltage. The voltage of this pin equals ½ × VINLDO1SNS. B9 PGVR3 O D VR3 power-good comparator output. This pin is a push-pull output. B10 SRAIL_ENIN I D Enable for power-good comparators E, F and G, which monitor the S rails: V33S, V18S, and V105S B13 VBATTBKUP I AS RTC backup battery-supply connection C1 AGND1 - A Analog ground 1. The this pin directly to the ground plane. C2 ENVR4 I D VR4 positive-feedback remote sense. Connect this pin to the output voltage of	A11	SWVR3	Ι	VR	VR3 switch-node connection			
B1 VREF1V25 O AS Decoupling capacitor connection for the internal voltage reference B3 VBSTVR4 I VR VR4 bottstrap pin B4 VREGVR4 I VR VR4 5-V drive-supply input. This pin is shorted on the PCB with LDO5V and is shared with VR3. B5 PGVR4 O D VR4 power-good comparator output. This pin is an open-drain output. B6 VINLD01 I VR LD01 input supply B7 PGNDLD01 VR LD01 output voltage. The voltage of this pin equals ½ × VINLD01SNS. B9 PGVR3 O D VR3 power-good comparator output. This pin is a push-pull output. B10 SRAIL_ENIN I D Enable for power-good comparators E, F and G, which monitor the S rails: V33S, V18S, and V16SS B11 VBSTVR3 I VR VR3 bootstrap pin B12 V33ADSW_ENIN I D Enable for power-good comparator A, which monitors V33ADSW B13 VBATTBKUP I AS RTC backup battery-supply connection C1 AGN1 - A Analog ground 1. Tie this pin directly to the ground plane. C2 EN	A12	DRVHVR3	0	VR	VR3 high-side gate-drive output for the external-power FET			
B3 VBSTVR4 I VR VR4 boxtstrap pin B4 VREGVR4 I VR VR4 5-V drive-supply input. This pin is shorted on the PCB with LDO5V and is shared with VR3. B5 PGVR4 O D VR4 power-good comparator output. This pin is an open-drain output. B6 VINLDO1 I VR LDO1 input supply B7 PGNDLDO1 — VR LDO1 output voltage. The voltage of this pin equals ½ × VINLDO1SNS. B9 PGVR3 O D VR3 power-good comparator output. This pin is a push-pull output. B10 SRAIL_ENIN I D Enable for power-good comparator output. This pin is a push-pull output. B11 VBSTVR3 I VR VR3 bootstrap pin B12 V33ADSW_ENIN I D Enable for power-good comparator A, which monitors V33ADSW B13 VBATTBKUP I A Analog ground 1. Tie this pin directly to the ground plane. C2 ENVR4 I D VR4 enable C3 G3 FBVR4P I A Analog ground 1. Tie this pin directly to the ground plane. C5 V18U2SU_ENOUT O <td< td=""><td>A13</td><td>NC</td><td>NC</td><td>—</td><td>No connect pin. Solder this pin to the PCB for mechanical strength.</td></td<>	A13	NC	NC	—	No connect pin. Solder this pin to the PCB for mechanical strength.			
B4 VREGVR4 I VR VR4 5-V drive-supply input. This pin is shorted on the PCB with LDOSV and is shared with VR3. B5 PGVR4 O D VR4 power-good comparator output. This pin is an open-drain output. B6 VINLDD1 I VR LDO1 input supply B7 PGNDLD01 - VR LDO1 input supply B7 PGNDLD01 - VR LDO1 input supply B8 VOUTLD01 O VR LDO1 output voltage. The voltage of this pin equals ½ × VINLD01SNS. B9 PGVR3 O D VR8 power-good comparator output. This pin is a push-pull output. B10 SRAIL_ENIN I D Enable for power-good comparator A, which monitors V33ADSW B11 VBSTVR3 I VR VR3 bootstrap pin B12 V33ADSW_ENIN I D Enable for power-good comparator A, which monitors V33ADSW B13 VBATTBKUP I AS RTC backup battery-supply connection C1 AGND1 - A Analog ground 1. Tie this pin directly to the ground plane.	B1	VREF1V25	0	AS	Decoupling capacitor connection for the internal voltage reference			
D4 VRLSUM I VR with VR3. B5 PGVR4 O D VR4 power-good comparator output. This pin is an open-drain output. B6 VINLDO1 I VR LDO1 input supply B7 PGNDLDO1 - VR LDO1 power ground B8 VOUTLDO1 O VR LDO1 output voltage. The voltage of this pin equals ½ x VINLDO1SNS. B9 PGVR3 O D VR3 power-good comparator output. This pin is a push-pull output. B10 SRAIL_ENIN I D Enable for power-good comparators E, F and G, which monitor the S rails: V33S, V18S, and V105S B11 VBSTVR3 I VR VR3 bootstrap pin B12 V33ADSW_ENIN I D Enable for power-good comparator A, which monitors V33ADSW B13 VBATTBKUP I AS RTC backup battery-supply connection C1 AGND1 - A Analog ground 1. Tie this pin directly to the ground plane. C2 ENVR4 I D VR4 enable VR4 positive-feedback remote sense. Connect this pin to the output voltage of VR4 at the output-load capacitor. C4 V33A_DSW_ENOUT	B3	VBSTVR4	Ι	VR				
B6 VINLDO1 I VR LDO1 input supply B7 PGNDLDO1 VR LDO1 power ground B8 VOUTLDO1 O VR LDO1 output voltage. The voltage of this pin equals ½ × VINLDO1SNS. B9 PGVR3 O D VR3 power-good comparator output. This pin is a push-pull output. B10 SRAIL_ENIN I D Enable for power-good comparators E, F and G, which monitor the S rails: V33S, V18S, and V105S B11 VBSTVR3 I VR VR3 bootstrap pin B12 V33ADSW_ENIN I D Enable for power-good comparator A, which monitors V33ADSW B13 VBATTBKUP I AS RTC backup battery-supply connection C1 AGND1 - A Analog ground 1. Tie this pin directly to the ground plane. C2 ENVR4 I D VR4 enable VR4 enable C3 FBVR4P I AS VR4 positive-feedback remote sense. Connect this pin to the output voltage of VR4 at the output-load capacitor. C4 V33A_DSW_ENOUT O D Qualified enable for external V33A_DSW rail. C5 V18U25U_ENOUT D <td>B4</td> <td>VREGVR4</td> <td>Ι</td> <td>VR</td> <td>VR4 5-V drive-supply input. This pin is shorted on the PCB with LDO5V and is shared with VR3.</td>	B4	VREGVR4	Ι	VR	VR4 5-V drive-supply input. This pin is shorted on the PCB with LDO5V and is shared with VR3.			
B7 PGNDLD01 VR LD01 power ground B8 VOUTLD01 O VR LD01 output voltage. The voltage of this pin equals ½ × VINLD01SNS. B9 PGVR3 O D VR3 power-good comparator output. This pin is a push-pull output. B10 SRAIL_ENIN I D Enable for power-good comparators E, F and G, which monitor the S rails: V33S, V18S, and V105S B11 VBSTVR3 I VR VR3 bootstrap pin B12 V33ADSW_ENIN I D Enable for power-good comparator A, which monitors V33ADSW B13 VBATTBKUP I AS RTC backup battery-supply connection C1 AGND1 A Analog ground 1. Tie this pin directly to the ground plane. C2 ENVR4 I D VR4 enable VR4 positive-feedback remote sense. Connect this pin to the output voltage of VR4 at the output-load capacitor. C4 V33A_DSW_ENOUT O D VR4 positive-feedback remote sense. Connect this pin is active low. C5 V18U25U_ENOUT O D V18U_25U enable to the PoL load switch or regulator (push-pull to VDDPG) C7 SHUTDOWN I D Set shutdow	B5	PGVR4	0	D	VR4 power-good comparator output. This pin is an open-drain output.			
B8 VOUTLDO1 O VR LDO1 output voltage. The voltage of this pin equals ½ × VINLDO1SNS. B9 PGVR3 O D VR3 power-good comparator output. This pin is a push-pull output. B10 SRAIL_ENIN I D Enable for power-good comparators E, F and G, which monitor the S rails: V33S, V18S, and V105S B11 VBSTVR3 I VR VR3 bootstrap pin B12 V33ADSW_ENIN I D Enable for power-good comparator A, which monitors V33ADSW B13 VBATTBKUP I AS RTC backup battery-supply connection C1 AGND1 — A Analog ground 1. Tie this pin directly to the ground plane. C2 ENVR4 I D VR4 enable VR4 positive-feedback remote sense. Connect this pin to the output voltage of VR4 at the output-load capacitor. C4 V33A_DSW_ENOUT O D Qualified enable for external V33A_DSW rail. C5 V18U25U_ENOUT O D Qualified enable to the PoL load switch or regulator (push-pull to VDDPG) C6 V5ADS3_PG O D Power-good comparator C output for V5A_DS3 (push-pull to VDDP	B6	VINLDO1	Ι	VR	LDO1 input supply			
B9 PGVR3 O D VR3 power-good comparator output. This pin is a push-pull output. B10 SRAIL_ENIN I D Enable for power-good comparators E, F and G, which monitor the S rails: V33S, V18S, and V105S B11 VBSTVR3 I VR VR3 bootstrap pin B12 V33ADSW_ENIN I D Enable for power-good comparator A, which monitors V33ADSW B13 VBATTBKUP I AS RTC backup battery-supply connection C1 AGND1 — A Analog ground 1. Tie this pin directly to the ground plane. C2 ENVR4 I D VR4 enable C3 FBVR4P I AS VR4 positive-feedback remote sense. Connect this pin to the output voltage of VR4 at the output-load capacitor. C4 V33A_DSW_ENOUT O D Qualified enable for external V33A_DSW rail. C5 V18U25U_ENOUT O D Qualified enable for external V33A_DSW rail. C5 V18U25U_ENOUT O D V18U_25U enable to the PoL load switch or regulator (push-pull to VDDPG) C6 V5ADS3_PG O D Power-good comparator C output for X5A_DS3 (push-pull to VDDPG)	B7	PGNDLDO1	_	VR	LDO1 power ground			
B10SRAIL_ENINIDEnable for power-good comparators E, F and G, which monitor the S rails: V33S, V18S, and V105SB11VBSTVR3IVRVR3 bootstrap pinB12V33ADSW_ENINIDEnable for power-good comparator A, which monitors V33ADSWB13VBATTBKUPIASRTC backup battery-supply connectionC1AGND1—AAnalog ground 1. Tie this pin directly to the ground plane.C2ENVR4IDVR4 enableC3FBVR4PIASVR4 positive-feedback remote sense. Connect this pin to the output voltage of VR4 at the output-load capacitor.C4V33A_DSW_ENOUTODQualified enable for external V33A_DSW rail.C5V18U25U_ENOUTODV18U_25U enable to the PoL load switch or regulator (push-pull to VDDPG)C6V5ADS3_PGODPower-good comparator C output for V5A_DS3 (push-pull to VDDPG)C7SHUTDOWNIDSet shutdown mode (all supplies off). This pin is active low.C8RESETODGlobal disable output for external converters and power tree. This pin is active low.C9ILIMVR3LSIASVR3 courrent-limit setting, low-side FET valley-current limitC10FBVR3PIASVR3 positive-feedback remote sense. Connect this pin to the output voltage of VR3 at the output-load capacitor.C11V18U25U_ENINIDEnable for power-good comparator G, which monitors V18U_25UC12V5A_DS3_ENINIDEnable for po	B8	VOUTLDO1	0	VR	LDO1 output voltage. The voltage of this pin equals $\frac{1}{2} \times \text{VINLDO1SNS}$.			
BI0 SHAIL_ENIN I D V18S, and V105S ⁻ B11 VBSTVR3 I VR VR3 bootstrap pin B12 V33ADSW_ENIN I D Enable for power-good comparator A, which monitors V33ADSW B13 VBATTBKUP I AS RTC backup battery-supply connection C1 AGND1 — A Analog ground 1. Tie this pin directly to the ground plane. C2 ENVR4 I D VR4 enable C3 FBVR4P I AS VR4 positive-feedback remote sense. Connect this pin to the output voltage of VR4 at the output-load capacitor. C4 V33A_DSW_ENOUT O D Qualified enable for external V33A_DSW rail. C5 V18U5U_ENOUT O D V18U_25U enable to the PoL load switch or regulator (push-pull to VDDPG) C6 V5ADS3_PG O D Power-good comparator C output for V5A_DS3 (push-pull to VDDPG) C7 SHUTDOWN I D Set shutdown mode (all supplies off). This pin is active low. C8 RESET O D Global disable output for external converters and power tree. This pin is active low. C9 ILIMVR3LS <td>B9</td> <td>PGVR3</td> <td>0</td> <td>D</td> <td>VR3 power-good comparator output. This pin is a push-pull output.</td>	B9	PGVR3	0	D	VR3 power-good comparator output. This pin is a push-pull output.			
B12 V33ADSW_ENIN I D Enable for power-good comparator A, which monitors V33ADSW B13 VBATTBKUP I AS RTC backup battery-supply connection C1 AGND1 — A Analog ground 1. Tie this pin directly to the ground plane. C2 ENVR4 I D VR4 enable C3 FBVR4P I AS VR4 positive-feedback remote sense. Connect this pin to the output voltage of VR4 at the output-load capacitor. C4 V33A_DSW_ENOUT O D Qualified enable for external V33A_DSW rail. C5 V18U25U_ENOUT O D V18U_25U enable to the PoL load switch or regulator (push-pull to VDDPG) C6 V5ADS3_PG O D Power-good comparator C output for V5A_DS3 (push-pull to VDDPG) C7 SHUTDOWN I D Set shutdown mode (all supplies off). This pin is active low. C8 RESET O D Global disable output for external converters and power tree. This pin is active low. C10 FBVR3P I AS VR3 positive-feedback remote sense. Connect this pin to the output voltage of VR3 at the output-load capacitor. C11 V18U25U_ENIN I D	B10	SRAIL_ENIN	I	D				
B13 VBATTBKUP I AS RTC backup battery-supply connection C1 AGND1 — A Analog ground 1. Tie this pin directly to the ground plane. C2 ENVR4 I D VR4 enable C3 FBVR4P I AS VR4 positive-feedback remote sense. Connect this pin to the output voltage of VR4 at the output-load capacitor. C4 V33A_DSW_ENOUT O D Qualified enable for external V33A_DSW rail. C5 V18U25U_ENOUT O D V18U_25U enable to the PoL load switch or regulator (push-pull to VDDPG) C6 V5ADS3_PG O D Power-good comparator C output for V5A_DS3 (push-pull to VDDPG) C7 SHUTDOWN I D Set shutdown mode (all supplies off). This pin is active low. C8 RESET O D Global disable output for external converters and power tree. This pin is active low. C9 ILIMVR3LS I AS VR3 positive-feedback remote sense. Connect this pin to the output voltage of VR3 at the output-load capacitor. C11 V18U25U_ENIN I D Enable for power-good comparator B, which monitors V18U_25U C12 V5A_DS3_ENIN I D	B11	VBSTVR3	Ι	VR	VR3 bootstrap pin			
C1AGND1—AAnalog ground 1. Tie this pin directly to the ground plane.C2ENVR4IDVR4 enableC3FBVR4PIASVR4 positive-feedback remote sense. Connect this pin to the output voltage of VR4 at the output-load capacitor.C4V33A_DSW_ENOUTODQualified enable for external V33A_DSW rail.C5V18U25U_ENOUTODV18U_25U enable to the PoL load switch or regulator (push-pull to VDDPG)C6V5ADS3_PGODPower-good comparator C output for V5A_DS3 (push-pull to VDDPG)C7SHUTDOWNIDSet shutdown mode (all supplies off). This pin is active low.C8RESETODGlobal disable output for external converters and power tree. This pin is active low.C9ILIMVR3LSIASVR3 current-limit setting, low-side FET valley-current limitC10FBVR3PIASVR3 positive-feedback remote sense. Connect this pin to the output voltage of VR3 at the output-load capacitor.C11V18U25U_ENINIDEnable for power-good comparator B, which monitors V18U_25UC12V5A_DS3_ENINIDEnable for power-good comparator C, which monitors V5A_DS3C13V3P3A_RTCOASPCH RTC power supplyD1VDDPGIVRPGx supply. This pin sets the output level for the PG pins for A-H if the PG pin is	B12	V33ADSW_ENIN	Ι	D	Enable for power-good comparator A, which monitors V33ADSW			
C2 ENVR4 I D VR4 enable C3 FBVR4P I As VR4 positive-feedback remote sense. Connect this pin to the output voltage of VR4 at the output-load capacitor. C4 V33A_DSW_ENOUT O D Qualified enable for external V33A_DSW rail. C5 V18U25U_ENOUT O D VI8U_25U enable to the PoL load switch or regulator (push-pull to VDDPG) C6 V5ADS3_PG O D Power-good comparator C output for V5A_DS3 (push-pull to VDDPG) C7 SHUTDOWN I D Set shutdown mode (all supplies off). This pin is active low. C8 RESET O D Global disable output for external converters and power tree. This pin is active low. C9 ILIMVR3LS I AS VR3 positive-feedback remote sense. Connect this pin to the output voltage of VR3 at the output-load capacitor. C10 FBVR3P I AS VR3 positive-feedback remote sense. Connect this pin to the output voltage of VR3 at the output-load capacitor. C11 V18U25U_ENIN I D Enable for power-good comparator B, which monitors V18U_25U C12 V5A_DS3_ENIN I D Enable for power-good comparator C, which monitors V5A_DS3	B13	VBATTBKUP	Ι	AS	RTC backup battery-supply connection			
C3FBVR4PIASVR4 positive-feedback remote sense. Connect this pin to the output voltage of VR4 at the output-load capacitor.C4V33A_DSW_ENOUTODQualified enable for external V33A_DSW rail.C5V18U25U_ENOUTODV18U_25U enable to the PoL load switch or regulator (push-pull to VDDPG)C6V5ADS3_PGODPower-good comparator C output for V5A_DS3 (push-pull to VDDPG)C7SHUTDOWNIDSet shutdown mode (all supplies off). This pin is active low.C8RESETODGlobal disable output for external converters and power tree. This pin is active low.C9ILIMVR3LSIASVR3 current-limit setting, low-side FET valley-current limitC10FBVR3PIASVR3 positive-feedback remote sense. Connect this pin to the output voltage of VR3 at the output-load capacitor.C11V18U25U_ENINIDEnable for power-good comparator C, which monitors V18U_25UC12V5A_DS3_ENINIDEnable for power-good comparator C, which monitors V5A_DS3C13V3P3A_RTCOASPCH RTC power supplyD1VDPRGIVRPGx supply. This pin sets the output level for the PG pins for A-H if the PG pin is	C1	AGND1	_	Α	Analog ground 1. Tie this pin directly to the ground plane.			
C3 FBVR4P I AS the output-load capacitor. C4 V33A_DSW_ENOUT O D Qualified enable for external V33A_DSW rail. C5 V18U25U_ENOUT O D V18U_25U enable to the PoL load switch or regulator (push-pull to VDDPG) C6 V5ADS3_PG O D Power-good comparator C output for V5A_DS3 (push-pull to VDDPG) C7 SHUTDOWN I D Set shutdown mode (all supplies off). This pin is active low. C8 RESET O D Global disable output for external converters and power tree. This pin is active low. C9 ILIMVR3LS I AS VR3 current-limit setting, low-side FET valley-current limit C10 FBVR3P I AS VR3 positive-feedback remote sense. Connect this pin to the output voltage of VR3 at the output-load capacitor. C11 V18U25U_ENIN I D Enable for power-good comparator B, which monitors V18U_25U C12 V5A_DS3_ENIN I D Enable for power-good comparator C, which monitors V5A_DS3 C13 V3P3A_RTC O AS PCH RTC power supply D1 VRP PGx supply. This pin sets the output level for the PG pins for A-H if the P	C2	ENVR4	Ι	D	VR4 enable			
C5 V18U25U_ENOUT O D V18U_25U enable to the PoL load switch or regulator (push-pull to VDDPG) C6 V5ADS3_PG O D Power-good comparator C output for V5A_DS3 (push-pull to VDDPG) C7 SHUTDOWN I D Set shutdown mode (all supplies off). This pin is active low. C8 RESET O D Global disable output for external converters and power tree. This pin is active low. C9 ILIMVR3LS I AS VR3 current-limit setting, low-side FET valley-current limit C10 FBVR3P I AS VR3 positive-feedback remote sense. Connect this pin to the output voltage of VR3 at the output-load capacitor. C11 V18U25U_ENIN I D Enable for power-good comparator C, which monitors V18U_25U C12 V5A_DS3_ENIN I D Enable for power-good comparator C, which monitors V5A_DS3 C13 V3P3A_RTC O AS PCH RTC power supply D1 VRB PGx supply. This pin sets the output level for the PG pins for A-H if the PG pin is	C3	FBVR4P	I	AS	VR4 positive-feedback remote sense. Connect this pin to the output voltage of VR4 at the output-load capacitor.			
C6 V5ADS3_PG O D Power-good comparator C output for V5A_DS3 (push-pull to VDDPG) C7 SHUTDOWN I D Set shutdown mode (all supplies off). This pin is active low. C8 RESET O D Global disable output for external converters and power tree. This pin is active low. C9 ILIMVR3LS I AS VR3 current-limit setting, low-side FET valley-current limit C10 FBVR3P I AS VR3 positive-feedback remote sense. Connect this pin to the output voltage of VR3 at the output-load capacitor. C11 V18U25U_ENIN I D Enable for power-good comparator C, which monitors V18U_25U C12 V5A_DS3_ENIN I D Enable for power-good comparator C, which monitors V5A_DS3 C13 V3P3A_RTC O AS PCH RTC power supply D1 VRB PGx supply. This pin sets the output level for the PG pins for A-H if the PG pin is	C4	V33A_DSW_ENOUT	0	D	Qualified enable for external V33A_DSW rail.			
C7 SHUTDOWN I D Set shutdown mode (all supplies off). This pin is active low. C8 RESET O D Global disable output for external converters and power tree. This pin is active low. C9 ILIMVR3LS I AS VR3 current-limit setting, low-side FET valley-current limit C10 FBVR3P I AS VR3 positive-feedback remote sense. Connect this pin to the output voltage of VR3 at the output-load capacitor. C11 V18U25U_ENIN I D Enable for power-good comparator B, which monitors V18U_25U C12 V5A_DS3_ENIN I D Enable for power-good comparator C, which monitors V5A_DS3 C13 V3P3A_RTC O AS PCH RTC power supply D1 VDDPC I VR	C5	V18U25U_ENOUT	0	D	V18U_25U enable to the PoL load switch or regulator (push-pull to VDDPG)			
C8 RESET O D Global disable output for external converters and power tree. This pin is active low. C9 ILIMVR3LS I AS VR3 current-limit setting, low-side FET valley-current limit C10 FBVR3P I AS VR3 positive-feedback remote sense. Connect this pin to the output voltage of VR3 at the output-load capacitor. C11 V18U25U_ENIN I D Enable for power-good comparator B, which monitors V18U_25U C12 V5A_DS3_ENIN I D Enable for power-good comparator C, which monitors V5A_DS3 C13 V3P3A_RTC O AS PCH RTC power supply D1 VRB PGx supply. This pin sets the output level for the PG pins for A-H if the PG pin is	C6	V5ADS3_PG	0	D	Power-good comparator C output for V5A_DS3 (push-pull to VDDPG)			
C9 ILIMVR3LS I AS VR3 current-limit setting, low-side FET valley-current limit C10 FBVR3P I AS VR3 positive-feedback remote sense. Connect this pin to the output voltage of VR3 at the output-load capacitor. C11 V18U25U_ENIN I D Enable for power-good comparator B, which monitors V18U_25U C12 V5A_DS3_ENIN I D Enable for power-good comparator C, which monitors V5A_DS3 C13 V3P3A_RTC O AS PCH RTC power supply D1 VDDPC I VR PGx supply. This pin sets the output level for the PG pins for A-H if the PG pin is	C7	SHUTDOWN	Ι	D	Set shutdown mode (all supplies off). This pin is active low.			
C10FBVR3PIASVR3 positive-feedback remote sense. Connect this pin to the output voltage of VR3 at the output-load capacitor.C11V18U25U_ENINIDEnable for power-good comparator B, which monitors V18U_25UC12V5A_DS3_ENINIDEnable for power-good comparator C, which monitors V5A_DS3C13V3P3A_RTCOASPCH RTC power supplyD1VDDPCIVRPGx supply. This pin sets the output level for the PG pins for A-H if the PG pin is	C8	RESET	0	D	Global disable output for external converters and power tree. This pin is active low.			
C10 FBVR3F I AS the output-load capacitor. C11 V18U25U_ENIN I D Enable for power-good comparator B, which monitors V18U_25U C12 V5A_DS3_ENIN I D Enable for power-good comparator C, which monitors V5A_DS3 C13 V3P3A_RTC O AS PCH RTC power supply D1 VDDPG I VR PGx supply. This pin sets the output level for the PG pins for A-H if the PG pin is	C9	ILIMVR3LS	Ι	AS	VR3 current-limit setting, low-side FET valley-current limit			
C12 V5A_DS3_ENIN I D Enable for power-good comparator C, which monitors V5A_DS3 C13 V3P3A_RTC O AS PCH RTC power supply D1 VDDPC I VR PGx supply. This pin sets the output level for the PG pins for A-H if the PG pin is	C10	FBVR3P	I	AS	VR3 positive-feedback remote sense. Connect this pin to the output voltage of VR3 at the output-load capacitor.			
C13 V3P3A_RTC O AS PCH RTC power supply D1 VDDPG I VB PGx supply. This pin sets the output level for the PG pins for A-H if the PG pin is	C11	V18U25U_ENIN	Ι	D	Enable for power-good comparator B, which monitors V18U_25U			
PGx supply. This pin sets the output level for the PG pins for A-H if the PG pin is	C12	V5A_DS3_ENIN	Ι	D	Enable for power-good comparator C, which monitors V5A_DS3			
	C13	V3P3A_RTC	0	AS	PCH RTC power supply			
	D1	VDDPG	I	VR	PGx supply. This pin sets the output level for the PG pins for A-H if the PG pin is configured as a push-pull pin.			
D2 ILIMVR4 I AS VR4 current-limit setting, low-side FET valley-current limit	D2	ILIMVR4	Ι	AS	VR4 current-limit setting, low-side FET valley-current limit			

(1) VR = VR critical, AS = Analog sensitive, D = Digital, A = AGND

	PIN		TYPE ⁽¹⁾	DESCRIPTION		
NO.	NAME	I/O	TYPE	DESCRIPTION		
D3	VPROGOTP	I	AS	Always connect this pin to the LDO5V pin. This pin is the supply voltage for OTP programming (must be connected to the LDO5V pin in normal operation).		
D4	DDRID	I	D	VR4 output voltage selection pin. Set this pin low for 1.2-V operation, high for 1.35-V operation, or floating for 1.1-V operation.		
D5	FBVR4N	I	AS	VR4 negative-feedback remote sense. Connect this pin to the GND of VR4 at the output-load capacitor.		
D6	V33ADSW_PG	0	D	Power good comparator A output for V33A_DSW rail.		
D7	FBVR3N	I	AS	VR3 negative-feedback remote sense. Connect this pin to the GND of VR3 at the output-load capacitor.		
D8	FBLDO1	I	AS	LDO1 feedback-voltage kelvin sense. Connect this pin to the output voltage of the LDO1 pin at the output-load capacitor.		
D9	STANDBY	I	D	Set rails in standby when this pin is low (low-power mode)		
D10	ILIMVR3HS	I	AS	VR3 current-limit setting, high-side FET peak-current limit		
D11	ACOK	I	D	ACOK input		
D12	PMIC_INT	0	D	PMIC to EC interrupt. This pin is an open-drain output and is active low.		
D13	AGND4	_	А	Analog ground 4. Tie this pin directly to the ground plane.		
E1	VDDIO	I	VR	Voltage supply input for the I/O buffers. The VDDIO pin should be tied to the LDO3V (3.3 V) pin.		
E2	ACIN	I	AS	AC adaptor voltage sense		
E3	DDR_VTT_CTRL	I	D	LDO1 enable and DVS control of VR4		
E4	VCCST_PWRGD	0	D	VCCST power good .This pin is an open-drain output.		
E5	VINPP	I	AS	VIN for the power-path domain. Connect this pin to the external diode or from AC, BAT1, or BAT2.		
E6	VCCIO	I	AS	Power good comparator D input and discharge path for VCCIO rail		
E7	V33ADSW	I	AS	Power Good comparator A Input and discharge path for the V33A_DSW_rail		
E8	V18S	I	AS	Power-good comparator F input and discharge path for the V18S rail		
E9	ENVR3	I	D	VR3 enable		
E10	FBVR2N	I	AS	VR2 negative-feedback remote sense. Connect this pin to the GND of VR2 at the output-load capacitor.		
E11	PCH_PWROK	0	D	Core and non-core power-good pin. This pin is the delayed version of the ALL_SYS_PWRGD pin. This pin is an open-drain output.		
E12	PGVR2	0	D	VR2 power-good comparator output. This pin is a push-pull output.		
E13	VREGVR2	I	VR	VR2 5-V drive-supply input. This pin is shorted on the PCB with LDO5V.		
F1	BAT1	I	AS	Battery 1 voltage-sense input		
F2	BAT1SWON	0	D	Battery 1 switch-on power path. This pin is an open-drain output and is active low.		
F3	V105S_PG	0	D	Power-good comparator G output for V105S. This pin is an open-drain output.		
F4	V33S	I	AS	Power-good comparator E input and discharge path for the V33A rail		
F5	IN_LSH	I	AS	Input for level shifter H		
F6	AGND	_	А	Analog ground. Tie this pin directly to the ground plane.		
F7	AGND	_	А	Analog ground. Tie this pin directly to the ground plane.		
F8	AGND	_	А	Analog ground. Tie this pin directly to the ground plane.		
F9	VINLDO1S	I	AS	LDO1 input voltage-reference sense. Connect this pin to the output voltage of the VR4 pin at the output-load capacitor.		
F10	SLP_SUS	I	D	Input for SLP_SUS signal for the power-good tree		
F11	ENVR2	I	D	VR2 enable		
F12	VINVR2	I	VR	VR2 power input voltage. Connect this pin to a 3.3-V voltage regulator, such as the V3.3A_DSW.		
F13	VINVR2	I	VR	VR2 power input voltage. Connect this pin to a 3.3-V voltage regulator, such as the V3.3A_DSW.		
G1	BAT2	I	AS	Battery 2 voltage-sense input		
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Pin Attributes—ZAJ Package (continued)

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Pin Attributes—ZAJ Package (continued)

	PIN	1/0	T VDE(1)	DECODIDITION	
NO.	NAME	I/O	TYPE ⁽¹⁾	DESCRIPTION	
G2	BAT2SWON	0	D	Battery 2 switch-on power path. This pin is an open-drain output and is active low.	
G3	VDCSNS	I	AS	VDC voltage monitor	
G4	FBVR5P	I	AS	VR5 positive-feedback remote sense. Connect this pin to the output voltage of VR5 at the output-load capacitor.	
G5	AGND		Α	Analog ground. Tie this pin directly to the ground plane.	
G6	AGND		Α	Analog ground. Tie this pin directly to the ground plane.	
G7	AGND	—	Α	Analog ground. Tie this pin directly to the ground plane.	
G8	AGND	—	Α	Analog ground. Tie this pin directly to the ground plane.	
G9	VINVR3	I	AS	VR3 input-voltage sense and high-side current-sense. Kelvin connect this pin to the drain of high-side FET.	
G10	FBVR2P	I	AS	VR2 positive-feedback remote sense. Connect this pin to the output voltage of VR2 at the output-load capacitor.	
G11	ALL_SYS_PWRGD	0	D	Non-core rails power-good pin. Power-good pin for all PMIC and specified monitored VRs. This pin is an open-drain output.	
G12	PGNDVR2	—	VR	VR2 power ground	
G13	PGNDVR2	—	VR	VR2 power ground	
H1	SDA	I/O	D	I ² C data	
H2	PWRBTNIN	I	AS	Power-button input (internal pullup to LDO3V). This pin is active low.	
H3	VCCIO_ENOUT	0	D	Qualified enable for VCCIO rail.	
H4	V5ADS3_ENOUT	0	D	Power-good comparator F output for V18S or V33A_PCH and enable to the PoL load switch or regulator (push-pull to VDDPG)	
H5	AGND	—	Α	Analog ground. Tie this pin directly to the ground plane.	
H6	AGND	—	Α	Analog ground. Tie this pin directly to the ground plane.	
H7	AGND	—	Α	Analog ground. Tie this pin directly to the ground plane.	
H8	AGND	—	Α	Analog ground. Tie this pin directly to the ground plane.	
H9	NVDC	I	D	$\frac{\text{NVDC}}{\text{NVDC}}$ select. This pin has two levels: low = $\frac{\text{NVDC}}{\text{NVDC}}$, high = non-NVDC. Connect the $\frac{\text{NVDC}}{\text{NVDC}}$ pin to ground for NVDC. Connect the $\frac{\text{NVDC}}{\text{NVDC}}$ pin to the LDO3V pin for non-NVDC.	
H10	TRIP	0	D	VCOMP comparator push-pull output. This pin is active low.	
H11	SYS_PWROK	0	D	Delayed version of the ALL_SYS_PWRGD pin. This pin is an open-drain output.	
H12	SWVR2	I	VR	VR2 switch-node connection	
H13	SWVR2	I	VR	VR2 switch-node connection	
J1	SCLK	I	D	I ² C clock	
J2	ACSWON	0	D	AC adaptor switch-on power path. This pin is an open-drain output and is active low.	
J3	EC_RST	0	D	EC reset. This pin is an open-drain output and is active low.	
J4	VCOMP	I	AS	VCOMP comparator input	
J5	AGND	—	Α	Analog ground. Tie this pin directly to the ground plane.	
J6	AGND	—	Α	Analog ground. Tie this pin directly to the ground plane.	
J7	AGND	—	Α	Analog ground. Tie this pin directly to the ground plane.	
J8	AGND	—	Α	Analog ground. Tie this pin directly to the ground plane.	
J9	FBVR1N	I	AS	VR1 negative-feedback remote sense. Connect this pin to the GND of the VR1 pin at the output-load capacitor.	
J10	V105S	I	AS	Power-good comparator G input and discharge path for the V105S rail	
J11	RSMRST_PWRGD	0	D	Resume-reset power good. This pin is an open-drain output and is active low.	
J12	SLP_S3	I	D	Input for SLP_SUS signal for the power-good tree	
J13	VCCIO_ENIN	I	D	Enable for power good comparator D which is V33A_DSW	
K1	AGND2		А	Analog ground 2. Tie this pin directly to the ground plane.	
K2	PCH_PWRBTN	0	D	Power-button signal to PCH. This pin is an open-drain output and is active low.	
K3	EN3V3SW	I	D	Enable for load switch from the LDO3V pin to the VOUT3V3SW output pin	

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			Pin Attr	ibutes—ZAJ Package (continued)					
	PIN	1/0	TYPE ⁽¹⁾	DECODIDITION					
NO.	NAME	I/O		DESCRIPTION					
K4	EC_ONOFF	0	D	Debounced version of PWRBTNIN. This pin is an op					
K5	ILIMVR5HS	I	AS	VR5 current-limit setting, high-side FET peak-curren					
K6	AGND	_	Α	Analog ground. Tie this pin directly to the ground pla					

inued)

NO.	NAME	1/0	TYPE	DESCRIPTION	
K4	EC_ONOFF	0	D	Debounced version of PWRBTNIN. This pin is an open-drain output and is active low.	
K5	ILIMVR5HS	I	AS	VR5 current-limit setting, high-side FET peak-current limit	
K6	AGND	_	Α	Analog ground. Tie this pin directly to the ground plane.	
K7	AGND		Α	Analog ground. Tie this pin directly to the ground plane.	
K8	V5A_DS3	I	AS	Power-good comparator C input and discharge path for the V5A_DS3 rail	
K9	V18U25U	I	AS	Power-good comparator B input and discharge path for the V18U_25U rail	
K10	FBVR1P	I	AS	VR1 positive-feedback remote sense. Connect this pin to the output voltage of VR1 at the output-load capacitor.	
K11	1Hz	0	D	1-Hz clock output for waking up the embedded controller (EC).	
K12	DPWROK	0	D	Delayed version of V3.3A_DSW_PG. This pin is an open-drain output.	
K13	DS3_VREN	0	D	DS3 VR enable. This pin enables the external power switches. This pin is a push-pull output.	
L1	ECVCC	I	AS	EC VCC supply	
L2	TEMP_ALERT	0	D	Open-drain output of the silicon temperature sensor. This pin is the input to the power-monitor unit (PMU). Connect this pin to the to PROCHOT pin of the system. This pin is active low. TI recommends connecting a 50- Ω pullup resistor from this pin to the V1.00S pin.	
L3	SLAVEADDR	I	D	I^2C slave-address select (low = 0x30, high = 0x32, open = float = 0x34). This pin keeps the same connection during operation.	
L4	FBVR5N	I	AS	VR5 negative-feedback remote sense. Connect this pin to the GND of VR5 at the output-load capacitor.	
L5	ILIMVR5LS	I	AS	VR5 Current-limit setting, low-side FET valley-current limit	
L6	IN_LSA	I	D	Input of level shifter A	
L7	VINVR5	I	AS	VR5 input-voltage sense and high-side current-sense. Kelvin connect this pin to the drain of high-side FET.	
L8	VDDLV	I	VR	LVx buffer supply. This pin sets the output level for the level shifter pins.	
L9	ILIMVR1	I	AS	VR1 current-limit setting, low-side FET valley-current limit	
L10	OUT_LSB	0	D	Output of level shifter B	
L11	IN_LSB	I	D	Input of level shifter B	
L12	OUT_LSA	0	D	Output of level shifter A	
L13	AGND3	_	A	Analog ground 3. Tie this pin directly to the ground plane.	
M1	DRVHVR5	0	VR	VR5 high-side gate-drive output for the external-power FET	
M2	ENVR5	I	D	VR5 enable	
M3	VBSTVR5	I	VR	VR5 bootstrap pin	
M4	PGVR5	0	D	VR5 power-good comparator output. This pin is a push-pull output.	
M5	EN5VSW	I	D	Enable internal-load switch from the 5-V switching regulator to the LDO5V output through the VIN5VSW pin. Connect this pin to power-good of the 5-V switching regulator.	
M6	OUT_LSH	0	D	Output of level shifter H	
M7	VOUT3V3SW	0	VR	EC domain load-switch output and discharge path from LDO3V	
M8	VINLDO3	I	VR	LDO3V input supply	
M9	PGVR1	0	D	VR1 power-good comparator output. This pin is a push-pull output.	
M10	VREGVR1	I	VR	5-V drive-supply input. This pin is shorted on the PCB with LDO5V. This pin is the supply for VR1 and VR5.	
M11	VBSTVR1	I	VR	VR1 bootstrap pin	
M12	ENVR1	I	D	VR1 enable	
M13	VDDIO	I	VR	Voltage supply input for the I/O buffers. The VDDIO pin should be tied to the LDO3V (3.3 V) pin.	
N1	NC	NC	—	No connect pin. Solder this pin to the PCB for mechanical strength.	
	SWVR5		VR	VR5 switch-node connection	

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PIN		1/0	TYPE ⁽¹⁾	DECODIDEION
NO.	NAME	I/O	TTPE	DESCRIPTION
N3	PGNDVR5		VR	VR5 power ground
N4	DRVLVR5	0	VR	VR5 Low side gate drive output for the external-power FET
N5	VIN5VSW	Ι	VR	Internal load switch from the 5-V switching regulator to the LDO5V output. Connect the VIN5VSW pin to the 5-V switching regulator output.
N6	VIN	Ι	VR	Device input voltage
N7	LDO5V	0	AS	5-V internal supply used primarily for the gate drives
N8	LDO3V	0	AS	3.3-V LDO used as a reference voltage and as a pullup supply
N9	DRVLVR1	0	VR	VR1 Low side gate drive output for the external-power FET
N10	PGNDVR1		VR	VR1 power ground
N11	SWVR1	Ι	VR	VR1 switch-node connection
N12	DRVHVR1	0	VR	VR1 high-side gate-drive output for the external-power FET
N13	NC	NC	_	No connect pin. Solder this pin to the PCB for mechanical strength.

Pin Attributes—ZAJ Package (continued)



5 Specifications

5.1 Absolute Maximum Ratings

Over operating free-air temperature range (unless otherwise noted)⁽¹⁾

		MIN	MAX	UNIT
CHIP				-
Power input pins	VIN, VINLDO3	-0.3	28	V
Analog ground pins	AGND1, AGND2, AGND3, AGND4, AGND (16 center pins)	-0.3	0.3	V
SWITCHING REGULATORS				
Input pins, controllers	VINVR3, VINVR5	-0.3	28	V
Switch size controllers	SWVR1, SWVR3, SWVR4, SWVR5	-1	28	V
Switch pins, controllers	SWVR1, SWVR3, SWVR4, SWVR5 (transient <10ns)	-2	28	V
High-drive pins, controllers	DRVHVR1, DRVHVR3, DRVHVR4, DRVHVR5	-0.3	32	V
Low-drive pins, controllers	DRVLVR1, DRVLVR3, DRVLVR4, DRVLVR5	-0.3	7	V
D	VBSTVR1, VBSTVR3, VBSTVR4, VBSTVR5	-0.3	32	V
Bootstrap pins, controllers	Differential voltage between VBSTVRx and SWVRx	-0.3	7	V
Input pin, converter	VINVR2	-0.3	3.6	V
	SWVR2	-1	4.0	V
Switch pins, converter	SWVR2 (transient <10ns)	-2	5.5	V
Power-ground pins	PGNDVR1, PGNDVR2, PGNDVR3, PGNDVR4, PGNDVR5	-0.3	0.3	V
Enable pins	ENVR1, ENVR2, ENVR3, ENVR4, ENVR5	-0.3	3.6	V
NVDC select pin	NVDC	-0.3	3.6	V
· · · · · · · ·	FBVR1P, FBVR2P, FBVR3P, FBVR4P	-0.3	3.6	V
Positive remote-feedback pins	FBVR5P	-0.3	5.7	V
Negative remote-feedback pins	FBVR1N, FBVR2N, FBVR3N, FBVR4N, FBVR5N	-0.3	0.3	V
Gate-drive regulator input-power pins	VREGVR1, VREGVR2, VREGVR4	-0.3	5.7	V
Low-side current limit	ILIMVR1, ILIMVR3LS, ILIMVR4, ILMVR5LS	-0.3	3.6	V
High-side current limit	ILMVR3HS, ILMVR5HS	-0.3	3.6	V
LDO REGULATOR		1		
Input pin	VINLDO1	-0.3	3.6	V
Output pin	VOUTLDO1	-0.3	3.6	V
Power ground pin	PGNDLDO1	-0.3	0.3	V
Input feedback pin	VINLDO1S	-0.3	3.6	V
Output feedback pin	FBLDO1	-0.3	3.6	V
l ² C				
SCLK, SDAT, SLAVEADDR		-0.3	3.6	V
POWER-GOOD COMPARATOR LOG	IC	1		1
Power-good (push-pull) supply for input pins	VDDPG	-0.3	3.6	V
Power-good input-voltage sense pins	V33ADSW, V5ADS3, V18U25U, VCCIO, V105S, V33S, V18S	-0.3	5.7	V
Power-good enable pins	V33ADSW_ENIN, V18U25U_ENIN, V5ADS3_ENIN, VCCIO_ENIN, SLP_SUS, SLP_S3, SRAIL_ENIN	-0.3	3.6	V
Power-good output pins	V33ADSW_PG, V18U25U_ENOUT, V5ADS3_PG, VCCIO_ENOUT, V33ADSW_ENOUT, V5ADS3_ENOUT, V105S_PG	-0.3	3.6	V

(1) Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Conditions. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

Absolute Maximum Ratings (continued)

Over operating free-air temperature range (unless otherwise noted)⁽¹⁾

		MIN	MAX	UNIT
POWER-GOOD TREE LOGIC				
Open-drain outputs	DPWROK, RSMRST_PWRGD, VCCST_PGOOD, SYS_PWROK, ALL_SYS_PWRGD, PCH_PWROK	-0.3	3.6	V
DDR CONTROL				
Input pins	DDR_VTT_CTRL, DDRID	-0.3	3.6	V
LEVEL SHIFTERS				
Level-shifter (push-pull) supply input pin	VDDLV	-0.3	3.6	V
Level-shifter enable input pins	IN_LSA, IN_LSB, IN_LSH	-0.3	3.6	V
Level-shifter output pins	OUT_LSA,OUT_LSB,OUT_LSH	-0.3	3.6	V
POWER-PATH LOGIC				
Power-path comparator input voltage sense pins	VCOMP, BAT1, BAT2, ACIN	-0.3	7	V
Power-path comparator open-drain output pins	BAT1SWON, BAT2SWON, ACSWON	-0.3	28	V
PTC overtemperature comparator open-drain output pin	TRIP	-0.3	3.6	V
Power-path domain diode OR input pin	VINPP	-0.3	28	V
POWER BUTTON				
PWRBNTIN, PCH_PWRBTN, EC_ONC)FF	-0.3	3.6	V
RESETS				
ECVCC, RESET, EC_RST		-0.3	3.6	V
CLOCKS				
EC 1-Hz wake clock		-0.3	3.6	V
POWER MΩNITOR				
VDCSNS		-0.3	28	V
TEMP_ALERT		-0.3	3.6	V
ACOK		-0.3	12	V
REFERENCE				
	LDO5V	-0.3	7	V
LDO output pins	VREF1V25, LDO3V	-0.3	3.6	V
3.3-V load-switch enable pin	EN3V3SW	-0.3	3.6	V
3.3-V load-switch output pin	VOUT3V3SW	-0.3	3.6	V
5V- load-switch enable pin	EN5VSW	-0.3	3.6	V
5-V load-switch input pin	VIN5VSW	-0.3	6	V
BACKUP BATTERY RTC SELECTOR				
VBATTBKUP, V3P3A_RTC		-0.3	3.6	V
MISCELLANEOUS PINS				
Input control pins	STANDBY, SHUTDOWN	-0.3	3.6	V
Output interrupt pin	PMIC_INT	-0.3	3.6	V
Output DS3 VR enable pin	DS3_VREN	-0.3	3.6	V
Buffer-supply input pin	VDDIO	-0.3	3.6	V
VPROGOTP		-0.3	7	V
GENERAL				
Operating junction temperature, T _J		-40	150	°C
Storage temperature, T _{stg}		-65	150	°C



5.2 **ESD Ratings**

			VALUE	UNIT
V	Electrostatic	Human body model (HBM), per ANSI/ESDA/JEDEC JS-001 ⁽¹⁾	±1500	V
V _(ESD)	discharge	Charged device model (CDM), per JEDEC specification JESD22-C101 ⁽²⁾	±500	V

JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process. JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process. (1)

(2)

5.3 **Recommended Operating Conditions**

Over operating free-air temperature range (unless otherwise noted)

		MIN	MAX	UNIT
CHIP				
Power input pins	VIN, VINLDO3	-0.3	21	V
Analog ground pins	AGND1, AGND2, AGND3, AGND4, AGND (16 center pins)	-0.3	0.3	V
SWITCHING REGULATORS				
Input pins, controllers	VINVR3, VINVR5	-0.3	21	V
Switch pins, controllers	SWVR1 , SWVR3 , SWVR4 , SWVR5	-1	21	V
High-drive pins, controllers	DRVHVR1, DRVHVR3, DRVHVR4, DRVHVR5	-0.3	26	V
Low-drive pins, controllers	DRVLVR1, DRVLVR3, DRVLVR4, DRVLVR5	-0.3	5	V
	VBSTVR1, VBSTVR3, VBSTVR4, VBSTVR5	-0.3	26	V
Bootstrap pins, controllers	Differential voltage between VBSTVRx and SWVRx	-0.3	5	V
Input pin, converter	VINVR2	-0.3	3.3	V
Switch pins, converter	SWVR2	-1	3.3	V
Power-ground pins	PGNDVR1, PGNDVR2, PGNDVR3, PGNDVR4, PGNDVR5	-0.3	0.3	V
Enable pins	ENVR1, ENVR2, ENVR3, ENVR4, ENVR5	-0.3	3.3	V
NVDC select pin	NVDC	-0.3	3.3	V
Desitive versets for discal, since	FBVR1P, FBVR2P, FBVR3P, FBVR4P	-0.3	3.3	V
Positive remote-feedback pins	FBVR5P	-0.3	5	V
Negative remote-feedback pins	FBVR1N, FBVR2N, FBVR3N, FBVR4N, FBVR5N	-0.3	0.3	V
Gate-drive regulator input power pins	VREGVR1, VREGVR2, VREGVR4	-0.3	5	V
Low-side current limit	ILIMVR1, ILIMVR3LS, ILIMVR4, ILMVR5LS	-0.3	3.3	V
High-side current limit	ILMVR3HS, ILMVR5HS	-0.3	3.3	V
LDO REGULATOR				
Input pin	VINLDO1	-0.3	3.3	V
Output pin	VOUTLDO1	-0.3	1.65	V
Power-ground pin	PGNDLDO1	-0.3	0.3	V
Input feedback pin	VINLDO1S	-0.3	3.3	V
Output feedback pin	FBLDO1	-0.3	1.65	V
l ² C				
SCLK, SDAT, SLAVEADDR		-0.3	3.3	V
POWERGOOD COMPARATOR LOGIC	C			
Power-good (push-pull) supply for input pins	VDDPG	-0.3	3.3	V
Power-good input voltage sense pins	V33ADSW, V5ADS3, V18U25U, VCCIO, V105S, V33S, V18S	-0.3	5	V
Power-good enable pins	V33ADSW_ENIN, V18U25U_ENIN, V5ADS3_ENIN, VCCIO_ENIN, SLP_SUS, SLP_S3, SRAIL_ENIN	-0.3	3.3	V
Power-good output pins	V33ADSW_PG, V18U25U_ENOUT, V5ADS3_PG, VCCIO_ENOUT, V33ADSW_ENOUT, V5ADS3_ENOUT, V105S_PG	-0.3	3.3	V
POWER-GOOD TREE LOGIC			+	
Open-drain outputs	DPWROK, RSMRST_PWRGD, VCCST_PGOOD, SYS_PWROK, ALL_SYS_PWRGD, PCH_PWROK	-0.3	3.3	V

Recommended Operating Conditions (continued)

Over operating free-air temperature range (unless otherwise noted)

		MIN	MAX	UNIT
DDR CONTROL				
Input pins	DDR_VTT_CTRL, DDRID	-0.3	3.3	V
LEVEL SHIFTERS				
Level-shifter (push-pull) supply input pin	VDDLV	-0.3	3.3	V
Level-shifter enable input pins	NU	-0.3	3.3	V
Level-shifter output pins	BC_ACOK	-0.3	3.3	V
POWER-PATH LOGIC				
Power-path comparator input voltage sense pins	VCOMP, BAT1, BAT2, ACIN	-0.3	5	V
Power-path comparator open-drain output pins	BAT1SWON, BAT2SWON, ACSWON	-0.3	21	V
PTC overtemperature comparator open-drain output pin	TRIP	-0.3	3.3	V
Power-path domain diode or input pir	VINPP	-0.3	21	V
POWER BUTTON				
PWRBNTIN, PCH_PWRBTN, EC_ON	IOFF	-0.3	3.3	V
RESETS				
ECVCC, RESET, EC_RST		-0.3	3.3	V
CLOCKS		·		
EC 1-Hz wake clock		-0.3	3.3	V
POWER MΩNITOR				
VDCSNS		-0.3	21	V
TEMP_ALERT		-0.3	3.3	V
ACOK		-0.3	3.3	V
REFERENCE				
LDO output pins	LDO5V	-0.3	5	V
	VREF1V25, LDO3V	-0.3	3.3	V
3.3-V load-switch enable pin	EN3V3SW	-0.3	3.3	V
3.3-V load-switch output pin	VOUT3V3SW	-0.3	3.3	V
5-V load-switch enable pin	EN5VSW	-0.3	3.3	V
5-V load-switch input pin	VIN5VSW	-0.3	5	V
BACKUP BATTERY RTC SELECTO	R			
VBATTBKUP, V3P3A_RTC		-0.3	3.3	V
MISCELLANEOUS PINS			;	
Input control pins	STANDBY, SHUTDOWN	-0.3	3.3	V
Output interrupt pin	PMIC_INT	-0.3	3.3	V
Output DS3 VR enable pin	DS3_VREN	-0.3	3.3	V
Buffer-supply input pin	VDDIO	-0.3	3.3	V
VPROGOTP		-0.3	5	V
GENERAL				
Operating free air temperature, T_A		-40	85	°C
Operating junction temperature, T _J		-40	125	°C



5.4 Thermal Information

		TPS650932	
	THERMAL METRIC ⁽¹⁾	ZAJ (nFBGA)	UNIT
		168 PINS	
R_{\thetaJA}	Junction-to-ambient thermal resistance	37.7	°C/W
R _{0JC(top)}	Junction-to-case (top) thermal resistance	15.1	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	11.8	°C/W
ΨJT	Junction-to-top characterization parameter	0.3	°C/W
ΨJB	Junction-to-board characterization parameter	11.7	°C/W
R _{0JC(bot)}	Junction-to-case (bottom) thermal resistance	_	°C/W

(1) For more information about traditional and new thermal metrics, see the *Semiconductor and IC Package Thermal Metrics* application report.

5.5 Electrical Characteristics: Control

Over recommended free-air temperature range and over recommended input voltage range (typical at an ambient temperature range of 25°C) (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN	ΤΥΡ	MAX	UNIT
SYSTEM						
M	Cystom input voltage	Parametric and functional	5.4	7.4	21	V
V _{IN}	System input voltage	Functional	5.4	7.4	24	V
Ι _Q	System quiescent current (includes IDDQ for LDO5V, LDO3V, and VREF1.25V, all registers are default setting)	Measured at VIN = 7.4 V		95	150	μΑ
V _{UVLO_5} V_Main	System undervoltage lockout threshold - All IC functionality including 5VLDO, except LDO3V and internal reference system	V _{VIN} voltage decreasing - measured at VIN (falling edge)	4.95	5.1	5.25	V
$V_{Hys_5V_Main}$	System undervoltage lockout threshold hysteresis	V_{VIN} voltage increasing - measured at VIN		200		mV
INTERNAL REF	ERENCES					
V _{O(VLDO5)}	LDO5V output	VIN = 5.4 V to 21 V, 10-mA load	4.9	5.0	5.1	V
Line regulation $V_{O(LDO5V)}$	Line regulation for regulator over operating voltage range	$\label{eq:VIN} \begin{array}{l} \text{VIN} = 5.4 \text{ V to } 21 \text{ V}, \text{ Measured as} \\ (?V_{O(LDO5V)}/V_{O(LDO5V)}) \text{ over this operating} \\ \text{range with } 40\text{mA load current. measured} \\ \text{at LDO5V pin with respect to AGND pin} \end{array}$			0.5%	
Load regulation V _{O(LDO5V)}	Load regulation for regulator over operating current range	$\label{eq:VIN} \begin{array}{l} VIN = 5.4V \mbox{ to } 21V \mbox{ Measured as} \\ (?V_{O(LDO5V)}/V_{O(LDO5V)}) \mbox{ over this operating} \\ range \mbox{ with } 10mA \mbox{ to } 100mA \mbox{ load current.} \\ measured \mbox{ at } LDO5V \mbox{ pin with respect to} \\ AGND \mbox{ pin} \end{array}$			2%	
I _{SC (LDO5V)}	Over current protection	Measured at 90% of the regulation voltage	115			mA
C _{O (LDO5V)}	External output capacitance range after derating	Actual capacitance after derating. ex: 2.7- μ F capacitance, then use a 4.7- μ F capacitor with 60% derating at 5 V	2.7	4.7	10	μF
V _{O(VREF1V25)}	VREF1V25 output - Internal buffered bandgap output	See below for output capacitance. measured at VREF1V25 pin with respect to AGND pin	1.244	1.25	1.256	V
C _{O (VREF1V25)}	External output capacitance range after derating	Actual capacitance after derating. ex: 0.27 - μ F capacitance, then use a 0.47 - μ F capacitor with 60% derating at 1.25 V	0.2		1	μF
V _{I(LDO3V)}	LDO3V input	Parametric and functional	5.4	7.4	21	V
V _{I(LDO3V)}	LDO3V input	Functional	3.45	7.4	24	V
V _{O(LDO3V)}	LDO3V output	VIN = 7.4 V, 1mA load	3.267	3.3	3.333	V
I _{O (LDO3V)}	Output current	Maximum current for external user is limited 40mA			40	mA

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Electrical Characteristics: Control (continued)

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
I _{SC (LDO3V)}	Output circuit current limit	Measured at 90% of the regulation voltage	75			mA
Line regulation V _{O(LDO3V)}	Line regulation for regulator over operating voltage range	$\label{eq:VIN} \begin{array}{l} \text{VIN} = 5.4 \text{ V to } 21 \text{ V}, \text{ Measured as} \\ (?V_{O(LDO3V)}/V_{O(LDO3V)}) \text{ over the operating} \\ \text{range with } 20\text{mA load current. measured} \\ \text{at LDO3V pin with respect to AGND pin} \end{array}$			0.5%	
Load regulation V _{O(LDO3V)}	Load regulation for regulator over operating current range	$\label{eq:VIN} \begin{array}{l} \text{VIN} = 7.4 \mbox{ Measured as} \\ (?V_{O(LDO3V)}/V_{O(LDO3V)}) \mbox{ over this operating} \\ range with 0mA to 50mA load current. \\ measured at LDO3V pin with respect to \\ AGND pin \end{array}$			0.5%	
C _{O (LDO3V)}	External output capacitance range after derating	Actual capacitance after derating, for example: 2.7 - μ F capacitance, then use a 4.7 μ F capacitor with 60% derating at 3.3 V	2.2	4.7	10	μF
t _{r (LDO3V)}	Rise time	Measured from 5% to 95% of the output voltage with 2.2 μF	300		450	μs
I/O BUFFER, DD	R_VTT_CTRL					
V _{IL_DDR_VTT_CTR}	DDR_VTT_CTRL input-low voltage	Input-low voltage threshold			0.49	V
V _{IH_DDR_VTT_CTR}	DDR_VTT_CTRL input-high voltage	Input-high voltage threshold	0.61			V
V _{HYST_DDR_VTT_}	DDR_VTT_CTRL hysteresis voltage	Hysteresis voltage		70		mV
l _{leakage_DDR_VTT_} CTRL	DDR_VTT_CTRL input current	Input current, Clamped to 1 V		0.01	0.2	μA
ENVR4, ENVR5, SRAIL_ENIN, INI	V33APCH_ENIN, V18U25U_ENIN,	ENC, V5ADS3_ENIN, VCCIO_ENIN, V33AD	SW ENIN.	SLP SUS		
M				02000		[
_	Input-low voltage				0.4	V
V _{IH_INPUTS}	Input-low voltage Input-high voltage		1.2			V V
V _{IH_INPUTS} V _{HYST_INPUTS}	Input-low voltage Input-high voltage Hysteresis voltage			300	0.4	V V mV
V _{IH_INPUTS} V _{HYST_INPUTS} I _{leakage_INPUTS}	Input-low voltage Input-high voltage Hysteresis voltage Input current	Clamped on 3.3 V			0.4	V V mV µA
VIH_INPUTS VHYST_INPUTS Ileakage_INPUTS VIL_PWRBTNZ	Input-low voltage Input-high voltage Hysteresis voltage	Clamped on 3.3 V Internal 5-kΩ pullup resistor between		300	0.4	V V mV
VIL_PWRBTNZ	Input-low voltage Input-high voltage Hysteresis voltage Input current Input-low voltage for PWRBTNZ	Clamped on 3.3 V	1.2	300	0.4	V V mV µA V
V _{IH_INPUTS} V _{HYST_INPUTS} I _{leakage_INPUTS} V _{IL_PWRBTNZ}	Input-low voltage Input-high voltage Hysteresis voltage Input current Input-low voltage for PWRBTNZ Input-high voltage for PWRBTNZ	Clamped on 3.3 V Internal 5-kΩ pullup resistor between	1.2	300 0.01	0.4	V V mV μΑ V V
VIH_INPUTS VHYST_INPUTS Ileakage_INPUTS VIL_PWRBTNZ VIH_PWRBTNZ VHYST_PWRBTNZ IOutput_PWRBTNZ tec_ONOFF_Debouinc_0	Input-low voltage Input-high voltage Hysteresis voltage Input current Input-low voltage for PWRBTNZ Input-high voltage for PWRBTNZ Hysteresis voltage for PWRBTNZ Output current for PWRBTNZ when power button is pressed to close and pulling PWRBTNZ to	Clamped on 3.3 V Internal 5-kΩ pullup resistor between PWRBTNZ pin and VDDIO PWRBTNZ = GND, Internal 5kΩ pullup resistor between PWRBTNZ pin and	1.2	300 0.01 580	0.4	V V mV μΑ V V mV
VIH_INPUTS VHYST_INPUTS VIL_PWRBTNZ VIL_PWRBTNZ VIH_PWRBTNZ VHYST_PWRBTNZ IOUTPUT_PWRBTNZ IOUTPUT_PWRBTNZ tec_ONOFF_Debouinc_0 e	Input-low voltage Input-high voltage Hysteresis voltage Input current Input-low voltage for PWRBTNZ Input-high voltage for PWRBTNZ Hysteresis voltage for PWRBTNZ Output current for PWRBTNZ when power button is pressed to close and pulling PWRBTNZ to GND EC_ONOFF debounce time, 0-ms	Clamped on 3.3 V Internal 5-kΩ pullup resistor between PWRBTNZ pin and VDDIO PWRBTNZ = GND, Internal 5kΩ pullup resistor between PWRBTNZ pin and VDDIO Time set to 0 ms, Measured from 0.5% PWBTNZ rising to 5% of the EC_ONOFF	1.2	300 0.01 580 660	0.4	V VmV μA V V wV μA
VIH_INPUTS VHYST_INPUTS Ileakage_INPUTS VIL_PWRBTNZ VIH_PWRBTNZ VHYST_PWRBTNZ IOutput_PWRBTNZ tec_onoff_Debouinc_0 e tec_onoff_Debouinc_3 0e	Input-low voltage Input-high voltage Hysteresis voltage Input current Input-low voltage for PWRBTNZ Input-high voltage for PWRBTNZ Hysteresis voltage for PWRBTNZ Output current for PWRBTNZ Output current for PWRBTNZ when power button is pressed to close and pulling PWRBTNZ to GND EC_ONOFF debounce time, 0-ms setting EC_ONOFF debounce time, 30- ms setting	Clamped on 3.3 V Internal 5-kΩ pullup resistor between PWRBTNZ pin and VDDIO PWRBTNZ = GND, Internal 5kΩ pullup resistor between PWRBTNZ pin and VDDIO Time set to 0 ms, Measured from 0.5% PWBTNZ rising to 5% of the EC_ONOFF output Time set to 30 ms, Measured from 0.5% PWBTNZ rising to 5% of the EC_ONOFF	1.2	300 0.01 580 660 0	0.4	V W μA V V mV μA ms
VIH_INPUTS VHYST_INPUTS Ileakage_INPUTS VIL_PWRBTNZ VIH_PWRBTNZ VHYST_PWRBTNZ IOutput_PWRBTNZ tec_onoff_Debouinc_0 e tec_onoff_Debouinc_3 0e	Input-low voltage Input-high voltage Hysteresis voltage Input current Input-low voltage for PWRBTNZ Input-high voltage for PWRBTNZ Hysteresis voltage for PWRBTNZ Output current for PWRBTNZ Output current for PWRBTNZ when power button is pressed to close and pulling PWRBTNZ to GND EC_ONOFF debounce time, 0-ms setting EC_ONOFF debounce time, 30- ms setting	Clamped on 3.3 V Internal 5-kΩ pullup resistor between PWRBTNZ pin and VDDIO PWRBTNZ = GND, Internal 5kΩ pullup resistor between PWRBTNZ pin and VDDIO Time set to 0 ms, Measured from 0.5% PWBTNZ rising to 5% of the EC_ONOFF output Time set to 30 ms, Measured from 0.5% PWBTNZ rising to 5% of the EC_ONOFF output	1.2	300 0.01 580 660 0	0.4	V W μA V V mV μA ms
VIH_INPUTS VHYST_INPUTS Ileakage_INPUTS VIL_PWRBTNZ VIH_PWRBTNZ VHYST_PWRBTNZ IOutput_PWRBTNZ IOutput_PWRBTNZ tec_ONOFF_Debouinc_0 e tec_ONOFF_Debouinc_3 0e VDDIO DOMAIN	Input-low voltage Input-high voltage Hysteresis voltage Input current Input-low voltage for PWRBTNZ Input-high voltage for PWRBTNZ Hysteresis voltage for PWRBTNZ Output current for PWRBTNZ Output current for PWRBTNZ when power button is pressed to close and pulling PWRBTNZ to GND EC_ONOFF debounce time, 0-ms setting EC_ONOFF debounce time, 30- ms setting	Clamped on 3.3 V Internal 5-kΩ pullup resistor between PWRBTNZ pin and VDDIO PWRBTNZ = GND, Internal 5kΩ pullup resistor between PWRBTNZ pin and VDDIO Time set to 0 ms, Measured from 0.5% PWBTNZ rising to 5% of the EC_ONOFF output Time set to 30 ms, Measured from 0.5% PWBTNZ rising to 5% of the EC_ONOFF output Hz, DS3_VREN, PGVR1, PGVR2, PGVR3, F Pulled up to VDDIO pin which should by	1.2	300 0.01 580 660 0 30	0.4	V W μA V V mV μA ms ms

Electrical Characteristics: Control (continued)

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
	N PUSH-PULL OUTPUTS, (V33APC 5ADS3_ENOUT, V33SDSW_ENOUT	H_PG, V18U25U_ENOUT, PGC, VCCIO_EN)	10UT, V33/	APCH_EN	OUT, V1	BS_PG,
V _{PP}	Pullup output voltage supply	Pulled up to VDDPG pin		VDDPG		V
V _{OL_PP}	Low-level output voltage	I _{OL} = 3 mA			0.6	V
V _{OH_PP}	High-level output voltage	I _{OH} = 3 mA	VDDPG - 0.6			V
GENERAL OPE	N-DRAIN OUTPUTS, (<u>ACSWON, BA</u> GD, ALL_SYS_PWRGD, PMIC_INT,	T <u>1SWON, BAT2SWON, VCCST_PWR</u> GD, EC_RST, PCH_PWRBTN, EC_ONOFF, DP	SYS_PWR WROK, V10	OK, PCH_ 05S_PG, F	PWROK, PGVR4, E	C_ACOK
V _{OL_OD1}	OD output voltage	I _{OL} = 2 mA			0.4	V
ILK OD1	OD leakage current	V _(PIN) = 3.3 V			0.45	μA
OPEN-DRAIN O	UTPUT (TEMP_ALERT)					
V _{OL_OD}	Open-drain low level output voltage	I_{OL} = 15 mA, with 75- Ω pullup resistor to 1 V			0.165	V
LK_OD	Open-drain leakage current	$V_{(\text{PIN})}$ = 3.3 V, with 75- Ω pullup resistor to 1 V			0.35	μA
TRISTATE INPU	T BUFFER (SLAVEADDR, DDRID)					
V _{IL_TRISTATE}	Low-level input voltage	$I_{OL} = 6 \ \mu A$			0.33	۷
VIH_TRISTATE	High-level input voltage	I _{OH} = 6 μA	1.8			V
ITRISTATE	ITRISTATE CURRENT	Maximum allowable current in or out of pin when floating to maintain FLOAT logic state	-0.650		0.675	μA
TRISTATE_TOTAL_ PIN_GND	Total current drawn when pin connected to GND	VINLDO3 current when TRISTATE pin = GND			6	μA
TRISTATE_TOTAL_ PIN_3.3V	Total current drawn when pin connected to 3.3 V	VINLDO3 current when TRISTATE pin = LDO3V = 3.3 V			6	μA
ITRISTATE_TOTAL_ PIN_FLOAT	Total current drawn when pin floating	VINLDO3 current when TRISTATE pin = Floating			4.5	μΑ
EXTERNAL RAI INH)	L POWER GOOD COMPARATORS	(V33APCH, V18U25U, VSC, V5ADS3, VCC	IO, V33AD	SW, V33S	, V18S, V	105S,
	VSx input voltage range	When VSx configured as voltage sense input	0.7		5	۷
	VSx input leakage current	When VSx configured as voltage sense input, VSx = 5.7V	0		9	μA
	Power-good exit threshold high, VSx	VSx rising out of power-good. When VSx configured as voltage sense input and power-good window comparator.	106%	108%	110%	
	Power-good threshold high, VSx hysteresis	VSx falling into power-good. When VSx configured as voltage sense input and power-good window comparator.		-3%		
	Power-good exit threshold low, VSx	VSx falling out of power-good. When VSx configured as voltage sense input and power-good window comparator.	90%	92%	94%	
	Power-good threshold low, VSx hystersis	VSx rising into power-good. When VSx configured as voltage sense input and power-good window comparator.		3%		
T _{VSX_} POWERGOO D_DEGLITCH	Power-good deglitch time for both rising and falling edges	VSx voltage must cross power-good threshold and stay for at least this time to change power-good output state.Measured from VSx into or out of power-good threshold, until PGx toggles, for both rising and falling edges.	27	30	33	μs

5.6 Electrical Characteristics: Embedded Controller Reset

Over recommended free-air temperature range and over recommended input voltage range (typical at an ambient temperature range of 25°C) (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
V _{OL_OD}	EC_RST output-low voltage	$I_{OL} = 2 \text{ mA}, V_{EC_{RST}} = 3.3 \text{ V}$			0.4	V
I _{LKG_OD}	EC_RST leakage current	Output buffer in open-drain mode, $V_{EC_{RST}} = 3.3 \text{ V}$		0.01	0.2	μA
		Reset-timer register value: 00b		20		
+	EC RST time duration	Reset-timer register value: 01b		40		m 0
t _{RST}		Reset-timer register value: 10b		80		ms
L		Reset-timer register value: 11b (default		200		
I _{LK}	ECVCC input quiescent current				3	μA
	Reset-voltage threshold register value: 000b	1.344	1.4	1.456		
		Reset-voltage threshold register value: 001b	1.44	1.5	1.56	
		Reset-voltage threshold register value: 010b	1.536	1.6	1.664	
V		Reset-voltage threshold register value: 011b	1.632	1.7	1.768	V
V _{TH}	ECVCC voltage threshold	Reset-voltage threshold register value: 100b	2.304	2.4	2.496	v
		Reset-voltage threshold register value: 101b	2.496	2.6	2.704	
l		Reset-voltage threshold register value: 110b	2.688	2.8	2.912	
		Reset-voltage threshold register value: 111b	2.88	3.0	3.12	

5.7 Electrical Characteristics: Power-Path Comparators and Critical Supply Voltage

	PARAMETER	TEST CONDITIONS	MIN	ТҮР	MAX	UNIT
ACIN, BAT1,	BAT2, VDCSNS					
	Output-low saturation voltage for open-drain logic output pin (TRIP)	Comparator input voltage > internal reference voltage, Output pulling low, Sink current = 5 mA			0.5	V
	Internal current source, IOUT VCOMP	Current out of the VCOMP pin when IOUT VCOMP enabled	9.5	10	10.6	μΑ
	Internal reference voltage, VREF_VCOMP_rising	Rising voltage at VCOMP pin, changes TRIP to logic low	1.211	1.223	1.235	V
	Internal hysteresis voltage, VHYST VCOMPFalling	Falling voltage at VCOMP pin, changes TRIP to logic high		61		mV
	Output-low saturation voltage for open-drain logic output pin (ACSWON, BAT1SWON, BAT2SWON)	Comparator input voltage > internal reference voltage, Output pulling low, Sink current = 5 mA			0.5	V
I _{LKG}	ACIN, BAT1, BAT2 - Current leakage	Current into the ACIN, BAT1, or BAT2 pins from 5.4 V to 24 V (when pin is below, at, or above 6V internal protection switch.)			0.1	μΑ
V _{REF_PP}	Internal reference voltage, VREF_ACIN_rising	Rising voltage at ACIN pin, makes ACSWON trigger low	1.2365	1.25	1.2645	V
V _{HYST_PP}	Internal hysteresis voltage, VHYST_ACIN_falling	Falling voltage with respect to <u>VREF_ACIN</u> at ACIN pin, makes ACSWON trigger high		125		mV

Electrical Characteristics: Power-Path Comparators and Critical Supply Voltage (continued)

Over recommended free-air temperature range and over recommended input voltage range (typical at an ambient temperature range of 25°C) (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
V _{REF_PP}	Internal reference voltage, VREF_BAT1_rising	Rising voltage at BAT1 pin, makes BAT1SWON trigger low	1.2365	1.25	1.2645	V
V _{HYST_PP}	Internal hysteresis voltage, VHYST_BAT1_falling	Falling voltage with respect to VREF_BAT1 at BAT1 pin, makes BAT1SWON trigger high		125		mV
V _{REF_PP}	Internal reference voltage, VREF_BAT2_rising	Rising voltage at BAT2 pin, makes BAT2SWON trigger low	1.2365	1.25	1.2645	V
V _{HYST_PP}	Internal hysteresis voltage, VHYST_BAT2_falling	Falling voltage with respect to VREF_BAT2 at BAT1 pin, makes BAT2SWON trigger high		125		mV
	Critical supply voltage (VDCSNS) falling threshold	Critical supply voltage threshold register value VDLMTCRT[3:0] = 0101b, Supply voltage decreasing. With a resistor divider from VDC to VDCSNS with 4R top, R bottom, VDC = 6 V when VDCSNS pin = 1.12 V.	1.10	1.12	1.14	V
	Critical supply voltage (VDCSNS) rising threshold hysteresis	Supply voltage increasing, With a resistor divider from VDC to VDCSNS with 4R top, R bottom, VDC_hyst = 100 mV when VDCSNS_hyst pin = 20 mV		20		mV
	Critical supply voltage (VDCSNS) input current	VDCSNS = 1.2 V to 1.75 V		0.01	0.1	μA
INTERNAL RAM	P COMPARATOR					
Vramp_comp_V IN_rising	Rising voltage at VIN pin, makes internal ramp compensation of all controllers slightly smaller		10.5	11	11.5	V
Vramp_comp_V IN_falling_hyst	Falling voltage hysteresis at VIN pin, makes the internal ramp compensation of all controllers slightly bigger			1.1		V

5.8 Electrical Characteristics: AC-Adapter Detection

	PARAMETER	TEST CONDITIONS	MIN	ТҮР	MAX	UNIT
V _{IL}	ACOK input-low voltage				0.4	V
V _{IH}	ACOK input-high voltage		1.2			V
	ACOK input current	ACOK = 3.3 V		0.01	0.1	μA
		ACOKDB register value: 00b	50	61	95	μs
		ACOKDB register value: 01b	7	10	13	
	Adapter detection debounce time	ACOKDB register value: 10b	15	20	25	ms
		ACOKDB register value: 11b (default)	24	30	36	

5.9 Electrical Characteristics: Emergency Reset Shutdown

Over recommended free-air temperature range and over recommended input voltage range (typical at an ambient temperature range of 25°C) (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN	ТҮР	MAX	UNIT
t _{UVLO_shutdown}	UVLO low shutdown time	Time from VIN < UVLO5 low threshold until shutdown			1	μs
t _{shutdown} _shutdown	SHUTDOWN low shutdown time	Time from SHUTDOWN pin falling-edge until shut down.			1	μs
t _{PWRGD_Fault_shut} down	PWRGD fault shutdown time	Time from PWRGD fault detected including deglitch time until shut down. Output voltage is overvoltage or undervoltage	27	30	33	μs
t _{CRIT_Temp_shutdo} wn	CRITICAL temperature high shutdown time	Time from $T_J > T_{CRIT_Temp}$ including deglitch time until shut down, Deglitch time can be changed from 5 µs to 300 µs			5	μs
t _{SDWNCTRL_bit_shu} tdown	SDWNCTRL bit set to 1 shutdown time	Time from SDWNCTRL register (0x49) bit 0 set to 1b until shutdown, Time after SDWNCTRL register is written to by I ² C			1	μs

5.10 Electrical Characteristics: Voltage Regulators (VR1, VR3, VR4, VR5)

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
GENERAL						
M		Parametric and functional	5.4	7.4	21	V
V _{IN}	Input voltage	Functional	5.4	7.4	24	v
t _{SS_total}	Soft-Start total turnon time (start- up time + output ramp-up time)	Time to start switching from enable to 95% of V_{OUT} , Continuous slope (no slope reversal)	770	876	1000	μs
t _{SS_delay}	Soft-start delay time	Delay time from enable to first switching pulse	120	136	150	μs
t _{SS}	Soft-start ramp-up time	From first switching pulse to 95% of $V_{\text{OUT}},$ Continuous slope (no slope reversal)	650	740	850	μs
$SS_{PG_{Mask}}$	Power-good mask time during & after soft-start ramp-up time		9	10	11	ms
PG _{Threshold}	Power-good exit threshold	Percentage of nominal VOUT	±5.5%	±8%	±10.5%	
PG _{HYS}	Power-good hysteresis	Percentage of nominal VOUT		3%		
PG _{deglitch}	Power-good deglitch time	Time measured from FBVRxP crossing power good threshold to PGVRx toggling\ (for both rising and falling edges)	27	30	33	μs
DRVH _{Rout_H}	DRVH resistance, high	Source, IDRVH = -50 mA		3.0	4.5	Ω
DRVH _{Rout_L}	DRVH resistance, low	Sink, IDRVH = 50 mA		2.0	3.5	Ω
DRVL _{Rout_H}	DRVL resistance, high	Source, IDRVL = -50 mA		3.0	4.5	Ω
DRVL _{Rout_L}	DRVL resistance, low	Sink, IDRVL = 50 mA		0.8	2.0	Ω
t _{dead_fall}	Dead time, fall	DRVH off to DRVL on		10		ns
t _{dead_rise}	Dead time, rise	DRVL off to DRVH on		20		ns
t _{ON_min}	High-side driver minimum on-time	DRVH on	65	80	105	ns
t _{OFF_min}	High-side driver minimum off-time	DRVH off	235	260	285	ns
Force_PWM _{PWM}	Time that PWM is forced to remain on once zero crossing comparator detects PWM to PFM transition	Cycles is the number of pulses on the switch node	16	16	16	cycles
CURRENT LIMIT	•					
I _{TRIP}	Current limit pin source current	T _A = 25°C	45	50	55	μA
TC _{ILIM_LS}	External low-side FET R _{DSon} current limit temperature coefficient	T _A = 25°C		4780		ppm/°C

Electrical Characteristics: Voltage Regulators (VR1, VR3, VR4, VR5) (continued)

	PARAMETER	TEST CONDITIONS	MIN	ТҮР	MAX	UNIT
TC _{ILIM_HS}	External high-side FET R _{DSon} current limit temperature coefficient	T _A = 25°C		3300		ppm/°C
V _{ILIM}	Current-limit pin setting voltage range	$V_{ILIM} = R_{CS} \times I_{TRIP}$ (usable voltage range across the operating temperature range)	0.2		2	V
DVS AND DECA	Y					
t _{DVS_total}	DVS total fall and rise time (delay time + output ramp time)	Time to start switching from enable to 5% of V_{OUT} , Continuous slope (no slope reversal), For V_{OUT} change = 300 mV	56	61.25	68.5	μs
t _{DVS_delay}	DVS delay time for falling and rising edge	DVS delay time from when STANDBY changes from High to Low, until the output voltage begins to fall.	1	1.25	1.5	μs
t _{DVS_ramp}	DVS ramp time for falling and rising edge	From first switching pulse to 5% of V _{OUT} , Continuous slope (no slope reversal), Total ramp time = ((V _{OUT} - V _{OUT} change) / slew rate), For V _{OUT} change = 300 mV	55	60	67	μs
DVS _{slew rate}	DVS slew rate for falling and rising edge	DVS falling edge slew rate for V_{OUT} to change from the upper target to the lower target after STANDBY (SLP_S0) changes from high to low	4.5	5	5.5	mV/μs
t _{decay_total}	Decay exit total turnon time (delay time + output ramp-up time)	time to start switching from enable to 95% of V _{OUT} , Continuous slope (no slope reversal). For V _{OUT} target = 0.95 V	69	79	99	μs
t _{decay_delay}	Decay exit delay time for rising edge	Decay delay time from when STANDBY changes from low to high, until the output voltage begins to rise.	10	12	16	μs
t _{decay_ramp}	Decay exit ramp time for rising edge	From first switching pulse to 95% of V _{OUT} , Continuous slope (no slope reversal). Total ramp time = $((V_{OUT} - 0 V) / slew$ rate). For V _{OUT} target = 0.95 V	59	67	83	μs
Exit Decay _{slew} rate	Decay exit slew rate for rising edge	Decay rising edge slew rate for V_{OUT} to change from the lower target to the upper target after STANDBY changes from low to high	12	15	17	μs
DVS _{PG_Mask}	Power good mask time during DVS ramp		t _{DVS_ram} p + 90	t _{DVS_ram} p + 100	t _{DVS_ram} _p + 110	μs
Force_PWM _{DVS}	Time that PWM is forced to remain on after DVS ramp		t _{DVS_ram} p + 9	t _{DVS_ram} p+ 10	t _{DVS_ram} p + 11	μs
OUTPUT DISCH	ARGE		1			
		Discharge register value: 00b (default)	1000			kΩ
R _{VRdis}	Output auto discharge resistance	Discharge register value: 01b	90	125	160	
··vrais		Discharge register value: 10b	170	225	315	Ω
		Discharge register value: 11b	450	550	690	
FB _{Rin}	Controller feedback input resistance	Controller enabled		1	2.25	MΩ
R _{internal_Boot}	Bootstrap internal-switch on resistance (R _{DSon})	$-40^{\circ}\text{C} = \text{T}_{\text{A}} = 125^{\circ}\text{C}$		15	25	Ω
VR1 CONTROLI	ER					
V _{OUT}	Output voltage	Power-save mode disabled (STANDBY = high, and V105ACNT[5:4] = 00b [default])		1.05		V
	VR1 maximum line regulation	With respect to nominal V _{OUT} ULQ/auto mode, V _{VIN} = 5.4 V to 21 V, I_{OUT} = 6 A	-0.5%		0.5%	

Electrical Characteristics: Voltage Regulators (VR1, VR3, VR4, VR5) (continued)

	PARAMETER	TEST CONDITIONS	MIN	ΤΥΡ	MAX	UNIT
	VR1 maximum load regulation	With respect to nominal V_{OUT} ULQ/auto mode, V_{VIN} = 7.4 V, I_{OUT} = 0 A to 10 A,	-0.5%		0.61%	
	VR1 switching frequency	V_{IN} = 7.4 V, PWM mode (\overline{NVDC} = 3.3 V = programmed to low switching frequency)		625		kHz
	VET Switching nequency	V_{IN} = 7.4 V, PWM mode (\overline{NVDC} = GND = programmed to high switching frequency)		1000		kHz
VR3 CONT	ROLLER					
V _{OUT}	Output voltage	Power-save mode disabled (STANDBY = high, and VCCIOCNT[5:4] = 00b [default])		3.3		V
	VR3 maximum line regulation	With respect to nominal V _{OUT} ULQ/auto mode, V _{VIN} = 5.4 V to 21 V, I _{OUT} = 6 A	-0.5%		0.65%	
	VR3 maximum load regulation	With respect to nominal V_{OUT} ULQ/auto mode, V_{VIN} = 7.4 V, I_{OUT} = 0 A to 10 A	-0.5%		0.55%	
	VR3 switching frequency	V_{IN} = 7.4 V, PWM mode (\overline{NVDC} = 3.3 V = programmed to low switching frequency)		625		kHz
	VITO Switching nequency	$_{\rm IN}$ = 7.4 V, PWM mode ($\overline{\rm NVDC}$ = GND = programmed to high switching frequency)		1000		kHz
VR4 CONT	ROLLER					
		Power-save mode disabled (DDR_VTT_CTRL = low, and V12UCNT[5:4] = 00b)		1.2		
V _{OUT}	Output voltage	Power-save mode disabled (DDR_VTT_CTRL = high, and V12UCNT[5:4] = 00b)		1.35		V
		Power-save mode disabled (DDR_VTT_CTRL = float, and V12UCNT[5:4] = 00b)		1.1		
	VR4 maximum line regulation	With respect to nominal V _{OUT} ULQ/auto mode, V _{VIN} = 5.4 V to 21 V, I _{OUT} = 6 A	-0.5%		0.5%	
	VR4 maximum load regulation	With respect to nominal V_{OUT} ULQ/auto mode, V_{VIN} = 7.4 V, I_{OUT} = 0 A to 10 A	-0.5%		0.65%	
	VR4 switching frequency	V_{IN} = 7.4 V, PWM mode (\overline{NVDC} = 3.3 V = programmed to low switching frequency)		625		kHz
	Vita switching nequency	V_{IN} = 7.4 V, PWM mode (\overline{NVDC} = GND = programmed to high switching frequency)		1000		kHz
VR5 CONT	ROLLER					
V _{OUT}	Output voltage	Power-save mode disabled (STANDBY = high, and VPRIMCORECNT[5:4] = 00b)		1.05		V
	VR5 maximum line regulation	With respect to nominal V _{OUT} ULQ/auto mode, V _{VIN} = 5.4 V to 21 V, I _{OUT} = 6 A	-0.5%		1.05%	
	VR5 maximum load regulation	With respect to nominal V _{OUT} ULQ/auto mode, V _{VIN} = 7.4 V, I _{OUT} = 0 A to 10 A	-0.5%		0.75%	
	VR5 switching frequency	V_{IN} = 7.4 V, PWM mode (NVDC = 3.3 V = programmed to low switching frequency)		625		kHz
	Vito Switching Requercy	V_{IN} = 7.4 V, PWM Mode (\overline{NVDC} = GND = programmed to high switching frequency)		1000		kHz

5.11 Electrical Characteristics: VR2 Converter

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
POWER						
V _{IN}	V _{VINVR2} power input voltage	Parametric and functional, V_{VIN} = 5.4 V to 21 V	3.135	3.3	3.465	V
		Functional, $V_{VIN} = 5.4 V$ to 24 V	2.97	3.3	3.63	
V _{OUT}	Output voltage	Power-save mode disabled (STANDBY = high and V18ACNT[5:4] = 10b)		1.8		V
I _{OUT}	Maximum average output current range	V _{VINVR2} = 2.97 V to 3.63 V	2500			mA
I _{LIM}	Low-side valley cycle-by-cycle positive current limit	V _{VINVR2} = 2.97 V to 3.63 V	2260		3360	mA
I _{nLIM}	Low-side valley cycle-by-cycle negative current limit	V _{VINVR2} = 2.97 V to 3.63 V	1400		1875	mA
HS_R _{DSon}	High-side switch on resistance	V_{VINVR2} = 3.3 V, 100% duty cycle	30		105	mO
LS_R _{DSon}	Low-side switch on resistance	V_{VINVR2} = 3.3 V, 0% duty cycle	30		95	mO
	Maximum line regulation	With respect to nominal V _{OUT} ULQ/auto mode, V _{VINVR2} = 2.97 V to 3.63 V, I _{OUT} = I _{max} , All output voltages, Measured at the regulation point output capacitor with Kelvin connections made directly from the regulation point to the differential feedback pins (FBVR2P – FBVR2N).	-0.5%		0.5%	
	Movimum load regulation	PWM mode with respect to nominal V_{OUT} ULQ/auto mode, $V_{VINVR2} = 2.97$ V to 3.63 V, $I_{OUT} = 0$ A to I_{max} . All output voltages, Measured at the regulation point output capacitor with Kelvin connections made directly from the regulation point to the differential feedback pins (FBVR2P – FBVR2N).	-0.5%		0.5%	
	Maximum load regulation	AUTO mode with respect to nominal V _{OUT} ULQ/auto Mode, V _{VINVR2} = 2.97 V to 3.63 V, I _{OUT} = 0 A to I _{max} . All output voltages, Measured at the regulation point output capacitor with Kelvin connections made directly from the regulation point to the differential feedback pins (FBVR2P – FBVR2N).	-0.65%		1%	
f _{SW}	Switching frequency	PWM mode, I _{OUT} = 2 A	1700	2000	2300	KHz
t _{on}	Soft-Start total turnon time (start- up time + output ramp-up time)	Time to start switching from enable to 95% of $V_{O(min)}$. Continuous slope (no slope reversal)	730	800	1050	μs
t _{delay}	Enable delay time	Delay time from enable to first switching pulse.	120	135	150	μs
t _{SS}	Soft-Start ramp-up time	From first switching pulse to 95% of $V_{O(\text{min})},$ Continuous slope (no slope reversal)	610	665	900	μs
SS _{PG_Mask}	Power-good mask time during and after soft-start ramp-up time		9	10	11	ms
t _{DVS_total}	DVS total fall and rise time (delay time + output ramp time)	Time to start switching from enable to 5% of V_{OUT} , Continuous slope (no slope reversal), For V_{OUT} change = 300 mV)	56	61.25	68.5	μs
t _{DVS_delay}	DVS delay time for falling and rising edge	DVS delay time from when STANDBY changes from high to Low, until the output voltage begins to fall	1	1.25	1.5	μs

Electrical Characteristics: VR2 Converter (continued)

	PARAMETER	TEST CONDITIONS	MIN	ТҮР	MAX	UNIT
t _{DVS_ramp}	DVS ramp time for falling and rising edge	From first switching pulse to 5% of V _{OUT} , Continuous slope (no slope reversal), Total ramp time = ([V _{OUT} - V _{OUT} change] / slew rate). For V _{OUT} change = 300 mV	55	60	67	μs
DVS _{slew rate}	DVS slew rate for falling and rising edge	DVS falling edge slew rate for V_{OUT} to change from the upper target to the lower target after STANDBY (SLP_S0) changes from high to low.	4.5	5	5.5	mV/µs
$DVS_{PG_{Mask}}$	Power-good mask time during DVS ramp		t _{DVS_ram} p + 90	t _{DVS_ram} _p + 100	t _{DVS_ram} _p + 110	μs
Forced_PWM _{DV}	Time that PWM is forced to remain on after DVS ramp		t _{DVS_ram} p + 9	t _{DVS_ram} p+ 10	t _{DVS_ram} p + 11	μs
		Discharge register value, DISCHGCNT3[7:6] = 00b	250	860	1450	kΩ
P	Output outo discharge registeres	Discharge register value, DISCHGCNT3[7:6] = 01b	80	100	120	
R _{VRdis}	Output auto discharge resistance	Discharge register value, DISCHGCNT3[7:6] = 10b	160	200	240	Ω
		Discharge register value, DISCHGCNT3[7:6] = 11b (default)	400	500	600	
FB _{Rin}	Feedback input resistance	Enabled			3	MΩ
Iq_VR2 _{LDO3V} _vregvr2	Quiescent current on LDO3V and VREGVR2 with converter when enabled	$I_{OUT} = 0$ mA, enabled, at $T_A=25^{\circ}$ C, Not switching, Measured at LDO3V, VREGVR2		30	55	μA
I _{SD}	Shutdown current into VIN, Currents from LDO3V, VREGVR2 and 1V25 supplies	V_{VINVR2} = 3.63 V, disabled, at T _A = 25°C			3	μA
CONTROL						
PG _{Threshold}	Power-good exit threshold	Percentage of nominal VOUT	±5.5%	±8%	±10.5%	
PG _{HYS}	Power-good hysteresis	Percentage of nominal V _{OUT}		3%		
PG _{deglitch}	Power-good deglitch time	Time measured from FBVRxP crossing power-good threshold to PGVRx toggling (for both rising and falling edges)	27	30	33	μs
T _{HOT}	Overtemperature protection Hot Warning		120		140	°C
T _{HOT_hys}	Overtemperature hysteresis Hot Warning			10		°C
T _{SHUTDOWN}	Overtemperature protection Shutdown		130		160	°C
T _{SHUTDOWN_hys}	Overtemperature hysteresis Shutdown			10		°C

5.12 Electrical Characteristics: LDO1 Regulator

	PARAMETER	TEST CONDITIONS	MIN	ТҮР	MAX	UNIT
POWER		•				
		DDRID = 0 V, VOUTLDO1 = (VINLDO1S) / 2, VINLDO1S = 1.2 V		0.6		
V _{OUT}	Output voltage	DDRID = 3.3 V, VOUTLDO1 = (VINLDO1S) / 2, VINLDO1S = 1.35 V		0.675		V
		DDRID = Open, VOUTLDO1 = (VINLDO1S) / 2, VINLDO1S = 1.1 V		0.55		
V _{OUT_Trans}	Output voltage tolerance, AC and DC transient load	$\begin{split} I_{OUT} = 1 \text{ A, VINLDO1} = 1.2 \text{ V, (FBLDO1} - \\ FBVR4N) = \text{Output voltage relative to} \\ (VINLDO1S - FBVR4N) / 2, where \\ VINLDO1S connected to FBVR4P on the \\ board, Load transient from 0 mA to 70% \times \\ 1 \text{ A, dI/dt} = 2.5 \text{ A/} \mu \text{s} \end{split}$	-30		30	mV
I _{Leak}	Leakage current	$T_A = 25^{\circ}C$, VIN13 = 1.2 V, LDO1 disabled			5	μΑ
I _{Bias}	Bias current at VINLDO1S	$T_A = 25^{\circ}C$, Bias current measured when VINLDO1S is at 1.2 V			40	μA
VLDO1 _{Max_Load}	Sink and source load current	Maximum current sink or source from LDO without exceeding load regulation	1000			mA
VLDO1 _{SC_Limit}	Sink and source short-circuit current limit	Measured when $V_{OUT} = (1.1 \# \text{ nominal} V_{OUT})$ for source. Measured when $V_{OUT} = (0.9 \times \text{ nominal} V_{OUT})$ for source	2000			mA
VLDO1 _{Load_Reg}	Maximum load regulation	V_{VIN} = 1.1 V, 1.2 V and 1.35 V, I_{OUT} = 0 A to 1 A	-4.5%		4.5%	
t _{on}	Total turnon time (enable + ramp)	Measure from LDO enable to V_{OUT} stable, Time to ramp from 0.3 V to $V_{O(min)}$. Continuous slope (no slope reversal). Assumes V_{VIN} is present, with 2 22-µF output capacitors			35	μs
C _{OUT}	External output capacitor	Minimum actual capacitance after derating	38			μF
C _{IN}	External input capacitor	Minimum actual capacitance after derating	8			μF
R _{LDO1dis}	Output auto-discharge resistance	Discharge register value: 0b	1000			kΩ
R _{LDO1dis}	Output auto-discharge resistance	Discharge register value: 1b	60	80	100	Ω
FB _{Rin}	FBLDO1 input impedance	LDO1 Enabled	20	25		MΩ
I _{Q(VIN)}	Quiescent current into VINLDO1	VINLDO1 = 1.35 V, I_{LDO1} = 0 mA, LDO1 enabled		3.5	5	μA
I _{Q(LDO3V)}	Quiescent current from 3.3-V reference LDO when LDO1 is enabled	V _{VINLDO1} = 1.35 V, Enabled			250	μΑ
CONTROL						
PG _{Threshold}	Power-good exit threshold	Percentage of nominal V _{OUT}	±8%	±10%	±12%	
PG _{HYS}	Power-good hysteresis	Percentage of nominal VOUT		±5%		
PG _{deglitch}	Power-good deglitch time	Time measured from FBLDO1 crossing power good threshold to PG for LDO1 toggling. (for both rising and falling edges)	27	30	33	μs
OVP _{temp}	Overtemperature protection		130	145	160	°C
OVP _{hys}	Overtemperature hysteresis			10		°C

5.13 Electrical Characteristics: Input Power Source Detection

Over recommended free-air temperature range and over recommended input voltage range (typical at an ambient temperature range of 25°C) (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN	ТҮР	MAX	UNIT
AC-ADAPTER	DETECTION					
V _{IL}	ACOK input-low voltage				0.4	V
V _{IH}	ACOK input-high voltage		1.2			V
	ACOK input current	ACOK = 3.3 V		0.01	0.1	μA
		ACOKDB register value: 00b	50	61	95	μs
	Adapter detection dehauses time	ACOKDB register value: 01b	7	10	13	
	Adapter detection debounce time	ACOKDB register value: 10b	15	20	25	ms
		ACOKDB register value: 11b	24	30	36	
POWER MONI V)	TORING (1-Hz CLOCK TO 1-Hz CLOC	CK - PULLED UP TO ECVCC INTERNAL P	ULLUP RA	IL = ECVC	C = 1.8	/ OR 3.3
	Clock frequency (1)		0.8	1	1.2	Hz
	Duty cycle			50%		
V _{PP}	Pullup output voltage supply	Pulled up to ECVCC pin which should be tied to 3.3-V LDO3V pin, can also have EC_VCC pullup to 1.8 V instead of 3.3 V		EC_VC C		V
V _{OL_PP}	Low-level output voltage	I _{OL} = 3 mA			0.66	V
V _{OH_PP}	High-level output voltage	I _{OH} = 3 mA	EC_VC C - 0.66			V
COIN-CELL SE	LECTOR	•				
V _{3v1LDO}	3V1 LDO RTC regulation voltage	VDCIN > UVLO, LDO3V and LDO5V on, Measured at the V3P3A_RTC pin with respect to AGND. Place a 1- μ F capacitor at V3P3A_RTC. (Do not exceed 2- μ F actual capacitance).	3	3.1	3.2	V
I _{3v1LDO}	Maximum 3V1 LDO RTC output current	Maximum output current out of 3V3RTC.			1	mA
I _{Q_bkup_no_} VIN	VBATTBKUP quiescent current, when no adapter and no main battery connected to system, automatically VBATTBKUP internally selected. internal 3.1-V LDO automatically off	V_{VDC} < UVLO, V_{BBC} = 2 V to 3 V, V_{VDC} = 0 V		0.03	0.45	μΑ
I _{Q_bkup_with_VIN}	VBATTBKUP quiescent current, when adapter or main battery connected to system, automatically VBATTBKUP internally not selected, internal 3.1-V LDO automatically on and selected.	V_{VDC} > UVLO, V_{BBC} = 2 V to 3 V, V_{VDC} = 7.4 V		0.15	0.85	μΑ
R _{ext_bkup}	External resistor in series with backup battery	Place between backup battery and VBATTBKUP pin, for limiting current out of backup battery		1		kΩ

(1) All values referred to V_{IH} min and V_{IH} maximum levels.

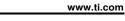
5.14 Electrical Characteristics: I²C Interface

Over recommended free-air temperature range and over recommended input voltage range (typical at an ambient temperature range of 25°C) (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN	ТҮР	MAX	UNIT
V _{IL}	SDA, SCL input-low voltage				0.4	V
V _{IH}	SDA, SCL input-high voltage		1.2			V
	SDA, SCL input current	Clamped on 3.3 V		0.01	0.3	μA
	SDA output-low voltage	$I_{SDA} = 5 \text{ mA}$ (using a 354- Ω or larger external pullup resistor)		0.04	0.4	V
Cb	Capacitive load for SDA and SCL				400	pF

5.15 Timing Requirements

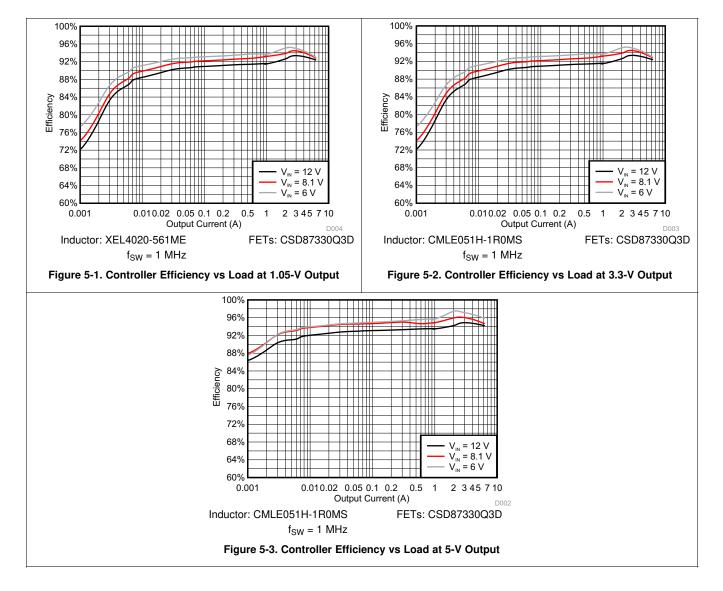
			MIN	NOM	MAX	UNIT
I ² C INTE	RFACE					
t _{I2C_Rdy}	Minimum time for I2C to be ready after VIN > UVLO5V rising	Time after VIN rising above > $V_{UVLO_{5V} Main} + V_{Hys_{5V} Main}$ until OTP is loaded and I2C is ready to communicate			1	ms
		Standard-mode			100	
f _(SCL)	SCL clock frequency	Fast-mode			400	kHz
		Fast-mode Plus			1000	
		Standard-mode	4.7			
t _{BUF}	Bus free time between a STOP and START condition	Fast-mode	1.3			μs
		Fast-mode Plus	0.5			
		Standard-mode	4			μs
t _{HD;} sta	Hold time (repeated) START condition	Fast-mode	600			ns
		Fast-mode Plus	260			ns
		Standard-mode	4.7			μs
	Setup time for a repeated START condition	Fast-mode	600			ns
		Fast-mode Plus	260			ns
	Data setup time	Standard-mode	250			
t _{SU; DAT}		Fast-mode	100			ns
		Fast-mode Plus	50			
		Standard-mode	0		3.45	μs
t _{hd; dat}	Data hold time	Fast-mode	0		0.9	μs
		Fast-mode Plus	0			ns
		Standard-mode			1000	
t _{rCL}	Rise time of SCL signal	Fast-mode	20		300	ns
		Fast-mode Plus			120	
		Standard-mode (using a 2.95 k Ω or smaller external pullup resistor)			1000	
t _{rDA}	Rise time of SDA signal	Fast-mode (using an 885 Ω or smaller external pullup resistor)	20		300	ns
		Fast-mode Plus (using a 354 Ω or smaller external pullup resistor)			120	
		Standard-mode			300	
t _{fDA}	Fall time of SDA signal	Fast-mode	20 x (V _{DD} / 5.5 V)		300	ns
		Fast-mode Plus	20 x (V _{DD} / 5.5 V)		120	
		Standard-mode	4			μs
t _{su; sто}	Setup time for STOP condition	Fast-mode	600			ns
		Fast-mode Plus	260			ns



Texas

NSTRUMENTS

5.16 Typical Characteristics





6 Detailed Description

6.1 Overview

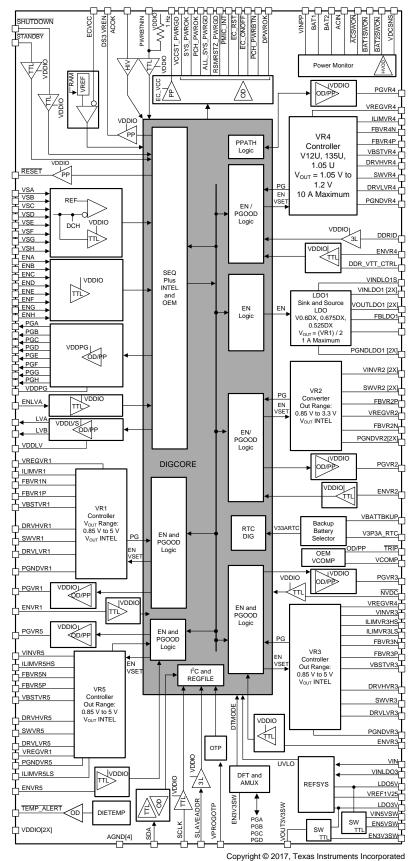
The TPS650932 device is a single-chip solution PMIC designed specifically for the latest Intel processors targeted for tablets, ultrabooks, and notebooks with NVDC or non-NVDC power architectures, using 2S, 3S Lithium-Ion battery packs.

The TPS650932 device can provide a power solution based on the Intel reference designs. Five highly efficient, step-down voltage regulators (VRs), a sink-source LDO, and power-up sequence logic that manages the external load switches are used to provide the proper power rails, sequencing, and protection, including DDR3 and DDR4 memory power. The regulators support dynamic-voltage scaling (DVS) for maximum efficiency including connected standby. The high-frequency voltage regulators use small inductors and capacitors to achieve a small solution size. Output power is adjustable on four VR controllers. An I²C interface allows simple control by the embedded controller (EC). The device is available in a 7-mm by 7-mm nFBGA packagewhich can be used in Type-4 PCB boards for the smallest area implementation

The power-good comparator logic allows controlling and monitoring of up to eight external load switches within the sequence. All the VRs and load-switch power good signals are used in the power-good tree to determine the system-level power goods including the ALL_SYS_PWRGD pin. Enable inputs allow connecting externally to set the sequence, and it also allows using various sleep-mode state signals. The STANDBY state allows entering a deep sleep mode, in which the output voltages of the voltage regulators can be reduced to save power by DVS.

The power monitoring comparators are used to detect and monitor up to three input power sources (adapter, battery1, battery2, or any other combination). Overtemperature detection of the PMIC self-protects, and outputs a status output, TEMPALERTZ. A dedicated comparator also monitors system overtemperature conditions with multiple stacked PTC thermistors, or an NTC thermistor. The PMIC automatically switches between an internal 3.1-V LDO when a power source is connected; or to a backup battery (coin cell) when all power sources are removed. This output RTC rail is used to maintain the always-on RTC rails for critical register data.

6.2 Functional Block Diagram





6.3 Feature Description

6.3.1 Converters

The PMIC has five built-in DC-DC converters. The voltage regulators are highly configurable with regard to voltage and current. Of the five voltage regulators, four voltage regulators have an external power stage with a programmable current limit (programmed by an external resistor). This programmable current limit allows for optimal selection of external passive components based on the desired system load. VR2 has a completely integrated power stage, except for the required passive components. To maintain high efficiency, the converters are implemented as synchronous step-down converters.

One additional voltage regulator is a low dropout (LDO) linear regulator is integrated as part of the PMIC. The LDO1 regulator is capable of sinking and sourcing current that regulates from the step-down controller (for DDR memory). This LDO regulator is designed to specifically provide the VTT power to DDR memory. The LDO1 output voltage tracks the output voltage of the step-down controller and is set to regulate to half of the voltage of the step-down controller voltage.

6.3.1.1 Power-Save Mode

At medium and heavy loads, the converter and the controllers operate in pulse-width modulation (PWM) mode. As soon as the inductor current becomes discontinuous, which indicates that the output current is lower than half of the inductor ripple current, the converters enter power-save mode. In power-save mode, the switching frequency decreases linearly with the load current and maintains a high efficiency. By default, the converters and controller operate in auto pulse-frequency modulation (AutoPFM) mode such that the transition into and out of power-save mode happens within the entire regulation scheme and is seamless in both directions.

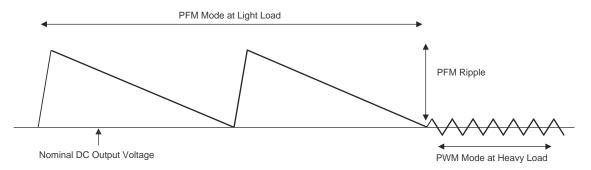


Figure 6-1. PFM and PWM Mode Operation

Figure 6-1 shows the converter and controller operation in PFM and PWM mode. In PFM mode, the minimum voltage to which the output falls is the programmed regulation voltage. The output voltage ripple in PFM mode is determined based on the external passive components (L and C). The regulator ensures that the minimum voltage during PFM mode is the same as the programmed regulation voltage (within the AC and DC tolerance).

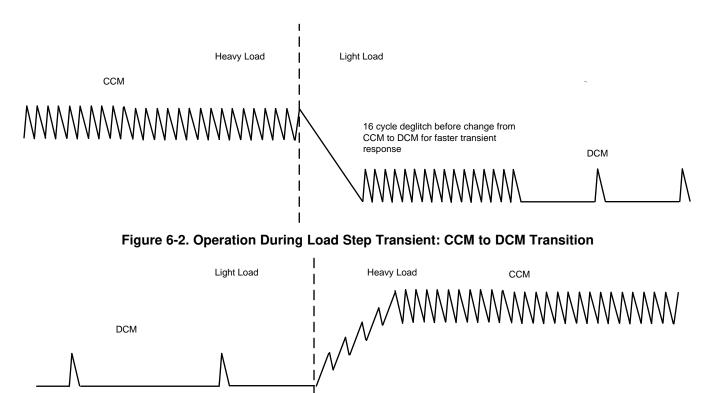


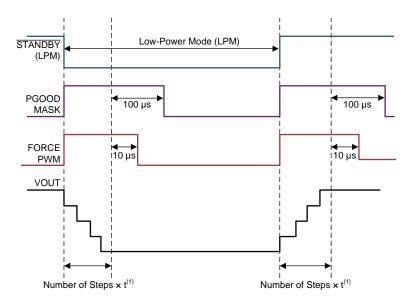


Figure 6-2 and Figure 6-3 shows the inductor current of the controller during a load transient as it transitions in and out of continuous-conduction mode (CCM) and discontinuous-conduction mode (DCM). CCM is often referred to as pulse-width modulation (PWM) mode, and DCM is referred to as pulse-frequency mode (PFM) mode. When the load step falls, a 16-cycle deglitch time passes, going from CCM to DCM. This time allows for a fast transient response and tighter peak-to-peak ripple voltage. When the load step rises, no deglitch time passes and therefore the controller goes directly from DCM to CCM in a quick-response characteristic of CCM.

6.3.1.2 Dynamic Voltage Scaling

The dynamic-voltage scaling (DVS) timing is controlled by stepping the internal reference up or down. The total ramp-up or ramp-down transition time is equal to the step time multiplied by the number of steps. The number of steps is equal to the VOUT_hi voltage minus the VOUT_lo voltage, divided by 25 mV for each step. The step time of 5 μ s for each 25-mV step ensures a time less than 70 μ s for a 300-mV voltage change. The controller is forced into PWM from the STANDBY (LPM) transition until 10 μ s after the reference ramp-up or ramp-down ends. This feature helps ensure a fast response. Similarly, the power-good signal for that rail is masked from the STANDBY (LPM) transition until 100 μ s after the internal reference ramp-up or ramp-down ends. This feature ensures that no turnoff of the false power-good fault happens during DVS. In most cases the undershoot or overshoot is negligible.





(1) Where:

number of steps = $(VOUT_hi - VOUT_lo) / 25 \text{ mV}$ per step t = 3 µs, 5 µs, 6 µs, or 7 µs per step.

Figure 6-4. DVS Transition Timing

6.3.1.3 Voltage Regulator Startup

All of the voltage regulators, including the VTT LDO1, can be enabled using either pin enables or I²C commands. The default setting uses the pin enable option. The VTT LDO1 can be enabled using the DDR_VTT_CTRL discrete input. The VTT LDO1 can also be enabled by bit 7 and bit 6 in the MISC_BITS register (address 0xE9). Bit 7 masks the DDR_VTT_CTRL pin, and bit 6 enables the VTT LDO1. All system power-good pin should be high to enable the VTT LDO. Each voltage regulator can be enabled by the enable pin (ENAVRx) or by I²C Register (xCNT). The voltage should not be changed by register at the exact same time the voltage regulator is enabled. If a different voltage other than the default is required at power-up, the register (xCNT) should program the voltage first, and then a separate command should enable the register separately. DVS can be performed any time after power-up.

Each of the voltage regulators, except for the VTT LDO1, are controlled by an internal soft-start function to ensure the output voltage ramps up gently and does not cause huge inrush current during startup to prevent droop on the input. The VTT LDO1 startup time is driven by the DDR memory requirements for the VTT voltage rail, which requires that the ramp-up on voltage is faster than 35 μ s.

6.3.1.4 Power Good and Power Fault

During operation, when the voltage regulators are enabled, the output voltage for each rail is monitored to assess if the output voltage is within a specified voltage range. A power-good status bit is generated and stored in the PGOOD_STAT1 and PGOOD_STAT2 registers. If the output voltage is within the specified voltage range, the respective power-good status bit is set to a logic high. If the output voltage falls below or goes above the specified voltage range, the power-good status bit is set to a logic low.

By default, if any of the output voltage rails experience a power-fault condition, the PMIC automatically shuts down to help protect the system unless the power fault is masked. If a power fault happens, the source of the power fault is maintained in the PWRSTAT1 and PWRSTAT2 registers which are maintained in the RTC domain. The voltage thresholds for each of the power-good comparators is a percentage relative to the nominal voltage setting of the output voltage. For the nominal value of each comparator, see Table 3-1. For the upper and lower limits of each comparator, see Section 5.5.

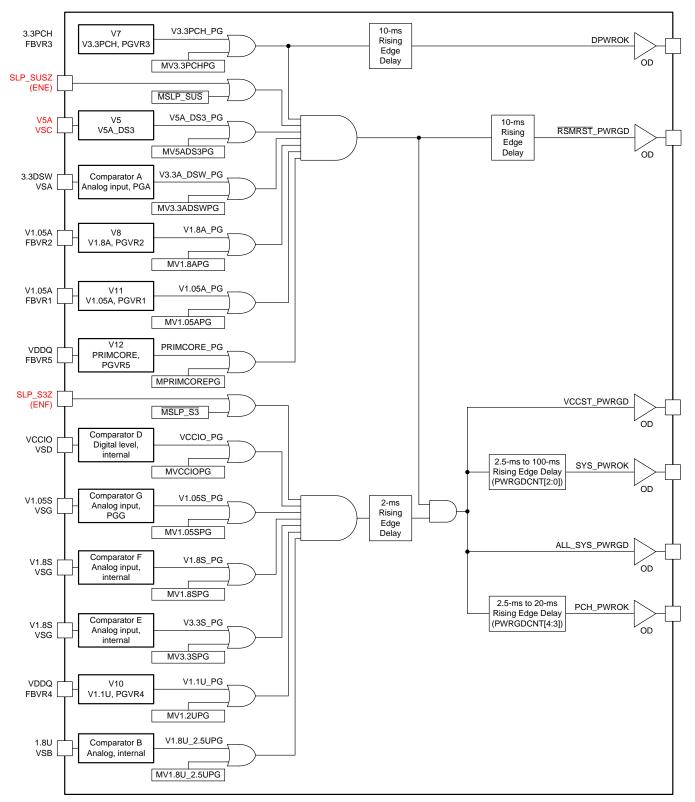
Figure 6-5 shows the power-good tree logic.

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If a particular voltage rail is not critical to the performance of the overall system, the respective powergood output can be masked using the PGMASK1 and PGMASK2 registers. The masking of a power fault prevents an automatic PMIC shutdown. This masking can be also very helpful for debug purposes in case of system failure to isolate the voltage regulator with the sensitive output voltage.

To avoid an erroneous power fault during the turnon of the voltage regulators, the power fault is masked for 10 ms relative to the enable whether it be from the discrete signal or from an I^2C command. The power-good comparator is also masked when coming out of the SLEEP (S3 state) for 100 μ s after the ALL_SYS_PWRGD pin goes high to ensure that no false triggering of the power-good comparators happens.

6.3.1.5 Current Limit

All voltage regulators are current limited. The current limit can be set based on the application load current using an external resistor for all VRs except for VR2. which has an internally-set current limit because it has an integrated power stage. The current limit controls the maximum output current. If the maximum current is reached, the output voltage starts to droop because the load can no longer be supplied with sufficient power. If the voltage drops below the power-good threshold, the power fault status is set to a logic high, and, if the power fault is not masked, the PMIC automatically shuts down in a controlled manner to protect the system.

For voltage regulators with an externally programmable current limit, see Section 7.2.2.1.4 to calculate the desired resistor value to prevent inductor saturation under nominal operation. A scaling factor of 1.5 is considered to account for the inductor variation ($\pm 20\%$) and temperature coefficient differences between the reference current (I_{REF}) and the FET R_{DSON} .

6.3.1.6 Output Discharge Feature

All of the voltage regulators have a built-in, output discharge feature. The output discharge feature consists of the ability to configure register bits to enable a discharge resistor that is only active when the voltage regulator is disabled. The discharge resistors for each of the voltage regulators can be configured using the DISCHCNT1, DISCHCNT2, DISCHCNT3, and DISCHCNT4 registers. The discharge resistors are disconnected when the voltage regulators are enabled to minimize any losses within the PMIC.

6.3.1.7 Output Voltage Control

All voltage regulators are designed to regulate a fixed-output voltage. To achieve high accuracy, the output voltage for the converters and controller is sensed using a separate feedback pin. For each of the voltage rails, except for the VTT LDO, the output voltage can be changed to slightly higher or lower values by changing the default setting in the voltage-regulator control registers. This function can be used to save power when supplying the connected load at the lowest possible supply voltage or to compensate for voltage drops during load transients by programming it slightly higher.

6.3.1.8 Converter LPM Operation

To optimize low-power operation, the output voltage of the converters can be set to a specific value. The low-power output voltage is set by the xxLVsel bits in the VR5 (0x31), VR3 (0x32), VR4 (0x36), and VR1 (0x37) registers. Entering LPM is accomplished by asserting the SLP_S0 signal to a logic low. In LPM, the power-good function remains active and is not affected by the transition from normal-operation mode to LPM, and from LPM to normal-operation mode.

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6.3.1.9 Controller LPM Operation

To optimize low-power operation, the output voltage of the controllers can be set to a specific value. The low-power output voltage is set by the V18ALVSEL[1:0] bit in the V18ACNT register. Entering the low-power mode is accomplished by asserting the DDR_VTT_CTRL pin or the STANDBY pin to a logic low. In this low-power mode, the power-good function remains active and is not affected by the transition from normal-operation mode to the LPM, and from LPM to normal-operation mode. The DDR_VTT_CTRL pin asserts DVS on VR4 and the STANDBY pin asserts DVS on VR1, VR2, VR3, and VR5, as defined by the CNT registers. In cases where the output current demand from the controller is very small, the controller is automatically placed in an ultra-low quiescent (ULQ) mode to reduce power consumption and increase the efficiency.

6.3.1.10 Controller Internal-Ramp Comparator

The controllers have an internal ramp characteristic of the DCAP2 control architecture which provides improved performance with low-ESR output capacitors. This internal ramp provides ramp compensation that helps maintain a relatively constant frequency during CCM and better stability for designs with very-low ESR on the output capacitors. The ramp height can be optimized and is a function of the input voltage to provide proportional feed-forward. At very high voltages, the ramp may exceed the operating window of the PWM comparator and may overpower the natural ripple of the output. Therefore a smaller ramp must be used. Because the ramp was already becoming large, switching to a smaller size is helpful. To switch to a smaller size, a comparator monitors the input voltage at the VIN pin. When input voltage rises and exceeds 11 V, it changes the ramp to a slightly smaller value. The smaller ramp has a wide 1.1-V hysteresis, so at approximately 9.9 V as the input voltage falls, the ramp returns to the slightly bigger size. In most cases this difference is negligible.

6.3.1.11 Undervoltage Lockout

An undervoltage-lockout (UVLO) function prevents the PMIC from operating if the supply voltage on the VIN pin of the PMIC is lower than the UVLO threshold (see Section 5.5). During operation, if the supply voltage on the VIN pin drops below the UVLO threshold, the system or PMIC shuts down.

6.3.2 Power-Good Comparators for Cannon Lake Platform

For the Cannon Lake power-map implementation, the five voltage regulators and LDO1 of the PMIC are assigned with the low-voltage rails which are either merged or split according to the configuration.

Figure 6-6 and Figure 6-7 show the operation of the window mode for the comparators. In window mode, the comparators have both high and low thresholds for detection of power good logic and power fail. In level mode, only the low threshold is present. For the voltage regulators and power good comparator logic assignments supporting the Cannon Lake platform, see Table 3-1.



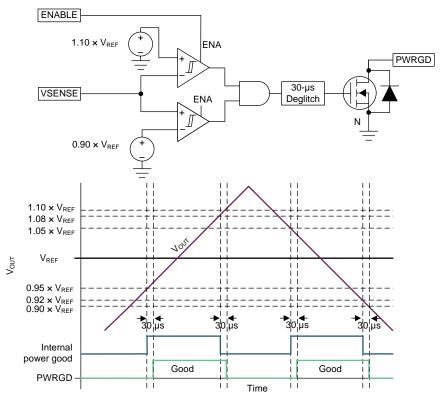
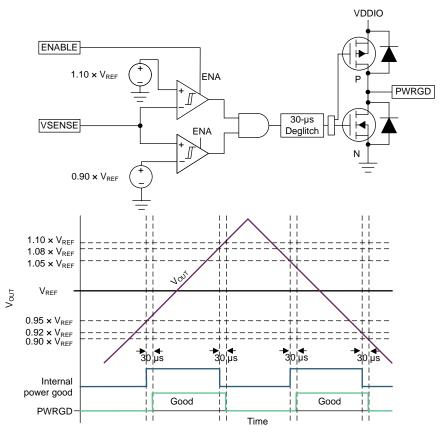


Figure 6-6. Power-Good Window Comparator With Open-Drain Output





6.3.2.1 Internal VR Power-Good Comparators

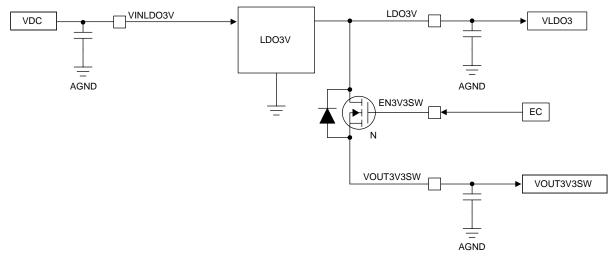
All power-good comparators (converter and controllers) can be configured for either open-drain outputs or push-pull outputs. For VR PG configuration settings, see Table 3-1. The power-good comparators monitor the output voltage to ensure it is within the power-good threshold ($PG_{Threshold}$) of the nominal target voltage. A deglitch time ($PG_{deglitch}$) exists on the output of all the power-good comparators. The open-drain output requires an external pullup resistor (typically in the 100-k Ω range). Open-drain outputs can be combined to create an AND logic function. For push-pull outputs, the output internally pulls up to VDDIO pin rail.

6.3.2.2 External VR Power-Good Comparators

The power-good comparators can be configured for either open-drain outputs or push-pull outputs. For VR PG configuration settings, see Table 3-1. The power-good comparators monitor the output voltage to ensure it is within the power-good threshold ($PG_{Threshold}$) of the nominal target voltage. A deglitch time ($PG_{deglitch}$) exists on the output of all the power-good comparators. The open-drain output requires an external pullup resistor (typically in the 100-k Ω range). Open-drain outputs can be combined to create an AND logic function. For push-pull outputs, the output internally pulls up to VDDPG pin rail.

6.3.3 LDO3V and 3V3SW Load Switch

The LDO3V LDO regulator powers up when the VINLDO3V pin voltage is greater than the UVLO3V threshold. The LDO3V LDO regulator powers the internal digital blocks and analog blocks of the PMIC. This LDO regulator is also used as the positive rail of the power-good comparator and level-shifter outputs. The 3V3SW load switch can optionally connect or disconnect the VOUT3V3SW output to a load. The 3V3SW load switch is enabled by the EN3V3SW pin. Figure 6-8 shows the block diagram for the load switch.



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Figure 6-8. LDO3V and 3V3SW Load Switch

6.3.4 LDO5V and 5VSW Load Switch

The LDO5V LDO regulator powers up when the VIN pin voltage is greater than the UVLO5V threshold. The LDO5V LDO regulator powers the gate drives for all the five VRs of the PMIC. The 5VSW load switch is used to switch the gate-drive source from the internal LDO5V LDO to the 5-V voltage regulator output as soon as the V5A switching regulator power-good signal goes high. Because the switching regulator is used instead of LDO5V, it significantly improves the efficiency of the VRs whose effect is more significant

at lower VR load current and higher VR input voltage. The load switch is enabled by the EN5VSW pin. Connect the V5A_PG signal to the EN5VSW pin. When the EN5VSW pin is high, the LDO5-V internal reference drops to 4.5 V to ensure the 5-V VR drives all the gate drive current, but also to ensure the gate drive never falls below 4.5 V. When the EN5VSW pin is low, the LDO resumes to the 5-V internal reference and the load switch is turned off to disconnect the 5-V VR.

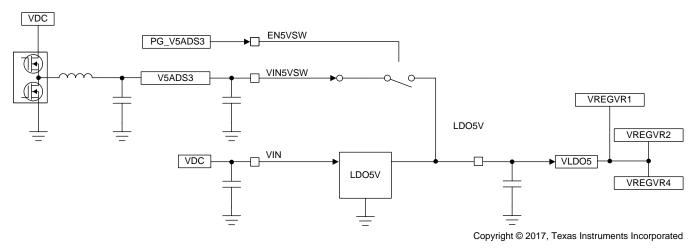


Figure 6-9. LDO5V and 5VSW Load Switch

6.3.5 RTC Selector and 3.1-V LDO

The RTC selector is used to select from the coin-cell backup battery and the internal 3.3-V LDO to power the 3P3A_RTC output rail for the RTC domain rail. If the VIN voltage is less than the $V_{UVLO_5V_Main}$ threshold, the coin-cell battery is selected. If the VIN voltage is greater than the UVLO5V threshold, then the internal 3.1-V LDO is selected. The selector logic for the backup battery selector has a very-low current draw when the battery is selected to extend the charge life of the backup battery. This rail allows keeping the data of the RTC registers even when the adapter and main battery are removed from the system. If the coin-cell voltage falls below the V_{bkup_UVLO} threshold, the RTC registers reset to the default values, as long as the VIN voltage is not also present. The 3.1-V LDO is set to 3.1 V to ensure the PCH voltage is always below 3.2 V (maximum) to help protect the PCH.

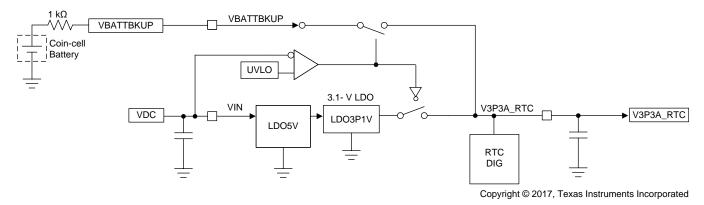


Figure 6-10. RTC Selector and 3.1-V LDO

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6.3.6 Power-Path Comparators

The power-path comparators are comparators rated for a high voltage. The input pins of the power-path comparators are rated for high voltage. Both the voltage-sense and comparator-output pins are independent from the rest of the PMIC. These comparators can be used when the PMIC is powered down, as long as the VINPP pin is above the UVLO5V threshold. Connect a resistor divider from the source to set the $V_{REF_{PP}}$ trigger threshold. These comparators can be used to detect an adapter and up to two batteries. An open-drain pin can detect the status, and a status register reports the status in the I²C registers using the ACOK, LOWBAT1, and LOWBAT2 bits. These bits can issue an interrupt to the EC if the interrupt mask bit is set appropriately at the MACOK, MLOWBAT1, and MLOWBAT2 bits. The high-voltage-rated outputs can be used to turn on the external P-channel power MOSFETs to control the power source path. Figure 6-11 shows an example of how to use the power-path comparators. A diode OR connection from all the power sources in use is recommended to ensure the VINPP pin is up when a source is available. If these comparators are not used, tie the VINPP pin to the VIN and VIN_LDO3 pins. Do not ground the VINPP pin when the VIN pin is powered up. These comparators can also be used as general-purpose comparators for numerous other applications.

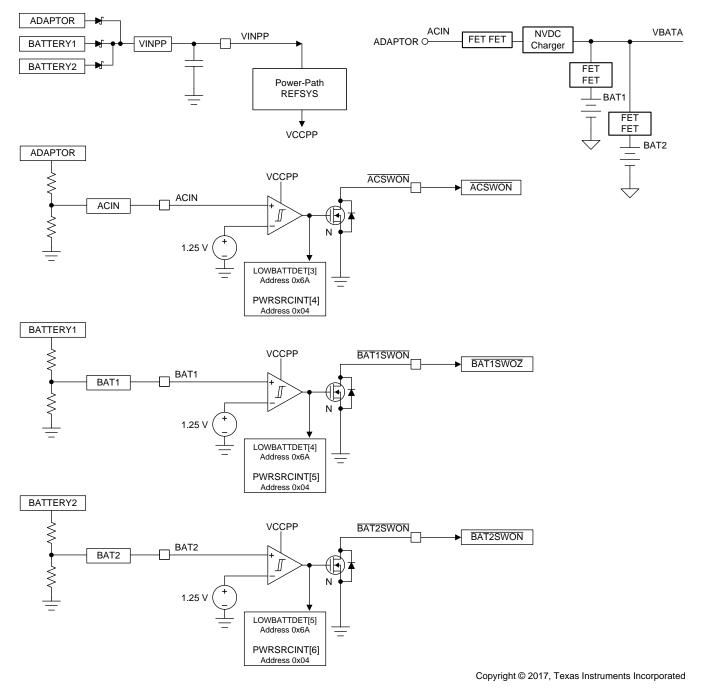


Figure 6-11. Power-Path Comparators

6.3.7 UVLO Comparators

The UVLO and VDCSNS comparators are high-voltage comparators rated for a 28-V input. The comparators are powered by the VIN pin for the LDO5V and 1.25-V LDO, and the VINLDO3V pin for the LDO3V. The VDCSNS input is also a high-voltage input pin to detect if the VIN voltage is above a programmable voltage. The VIN and VINLDO3V pins are tied directly to the VIN. The VDCSNS pin requires a resistor divider to set the proper detection gain.



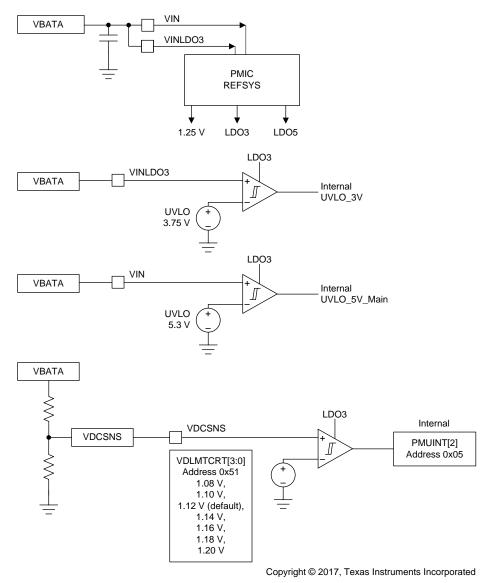
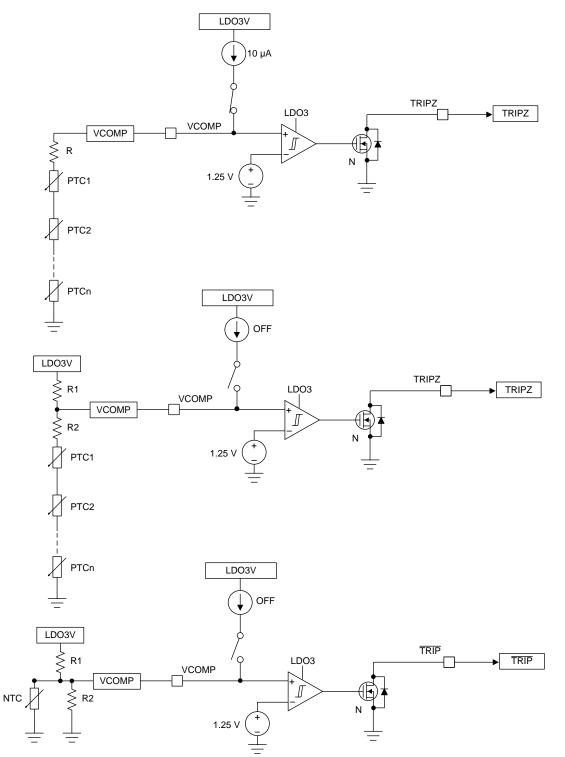


Figure 6-12. UVLO Comparators

6.3.8 Board Temperature Monitor

The temperature comparator is used to detect either several PTC thermistors stacked in a series string or a single NTC thermistor. The PTC thermistors allow for an inexpensive overtemperature detection of any fault throughout several points on the motherboard, with each PTC thermistor selected to have its own temperature-threshold trigger point. An internal current source can be enabled to drive the PTC thermistors to minimize noise sensitivity. The current source can be disabled to drive with a voltage source, such as the LDO3V, to allow for tighter accuracy. Only a single NTC thermistor can be detected at a time, but the NTC allows tracking several temperature profiles. This comparator can also be used as a general-purpose comparator for numerous other applications.

The VCOMP comparator is on by default with the 10-μA current source also on. To completely disable the 10-μA current source or the comparator, write to the EN_VCOMP_10U and VCOMPEN bits.



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Figure 6-13. Temperature Comparator

6.3.9 Low-Power Mode (LPM), Connected Standby, Instant Go of VRs

The voltage regulators from the PMIC can be programmed by a register to change the voltage in active mode, or to change to a lower voltage or decay in the low-power mode (LPM). This feature can be used to conserve system power and extend battery life. This capability is useful to help meet the Connected Standby and Instant Go specifications. The STANDBY pin triggers low-power mode (LPM) when low. The STANDBY pin triggers active mode when high. Connect the SLP_SO signal from the processor core (PCH) to the STANDBY pin to trigger LPM. The default settings can be changed by the user with the I²C register at any time.

In LPM, DVS and decay modes are enabled on the rails that were programmed for change in the VxxxCNT registers (address 0x30 through 0x38). The VCCIOCNT register is different because decay mode is enabled instead of DVS and therefore, only the CSDECAYEN bit is used.

For more information on DVS and decay, see Section 6.3.1.8 and Section 6.3.1.9.

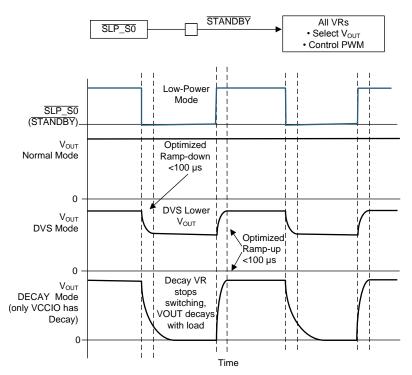
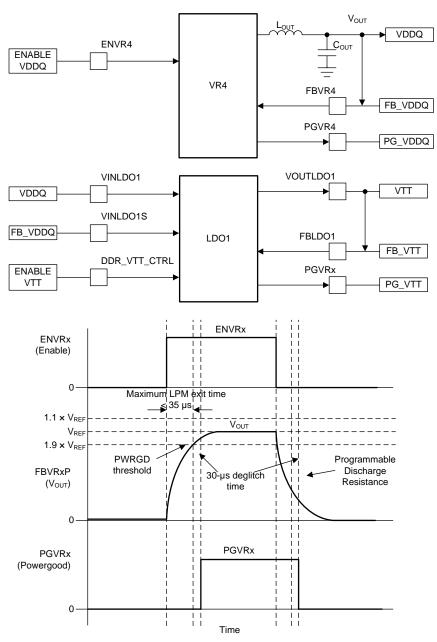


Figure 6-14. Low-Power Mode (LPM), Connected Standby, and Instant Go of VRs

6.3.10 VR4 VDDQ and LDO1 VTT Enabling

The VDDQ VR is enabled by the ENVR4 pin and the LDO1 VTT push-pull LDO is enabled by the DDR_VTT_CTRL pin. The DDR_VTT_CTRL pin is often connected to the SLP_S0 pin to turn off the VTT rail during sleep mode. The DDRID pin is a tri-level pin that sets the VR4 VDDQ voltage to either 1.2 V, 1.35 V, or 1.1 V. The DDR_VTT_CTRL pin is also used for DVS control of VR4, as defined by the V1P2UCNT register (0x36).







6.3.11 RTC Power Path and LDO

In case the main system battery is removed and no alternate power source is available, the RTC data, configuration and status registers, oscillator, and timekeeping path of the RTC block are backed up by either a super capacitor or a coin-cell battery. If the coin-cell or super-capacitor battery voltage falls below the minimum operational voltage and no input voltage is present (AC-DC voltage greater than the PMIC UVLO), the RTC data registers are invalid. Because the Intel RTC cannot support a maximum voltage greater than 3.2 V, when an AC-DC voltage is present and is higher than the UVLO threshold, the RTC is supplied by the AC-DC voltage instead of from the coin-cell battery. Supplying the RTC from the AC-DC voltage maximizes the stored charge in the coin-cell battery. When an AC-DC voltage is present, the internal coin-cell selector selects the higher voltage from either the coin-cell voltage or the AC-DC voltage. When the AC-DC voltage is selected as a source, the coin-cell LDO is driven from the 5-V PMIC LDO to regulate the output voltage at a fixed 3.1 V to ensure the maximum voltage remains below 3.2 V.

When the main system battery (V_{DC}) is greater than 5.4 V, the main power source for the RTC LDO is the 5-V internal LDO of the PMIC. The RTC LDO is bypassed and the RTC supply is powered by the coin-cell when the V_{DC} falls below this threshold to maximize the life of the coin-cell battery. The coin-cell battery is used only if other options have failed. All power routing of the source selection for the RTC power happens internally and no external connections other than the coin-cell battery or super capacitor is required.

6.4 Device Functional Modes

6.4.1 OFF State (No VIN and No Backup Battery)

If the VIN voltage and the VBATTBKUP battery are both lower than their respective UVLO thresholds then the device is in the OFF state. In this state, the device cannot turn on or enable any VRs or discrete load switches and regulators. The clock and I²C are not active in this state.

In the OFF state, only the ACIN, BAT1, and BAT2 power-path switch comparators are available for use. To use these comparators, the VINPP pin must be supplied with the highest of the three input voltages from either the AC, BAT1, and BAT2 pin. In all other states, the VINPP must be supplied from the same source as the VIN pin.

6.4.2 STARTUP State

The device enters the STARTUP state when the VIN voltage is greater than the UVLO threshold. In the STARTUP state, the LDO3V, LDO5V, and VREF1V25 pins ramp-up. When the LDO3V and LDO5V pins both reach their nominal voltage and their power-good pins assert HIGH, the OTP memory loads into the I²C registers. After the LDO5V_PG pin asserts HIGH, the RTC LDO turns on and the V3.3A_RTC is regulated to 3.1 V, powered from the LDO5V. When the OTP memory is loaded and the RTC LDO is regulated to 3.1 V the device enters the READY state.

6.4.3 READY State

The device is considered to be in the READY state when all of the internal supplies and RTC are regulated, and the OTP memory is loaded into the registers. In this state, the device is ready for enable commands. The comparators, level shifters, and all other blocks are available for use.

6.4.4 STANDBY State

The device enters the STANDBY state when the STANDBY pin transitions from HIGH to LOW only if the ALL_SYS_PWRGD pin is HIGH. Only the VRs that have the DVS feature by default or through I²C register definition in registers 0x30 through 0x38 enter the STANDBY state.

6.4.5 Emergency Shutdown

An emergency shutdown is a protection feature for system loads. This feature reduces the risk of reverse bias in the processor or other devices from one rail to another. When an emergency shutdown is initiated, the DPWROK pin is pulled LOW, discharge resistors are enabled for all rails, and all rails are disabled at the same time. The PMIC remains in emergency shutdown mode until any of the following happens:

- A PWRBTNIN falling edge is detected.
- The ACOK pin transitions from LOW to HIGH.
- The VIN voltage is less than the UVLO threshold.

The PMIC only causes an emergency power shutdown of the rails for the following conditions:

- The is VIN pin voltage is less than the UVLO5V threshold or the VINLDO3V pin voltage is equal to or less than the UVLO3V threshold. In this case, read bit 2 in the IRQLVL1 register to determine if a VIN voltage < UVLO caused shutdown.
- A VR fault is detected. In this case, read the RESETIRQ1 register to determine if a VR fault caused shutdown.

- The junction temperature equals the critical temperature which casus a die thermal fault. In this case, read the RESETIRQ2 register to determine if thermal fault caused shutdown.
- The hardware forces shutdown. In this case, the SHUTDOWNZ pin is forced low.
- The software forces shutdown. In this case, read the SDWNCTRL register (address 0x49).
- The PWRBTN bit is held longer than the time defined by the FLT[5:0] bit. In this case, read the RESETIRQ1 register to determine if the push button caused shutdown.

The PMIC monitors each rail and ensures no faults are present. All rails are monitored for fault protection. Notice also that the current limit does not directly cause a shutdown. Instead, an overcurrent condition could cause a shutdown indirectly by means of a power fault. The overcurrent condition limits the maximum possible output current, such that if the load current exceeds the current limit, then the voltage drops until the lower output voltage causes a power fault if it is below the power-good threshold for more than the PG_{deglitch} time (30 μ s). An emergency power shutdown causes all rails to immediately power down. The LDO3, LDO5, and VREF1.25V remain on if the input voltage is greater than the UVLO3 and UVLO5 thresholds.

6.4.6 Backup Battery, G3 (No VIN)

G3 is an Intel defined state where the VIN voltage is greater than the UVLO threshold to the device and a valid backup battery is present on the VBATTBKUP pin. In this state, the backup battery is passed to the RTC output and the RTC-domain I²C register values are saved. When the VIN voltage is greater than the UVLO threshold these register retain their value and can be read when I²C is ready.

In this state, all VRs and internal LDOs are off and I²C access is not available.



6.5 Programming

6.5.1 PC Interface

I²C is a 2-wire serial interface developed by NXP (formerly Philips Semiconductor) (refer to the I²C-Bus Specification and user manual, Rev 4, 13 February 2012). The bus consists of a data line (SDA) and a clock line (SCL) with pullup structures. When the bus is idle, both SDA and SCL lines are pulled high. All the I²C compatible devices connect to the I²C bus through open drain I/O pins, SDA and SCL. A master device, usually a microcontroller (MCU) or a digital-signal processor (DSP), controls the bus. The master is responsible for generating the SCL signal and device addresses. The master also generates specific conditions that indicate the start and stop of data transfer. A slave device receives, transmits, or receives and transmits data on the bus under control of the master device.

The TPS650932 works as a slave and supports the following data transfer modes, as defined in the I^2C -Bus Specification: standard mode (100 kbps) and fast mode (400 kbps). The interface adds flexibility to the power-supply solution, enabling most functions to be programmed to new values depending on the instantaneous application requirements. Register contents are loaded when voltage is applied to the TPS650932 device that is higher than the UNVLO threshold. The I^2C interface is running from an internal oscillator that is automatically enabled when an access to the interface is available.

The data transfer protocol for standard and fast modes is exactly the same, and, therefore, they are referred to as F/S-mode.

The TPS650932 device supports 7-bit addressing. The device does not support 10-bit addressing and general-call address. The default device address is defined by the status of the SLAVEADDR pin. Three different slave addresses are possible: 0x30 (SLAVEADDR, 0 V), 0x32 (SLAVEADDR, 3.3 V), and 0x34 (SLAVEADDR, floating).

All registers are set to their default value when the supply voltage is less than the UVLO threshold.

6.5.1.1 F/S-Mode Protocol

The master initiates data transfer by generating a start condition. The start condition is when a high-to-low transition occurs on the SDA line while SCL is high, see Figure 6-16. All I²C-compatible devices should recognize a start condition.

The master then generates the SCL pulses, and transmits the 7-bit address and the read-write direction bit, R/W, on the SDA line. During all transmissions, the master ensures that data is valid. A valid data condition requires the SDA line to be stable during the entire high period of the clock pulse, see Figure 6-17. All devices recognize the address sent by the master and compare it to their internal fixed addresses. Only the slave device with a matching address generates an *acknowledge*, see Figure 6-18, by pulling the SDA line low during the entire high period of the ninth SCL cycle. Upon detecting this acknowledge, the master knows that the communication link with a slave has been established.

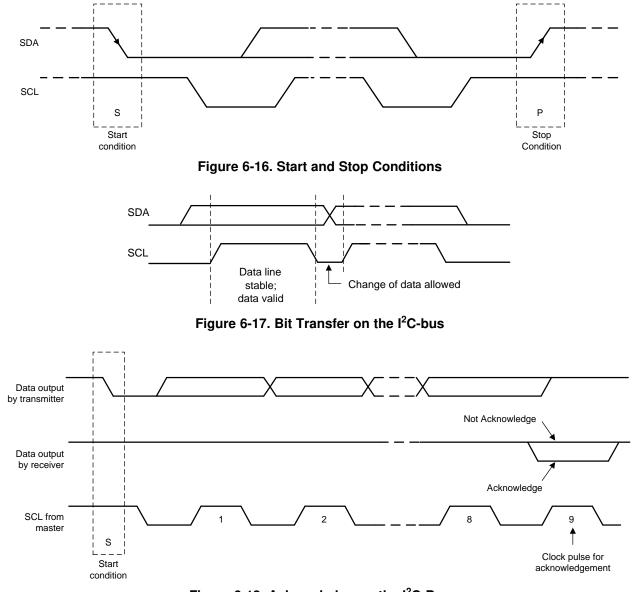
The master generates further SCL cycles to either transmit data to the slave (R/W bit = 0) or receive data from the slave (R/W bit = 1). In either case, the receiver needs to acknowledge the data sent by the transmitter. An acknowledge signal can either be generated by the master or by the slave, depending on which one is the receiver. 9-bit valid data sequences consisting of 8-bit data and 1-bit acknowledge can continue as long as necessary.

To signal the end of the data transfer, the master generates a stop condition by pulling the SDA line from low to high while the SCL line is high, see Figure 6-16. This releases the bus and stops the communication link with the addressed slave. All I^2C compatible devices must recognize the stop condition. Upon the receipt of a stop condition, all devices know that the bus is released, and they wait for a start condition followed by a matching address

Attempting to read data from register addresses not listed in this section results in FFh being read out. F/S I²C operation does not support repeated start.



6.5.1.2 Diagrams of I²C Protocol





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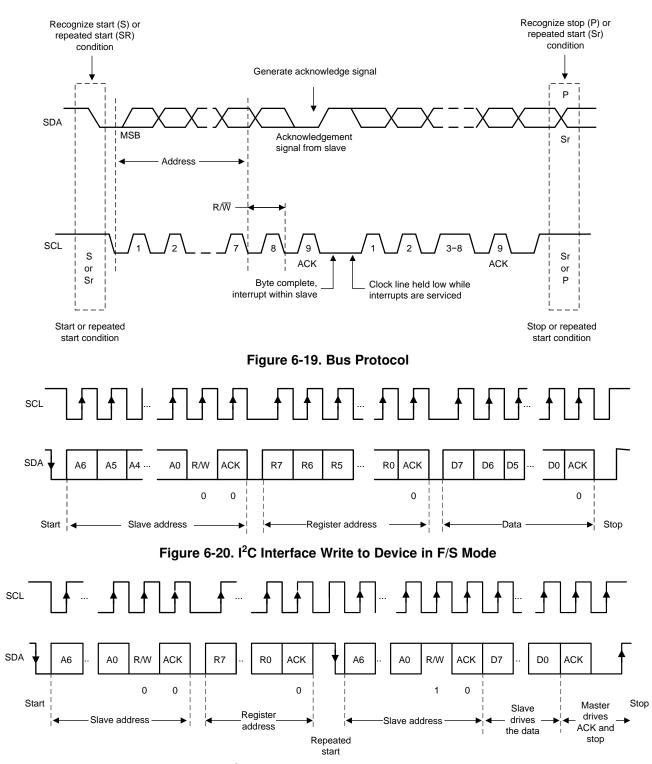


Figure 6-21. I²C Interface Read from Device in F/S Mode

6.6 Register Maps

 Table 6-1 lists the memory-mapped registers for the TPS650932. All register offset addresses not listed in

 Table 6-1 should be considered as reserved locations and the register contents should not be modified.

Address	Acronym	Register Name	Domain	Section
0x00	VENDORID	Code that indicated a Texas Instruments' PMIC device	RESET	Go
0x01	REVID	Code to identify device revision and programming revision	RESET	Go
0x02	IRQLVL1	Top level interrupts	RTC	Go
0x04	PWRSRCINT	Input power interrupts	RTC	Go
0x05	PMUINT	PMU interrupts	RTC	Go
0x08	RESETIRQ1	Emergency shutdown interrupts	RTC	Go
0x09	RESETIRQ2	Emergency shutdown interrupts	RTC	Go
0x0B	MPMUINT	Mask PMU interrupts	RTC	Go
0x0C	MPWRSRCNT	Mask input power interrupts	RTC	Go
0x11	RESETIRQ1MASK	Mask emergency shutdown interrupts	RTC	Go
0x12	RESETIRQ2MASK	Mask emergency shutdown interrupts	RTC	Go
0x13	IRQLVL1MSK	Mask top level interrupt	RTC	Go
0x14	PBCONFIG	Power button configuration	RTC	Go
0x15	PBSTATUS	Power button status	RTC	Go
0x16	PWRSTAT1	VR fault reporting	RTC	Go
0x17	PWRSTAT2	VR fault reporting	RTC	Go
0x18	PGMASK1	Mask VR PGs from system power good tree	RTC	Go
0x19	PGMASK2	Mask VR PGs from system power good tree	RTC	Go
0x30	VCCIOCNT	VCCIO control	RESET	Go
0x31	VPRIMCORECNT	PRIMCORE control	RESET	Go
0x32	V33ADSWCNT	V3.3A_DSW control	RESET	Go
0x33	V33APCHCNT	V3.3A_PCH (PGE) control	RESET	Go
0x34	V18ACNT	V1.8A control	RESET	Go
0x35	V18U25UCNT	V1.8U_2.5U (PGB) control	RESET	Go
0x36	VDDQCNT	VDDQ / VDDQ (VR4) control	RESET	Go
0x37	V105ACNT	V1.05A (VR1) control	RESET	Go
0x38	V5ACNT	V5A control	RESET	Go
0x3B	VRMODECTRL	Force low power mode	RESET	Go
0x3C	DISCHCNT1	Discharge resistors settings	RESET	Go
0x3D	DISCHCNT2	Discharge resistors settings	RESET	Go
0x3E	DISCHCNT3	Discharge resistors settings	RESET	Go
0x3F	DISCHCNT4	Discharge resistors settings	RESET	Go
0x40	PWRGDCNT1	System level power goods	RESET	Go
0x41	VREN	Deep sleep enable	RESET	Go
0x42	REGLOCK	Lock for control registers 0x30 through 0x38	RESET	Go
0x43	VRENPINMASK	Mask hardware enable pins	RESET	Go
0x48	RSTCTRL	Reset control	RTC	Go
0x49	SDWNCTRL	Software force shutdown	RESET	Go
0x51	VDLMTCRT	VDCSNS settings	RESET	Go
0x69	ACOKDBDM	ACOK settings	RESET	Go
0x6A	LOWBATTDET	Battery detection settings	RESET	Go
0x6F	SPWRSRCINT	Input power statuses	RESET	Go
0xD0	CLKCTRL1	Clock control	RTC	Go

Table 6-1. Register Summary

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Address	Acronym	Register Name	Domain	Section		
0xDD	COMPA_REF	Comparator A settings	RESET	Go		
0xDE	COMPB_REF	Comparator B settings	RESET	Go		
0xDF	RESERVED	Reserved	—			
0xE0	RESERVED	Reserved	—			
0xE1	RESERVED	Reserved	—			
0xE2	RESERVED	Reserved	_			
0xE3	RESERVED	Reserved	Reserved —			
0xE4	RESERVED	Reserved	_			
0xE5	PWRFAULT_MASK1	Mask VR faults from emergency shutdown	RESET	Go		
0xE6	PWRFAULT_MASK2	Mask VR Faults from emergency shutdown	RESET	Go		
0xE7	PGOOD_STAT1	VR PGs statuses	RESET	Go		
0xE8	PGOOD_STAT2	VR PGs statuses	RESET	Go		
0xE9	MISC_BITS	Miscellaneous bits	RESET	Go		
0xEA	STDY_CTRL	VCOMP and standby control	RTC	Go		
0xEB	TEMPCRIT	VR critical temperature	RTC	Go		
0xEC	TEMPHOT	VR hot temperature	RTC	Go		
0xEE	VREN_PIN_OVR	VR enable override with software	RESET	Go		

Table 6-1. Register Summary (continued)

Complex bit access types are encoded to fit into small table cells. Table 6-2 shows the codes that are used for access types in this section.

Access Type	Code	Description					
Read Type							
R	R	Read					
R-0	R -0	Read Returns 0s					
R-1	R -1	Read Returns 1s					
Write Type							
W	W	Write					
W1C	W 1C	Write 1 to clear					
Reset or Default	Reset or Default Value						
-n		Value after reset or the default value					

Table 6-2. Access Type Codes

6.6.1 VENDORID Register (address = 0x00) [reset = 0x22]

VENDORID is shown in Figure 6-22 and described in Table 6-3.

Return to Summary Table.

Register domain: RESET

Figure 6-22. VENDORID Register

7	6	5	4	3	2	1	0	
VENDORID[7:0]								
			R/W	-22h				

Table 6-3. VENDORID Register Field Descriptions

Bit	Field	Туре	Reset	Description
7-0	VENDORID[7:0]	R/W	22h	Vendor ID

6.6.2 REVID Register (address = 0x01) [reset = 0x00]

REVID is shown in Figure 6-23 and described in Table 6-4.

Return to Summary Table.

Register domain: RESET

Figure 6-23. REVID Register

7	6	5	4	3	2	1	0
DNUM[3:0]				OTPREV[1:0]		REVID[1:0]	
R/W-0h				R/\	N-0h	R/W	/-0h

Table 6-4.	REVID	Register	Field	Descriptions
------------	-------	----------	-------	--------------

Bit	Field	Туре	Reset	Description
7-4	DNUM[3:0]	R/W	0h	Major revision ID
				Oh = A
				1h = B
				2h = C
				3h = D
				4h = E
				5h = F
3-2	OTPREV[1:0]	R/W	0h	
				Minor revision ID
				0h = 0
				1h = 1
				2h = 2
				3h = 3
				4h = 4
				5h = 5
				6h = 6
				7h = 7
1-0	REVID[1:0]	R/W	0h	Minor revision ID
				0h = 0
				1h = 1
				2h = 2
				3h = 3
				4h = 4
				5h = 5
				6h = 6
				7h = 7

6.6.3 IRQLVL1 Register (address = 0x02) [reset = 0x00]

IRQLVL1 is shown in Figure 6-24 and described in Table 6-5.

Return to Summary Table.

Register domain: RTC

Figure 6-24. IRQLVL1 Register

7	6	5	4	3	2	1	0
RESET	RESERVED2	PMU	RESERVED	D1[1:0]	PWRSRC	RESERVED	PWRBTN
R/W-0h	R-0h	R/W-0h	R-0h		R/W-0h	R-0h	R/W1C-0h

Table 6-5. IRQLVL1 Register Field Descriptions

Bit	Field	Туре	Reset	Description
7	RESET	R	0h	RESET interrupt
				0h = Not asserted
				1h = Asserted
6	RESERVED2	R	0h	
5	PMU	R	0h	Power monitor interrupt
				0h = Not asserted
				1h = Asserted
4-3	RESERVED1[1:0]	R	0h	
2	PWRSRC	R	0h	Power source interrupt
				0h = Not asserted
				1h = Asserted
1	RESERVED	R	0h	
0	PWRBTN	R/W1C	0h	Power button interrupt
				0h = Not asserted
				1h = Asserted, write 1 to clear

6.6.4 PWRSRCINT Register (address = 0x04) [reset = 0x00]

PWRSRCINT is shown in Figure 6-25 and described in Table 6-6.

Return to Summary Table.

Register domain: RTC

Figure 6-25. PWRSRCINT Register

7	6	5	4	3	2	1	0
RESERVED1_ PWRSRCINT	LOWBATT2	LOWBATT1	ACOK	PMICHOT		RESERVED[2:0]	
R-0h	R/W-0h	R/W-0h	R/W-0h	R/W-0h		R-0h	

Bit	Field	Туре	Reset	Description
7	RESERVED1_PWRSRCINT	R	0	
6	LOWBATT2	R/W	0	Low battery2 interrupt (rising-edge detect threshold = 1.25 V; falling-edge hysteresis = 125 mV)
				0h = No battery2 detected
				1h = Battery2 detected
5	LOWBATT1	R/W	0	Low battery1 interrupt (rising-edge detect threshold = 1.25 V ; falling-edge hysteresis = 125 mV)
				0h = No battery1 detected
				1h = Battery1 detected
4	ACOK	R/W	0	AC/DC adapter detection interrupt (rising-edge detect threshold = 1.25 V; falling-edge hysteresis = 125 mV)
				0h = No adapter detected
				1h = Adapter detected
3	PMICHOT	R/W	0	PMIC internal temperature interrupt
				0h = PMIC temperature normal
				1h = PMIC temperature hot
2-0	RESERVED[2:0]	R	000	

Table 6-6. PWRSRCINT Register Field Descriptions

6.6.5 PMUINT Register (address = 0x05) [reset = 0x00]

PMUINT is shown in Figure 6-26 and described in Table 6-7.

Return to Summary Table.

Register domain: RTC

Figure 6-26. PMUINT Register

			-	-			
7	6	5	4	3	2	1 0	
	RESERVED2[2:0]		PMUACOK	RESERVED1_ PMUINT	PMUVDC	RESERVED_PMUINT[1:0]
	R-0h		R/W-0h	R-0h	R/W-0h	R-0h	

Table 6-7. PMUINT Register Field Descriptions

Bit	Field	Туре	Reset	Description
7-5		R	0h	
4	PMUACOK	R/W	0h	Adapter detection interrupt
				0h = No interrupt pending
				1h = AC adapter removed (SACOK goes from H to L)
3	RESERVED1_PMUINT	R	0h	
2	PMUVDC	R/W	0h	Power monitor critical supply voltage interrupt 0h = Critical supply voltage over threshold limit
				1h = Critical supply voltage below threshold limit
1-0	RESERVED_PMUINT[1:0]	R	0h	

6.6.6 RESETIRQ1 Register (address = 0x08) [reset = 0x00]

RESETIRQ1 is shown in Figure 6-27 and described in Table 6-8.

Return to Summary Table.

Register domain: RTC

Figure 6-27. RESETIRQ1 Register

7 6	5	4	3	2	1	0
RESERVED1_RESETIRQ1[1:0]	FCO	VRFAULT		RESER\	/ED[3:0]	
R-0h	R/W-0h	R/W-0h		R-	0h	

Table 6-8. RESETIRQ1 Register Field Descriptions

Bit	Field	Туре	Reset	Description
7-6	RESERVED1_RESETIRQ1[1:0]	R	0h	
5	FCO	R/W	0h	Power button triggered reset interrupt 0h = Power button counter has not forced an emergency reset 1h = Power button counter has forced an emergency reset
4	VRFAULT	R/W	Oh	Voltage regulator triggered reset interrupt Oh = Voltage regulator fault has not triggered an emergency reset 1h = Voltage regulator fault has triggered an emergency reset
3-0	RESERVED[3:0]	R	0h	

6.6.7 RESETIRQ2 Register (address = 0x09) [reset = 0x00]

RESETIRQ2 is shown in Figure 6-28 and described in Table 6-9.

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Register domain: RTC

Figure 6-28. RESETIRQ2 Register

			•		•		
7	6	5	4	3	2	1	0
	RESERVED1[5:0]						RESERVED_R ESETIRQ2
	R-0h						R-0h

Table 6-9. RESETIRQ2 Register Field Descriptions

Bit	Field	Туре	Reset	Description
7-2	RESERVED1[5:0]	R	0h	
1	CRITTEMP	R/W	0h	Temperature triggered reset interrupt 0h = Critical temperature not reached 1h = Critical temperature reached, forcing emergency shutdown
0	RESERVED_RESETIRQ2	R	0h	

6.6.8 MPMUINT Register (address = 0x0B) [reset = 0x14]

MPMUINT is shown in Figure 6-29 and described in Table 6-10.

Return to Summary Table.

Register domain: RTC

Figure 6-29. MPMUINT Register

7	6	5	4	3	2	1	0
RES	ERVED2_MPMUIN	T[2:0]	MPMUACOK	RESERVED1_ MPMUINT	MPMUVDC	RESERVED_MP	MUINT[1:0]
	R-0h		R/W-1h	R-0h	R/W-1h	R-0h	

Table 6-10. MPMUINT Register Field Descriptions

Bit	Field	Туре	Reset	Description
7-5	RESERVED2_MPMUINT[2:0]	R	0h	
4	MPMUACOK	R/W	1h	Power monitor critical supply voltage (adapter) mask interrupt 0h = Not masked 1h = Masked
3	RESERVED1_MPMUINT	R	0h	
2	MPMUVDC	R/W	1h	Power monitor critical supply voltage mask interrupt 0h = Not masked 1h = Masked
1-0	RESERVED_MPMUINT[1:0]	R	0h	

6.6.9 MPWRSRCINT Register (address = 0x0C) [reset = 0x078]

MPWRSRCINT is shown in Figure 6-30 and described in Table 6-11.

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Register domain: RTC

Figure 6-30. MPWRSRCINT Register

7	6	5	4	3	2	1	0
RESERVED1_ MPWRSRCINT	MLOWBAT2	MLOWBAT1	MACOK	MPMICHOT	RESER'	VED_MPWRSRC	INT[2:0]
R-0h	R/W-1h	R/W-1h	R/W-1h	R/W-1h		R-0h	

Bit	Field	Туре	Reset	Description
7	RESERVED1_MPWRSRCINT	R	0h	
6	MLOWBAT2	R/W	1h	Low battery voltage mask interrupt 0h = Not masked
				1h = Masked
5	MLOWBAT1	R/W	1h	Low battery voltage mask interrupt
				0h = Not masked
				1h = Masked
4	МАСОК	R/W	1h	AC/DC adapter detection mask interrupt
				0h = Not masked
				1h = Masked
3	МРМІСНОТ	R/W	1h	PMIC internal temperature mask interrupt
				0h = Not masked
				1h = Masked
2-0	RESERVED_MPWRSRCINT[2:0]	R	0h	

Table 6-11. MPWRSRCINT Register Field Descriptions

6.6.10 RESETIRQ1MASK Register (address = 0x11) [reset = 0x30]

RESETIRQ1MASK is shown in Figure 6-31 and described in Table 6-12.

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Register domain: RTC

Figure 6-31. RESETIRQ1MASK Register

7	6	5	4	3	2	1	0
RESERVED1_R K[1		MFCO	MVRFAULT		RESERVED_RES	ETIRQ1MASK[3:0]
R-0)h	R/W-1h	R/W-1h		R	-0h	

Table 6-12. RESETIRQ1MASK Register Field Descriptions

Bit	Field	Туре	Reset	Description
7-6	RESERVED1_RESETIRQ1MASK[1: 0]	R	0h	
5	MFCO	R/W	1h	Power button triggered reset mask interrupt 0h = Not masked 1h = Masked
4	MVRFAULT	R/W	1h	Voltage regulator triggered reset mask interrupt 0h = Not masked 1h = Masked
3-0	RESERVED_RESETIRQ1MASK[3:0]	R	0h	

6.6.11 RESETIRQ2MASK Register (address = 0x12) [reset = 0x02]

RESETIRQ2MASK is shown in Figure 6-32 and described in Table 6-13.

Return to Summary Table.

Register domain: RTC

Figure 6-32. RESETIRQ2MASK Register

7	6	5	4	3	2	1	0
	R	ESERVED1_RES	ETIRQ2MASK[5:	0]		MCRITTEMP	RESERVED_R ESETIRQ2 MASK
		R-	0h			R/W-1h	R-0h

Table 6-13. RESETIRQ2MASK Register Field Descriptions

Bit	Field	Туре	Reset	Description
7-2	RESERVED1_RESETIRQ2MASK[5: 0]	R	0h	
1	MCRITTEMP	R/W	1h	Temperature triggered reset mask interrupt 0h = Not masked 1h = Masked
0	RESERVED_RESETIRQ2 MASK	R	0h	

6.6.12 IRQLVL1msK Register (address = 0x13) [reset = 0xA5]

IRQLVL1msK is shown in Figure 6-33 and described in Table 6-14.

Return to Summary Table.

Register domain: RTC

Figure 6-33. IRQLVL1msK Register

7	6	5	4 3	2	1	0
MRESET	RESERVED2_I RQLVL1msK	MPMU	RESERVED1_IRQLVL1msK[1:0]	MPWRSRC	RESERVED_IR QLVL1msK	MPWRBTN
R/W-1h	R-0h	R/W-1h	R-0h	R/W-1h	R-0h	R/W-1h

Table 6-14. IRQLVL1msK Register Field Descriptions

Bit	Field	Туре	Reset	Description
7	MRESET	R/W	1h	RESET mask interrupt
				0h = Not masked
				1h = Masked
6	RESERVED2_IRQLVL1msK	R	0h	
5	MPMU	R/W	1h	Power monitor mask interrupt
				0h = Not masked
				1h = Masked
4-3	RESERVED1_IRQLVL1msK[1:0]	R	0h	
2	MPWRSRC	R/W	1h	Power source mask interrupt
				0h = Not masked
				1h = Masked
1	RESERVED_IRQLVL1msK	R	0h	
0	MPWRBTN	R/W	1h	Power button mask interrupt
				0h = Not masked
				1h = Masked

6.6.13 PBCONFIG Register (address = 0x14) [reset = 0x1F]

PBCONFIG is shown in Figure 6-34 and described in Table 6-15.

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Register domain: RTC

Figure 6-34. PBCONFIG Register

7	6	5	4	3	2	1	0
PWRBTNDBN	CLRHT			FLT	[5:0]		
R/W-0h	R/W-0h			R/W	/-1Fh		

Bit	Field	Туре	Reset	Description
7	PWRBTNDBN	R/W	0h	Power button debounce
				0h = 30 ms
				1h = 0 ms (no debounce)
6	CLRHT	R/W	0h	Reset of power button timer logic
				0h = No action
				1h = Reset of HT, bit is self clearing
5-0	FLT[5:0]	R/W	1Fh	Time that the button must be held to force an emergency reset
				0h: 0 s
				1h: 1 s
				2h: 2 s
				3h: 3 s
				4h: 4 s
				5h = 5 s
				6h: 6 s
				7h: 7 s
				8h: 8 s
				9h: 9 s
				Ah: 10 s
				1Fh: 31 s
				3Ch: 60 s
				3Dh: 61 s
				3Eh: 62 s
				3Fh: 63 s

Table 6-15. PBCONFIG Register Field Descriptions

6.6.14 PBSTATUS Register (address = 0x15) [reset = 0x00]

PBSTATUS is shown in Figure 6-35 and described in Table 6-16.

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Register domain: RTC

Figure 6-35. PBSTATUS Register

7	6	5	4	3	2	1	0
RESERVED_P BSTATUS	LVL			HT	[5:0]		
R-0h	R-0h			R	-0h		

Bit	Field	Туре	Reset	Description
7	RESERVED_PBSTATUS	R	0h	
6	LVL	R	0h	Power button present level
				0h = Power button held
				1h = Power button released
5-0	HT[5:0]	R	0h	Time that the button has been held
				0h = Disabled
				1h = Disabled
				2h = 2 s
				3h = 3 s
				4h = 4 s
				5h = 5 s
				6h = 6 s
				7h = 7 s
				8h = 8 s
				9h = 9 s
				Ah = 10 s
				3Ch = 60 s
				3Dh = 61 s
				3Eh = 62 s
				3Fh = 63 s

Table 6-16. PBSTATUS Register Field Descriptions

6.6.15 PWRSTAT1 Register (address = 0x16) [reset = 0x00]

PWRSTAT1 is shown in Figure 6-36 and described in Table 6-17.

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Register domain: RTC

Figure 6-36. PWRSTAT1 Register

7	6	5	4	3	2	1	0
VCCIO_FAULT	V5A_FAULT	V33A_PCH_FA ULT	V33A_DSW_F AULT	V18A_FAULT	V18U_25U_FA ULT	VDDQ_FAULT	V06DX_FAULT
R/W-0h	R/W-0h	R/W-0h	R/W-0h	R/W-0h	R/W-0h	R/W-0h	R/W-0h

Table 6-17. PWRSTAT1 Register Field Descriptions

Bit	Field	Туре	Reset	Description
7	VCCIO_FAULT	R/W	0h	These bits indicate that the VR has lost regulation
				0h = Clears register
				1h = Indicates power fault
6	V5A_FAULT	R/W	0h	These bits indicate that the VR has lost regulation
				0h = Clears register
				1h = Indicates power fault
4	V33A_PCH_FAULT	R/W	0h	These bits indicate that the VR has lost regulation
				0h = Clears register
				1h = Indicates power fault
5	V33A_DSW_FAULT	R/W	0h	These bits indicate that the VR has lost regulation
				0h = Clears register
				1h = Indicates power fault
3	V18A_FAULT	R/W	0h	These bits indicate that the VR has lost regulation
				0h = Clears register
				1h = Indicates power fault
2	V18U_25U_FAULT	R/W	0h	These bits indicate that the VR has lost regulation
				0h = Clears register
				1h = Indicates power fault
1	VDDQ_FAULT	R/W	0h	These bits indicate that the VR has lost regulation
				0h = Clears register
				1h = Indicates power fault
0	V06DX_FAULT	R/W	0h	These bits indicate that the VR has lost regulation
				0h = Clears register
				1h = Indicates power fault

6.6.16 PWRSTAT2 Register (address = 0x17) [reset = 0x00]

PWRSTAT2 is shown in Figure 6-37 and described in Table 6-18.

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Register domain: RTC

Figure 6-37. PWRSTAT2 Register

7	6	5	4	3	2	1	0
	RESERVED[5:0]						VPRIMCORE_ FAULT
		R/W-0h	R/W-0h				

Table 6-18. PWRSTAT2 Register Field Descriptions

Bit	Field	Туре	Reset	Description
7-2	RESERVED[5:0]	R	0h	
1	V105A_FAULT	R/W	0h	These bits indicate that the VR has lost regulation 0h = Clears register 1h = Indicates power fault
0	VPRIMCORE_FAULT	R/W	0h	These bits indicate that the VR has lost regulation 0h = Clears register 1h = Indicates power fault

6.6.17 PGMASK1 Register (address = 0x18) [reset = 0x00]

PGMASK1 is shown in Figure 6-38 and described in Table 6-19.

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Register domain: RTC

Figure 6-38. PGMASK1 Register

			•		•		
7	6	5	4	3	2	1	0
MVCCIOPG	MVPRIMCORE PG	MV105APG	MV18APG	MV33ADSWPG	MV5APG	MV33APCHPG	MV105SPG
R/W-0h	R/W-0h	R/W-0h	R/W-0h	R/W-0h	R/W-0h	R/W-0h	R/W-0h

Bit	Field	Туре	Reset	Description
7	MVCCIOPG	R/W	0h	VCCIO PG is part of the power good tree
				Oh = Power good function is enabled
				1h = Power good function is masked and set to 1 (not part of the power good tree)
6	MVPRIMCOREPG	R/W	0 h	V0.85A PG is part of the power good tree
				0h = Power good function is enabled
				1h = Power good function is masked and set to 1 (not part of the power good tree)
5	MV105APG	R/W	0h	V105A PG is part of the power good tree
				0h = Power good function is enabled
				1h = Power good function is masked and set to 1 (not part of the power good tree)
4	MV18APG	R/W	0h	V1.8A PG is part of the power good tree
				0h = Power good function is enabled
				1h = Power good function is masked and set to 1 (not part of the power good tree)
3	MV33ADSWPG	R/W	0h	V3.3A DSW PG is part of the power good tree
				0h = Power good function is enabled
				1h = Power good function is masked and set to 1 (not part of the power good tree)
2	MV5APG	R/W	0h	V5AA DS3 PG is part of the power good tree
				0h = Power good function is enabled
				1h = Power good function is masked and set to 1 (not part of the power good tree)
1	MV33APCHPG	R/W	0h	V3.3A PCH PG is part of the power good tree
				0h = Power good function is enabled
				1h = Power good function is masked and set to 1 (not part of the power good tree)
0	MV105SPG	R/W	0h	V105S PG is part of the power good tree
				0h = Power good function is enabled
				1h = Power good function is masked and set to 1 (not part of the

Table 6-19. PGMASK1 Register Field Descriptions

power good tree)

6.6.18 PGMASK2 Register (address = 0x19) [reset = 0x00]

PGMASK2 is shown in Figure 6-39 and described in Table 6-20.

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Register domain: RTC

Figure 6-39. PGMASK2 Register

			-		-		
7	6	5	4	3	2	1	0
	RESERVED_P	GMASK2[3:0]		V18U25UPG	MVDDQPG	MV33SPG	MV18SPG
	R-(Dh		R/W-0h	R/W-0h	R/W-0h	R/W-0h

Table 6-20. PGMASK2 Register Field Descriptions

Bit	Field	Туре	Reset	Description
7-4	RESERVED_PGMASK2[3:0]	R	0h	
3	V18U25UPG	PG R/W 0h		V1.8_2.5U PG is part of the power good tree
				0h = Power good function is enabled
				1h = Power good function is masked and set to 1 (not part of the power good tree)
2	MVDDQPG	R/W	0h	VDDQ PG is part of the power good tree
				0h = Power good function is enabled
				1h = Power good function is masked and set to 1 (not part of the power good tree)
1	MV33SPG	R/W	0h	V3.3S PG is part of the power good tree
				0h = Power good function is enabled
				1h = Power good function is masked and set to 1 (not part of the power good tree)
0	MV18SPG	R/W	0h	V1.8S PG is part of the power good tree
				0h = Power good function is enabled
				1h = Power good function is masked and set to 1 (not part of the power good tree)

6.6.19 VCCIOCNT Register (address = 0x30) [reset = 0x1Ah]

VCCIOCNT is shown in Figure 6-40 and described in Table 6-21.

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Register domain: RESET

Figure 6-40. VCCIOCNT Register

7	6	5	4	3	2	1	0
RESERVED_V CCIOCNT	CSDECAYEN	RESERVED_	VCCIOVSEL	RESE	RVED	CTLVVC	CIO[1:0]
R-0h	R/W-0h	R-	1h	R-	-2h	R/V	V-2h

Table 6-21. VCCIOCNT Register Field Descriptions

Bit	Field	Туре	Reset	Description
7	RESERVED_VCCIOCNT	R	0h	
6	CSDECAYEN	R/W	0h	Enables VCCIO decay when $\overline{\text{SLP}_S0}$ is asserted. Wait 2 µs after removing FPWM, before entering DECAY mode. Direct FPWM to DECAY by $\overline{\text{SLP}_S0}$ may cause ringing. Decay exit time within 100 µs not ensured for V _{OUT} > 1 V.)
				0h = VCCIO stays at voltage set by VCCIOVSEL independent of state of SLP_S0
				$\frac{1h = VCCIO}{SLP_S0}$ decays to 0 V, PGOOD is maintained when $\frac{1}{SLP_S0}$ is asserted (low)
5-4	RESERVED_VCCIOVSEL	R	1h	
3-2	RESERVED	R	2h	
1-0	CTLVVCCIO[1:0]	R/W	2h	Mode control (VCCIO)
				0h = Converter disabled
				1h = Auto Mode, automatic transition from PFM to PWM
				2h = Auto Mode, automatic transition from PFM to PWM
				3h = Forced PWM operation

6.6.20 VPRIMCORECNT Register (address = 0x31) [reset = 0x4A]

VPRIMCORECNT is shown in Figure 6-41 and described in Table 6-22.

Return to Summary Table.

Register domain: RESET

Figure 6-41. VPRIMCORECNT Register

7	6	5	4	3	2	1	0
VPRIMCORELVSEL[1:0]		VPRIMCOF	EVSEL[1:0]	AOACCNTVP	RIMCORE[1:0]	CTLVPRIM	/CORE[1:0]
R/W-1h		R/W	/-0h	R/V	V-2h	R/V	V-2h

Bit	Field	Туре	Reset	Description
7-6	VPRIMCORELVSEL[1:0]	R/W	1h	VPRIMCORE low power mode output voltage set point Set at assertion of SLP_S0
				0h = Disabled, voltage stays at value set by VPRIMCOREVSEL[1:0]
				1h = 0.75 V
				2h = 0.8 V
				3h = 0.85 V
5-4	VPRIMCOREVSEL[1:0]	R/W	0h	Output voltage select
				0h = 0.95 V
				1h = 0.9 V
				2h = 0.85 V
				3h = 0.8 V
3-2	AOACCNTVPRIMCORE[1:0]	R/W	2h	Mode control for exit standby (rising edge of SLP_S0) Changes bits on exit
				0h = No change in bits; fast change mode disabled
				1h = Auto Mode, automatic transition from PFM to PWM
				2h = Auto Mode, automatic transition from PFM to PWM
				3h = Forced PWM operation
1-0	CTLVPRIMCORE[1:0]	R/W	2h	Mode control (VPRIMCORE)
				0h = Converter disabled
				1h = Auto Mode, automatic transition from PFM to PWM
				2h = Auto Mode, automatic transition from PFM to PWM
				3h = Forced PWM operation

Table 6-22. VPRIMCORECNT Register Field Descriptions

6.6.21 V33ADSWCNT Register (address = 0x32) [reset = 0x2A]

V33ADSWCNT is shown in Figure 6-42 and described in Table 6-23.

Return to Summary Table.

Register domain: RESET

Figure 6-42. V33ADSWCNT Register

7	6	5	4	3	2	1	0	
V33ADSWLVSEL[1:0]		V33ADSW	V33ADSWVSEL[1:0]		33ADSW[1:0]	CTLV33ADSW[1:0]		
R/V	V-0h	R/W	/-2h	R/V	V-2h	R/V	V-2h	

Bit	Field	Туре	Reset	Description
7-6	V33ADSWLVSEL[1:0]	R/W	0h	V33A_DSW low power mode output voltage set point - set at assertion of SLP_S0
				0h = Disabled, voltage stays at value set by V33ADSWVSEL[1:0]
				1h = Vnom – 4%
				2h = Vnom - 3%
				3h = Vnom – 2%
5-4	V33ADSWVSEL[1:0]	R/W	2h	Output voltage select
				0h = Vnom + 3 %
				1h = Vnom + 2 %
				2h = Vnom
				3h = Vnom – 2 %
3-2	AOACCNTV33ADSW[1:0]	R/W	2h	Mode control for exit standby (rising edge of SLP_S0) Changes bits on exit
				0h = No change in bits; fast change mode disabled
				1h = Auto Mode, automatic transition from PFM to PWM
				2h = Auto Mode, automatic transition from PFM to PWM
				3h = Forced PWM operation
1-0	CTLV33ADSW[1:0]	R/W	2h	Mode control (V33ADSW)
				0h = Converter disabled
				1h = Auto Mode, automatic transition from PFM to PWM
				2h = Auto Mode, automatic transition from PFM to PWM
				3h = Forced PWM operation

Table 6-23. V33ADSWCNT Register Field Descriptions

6.6.22 V33APCHCNT Register (address = 0x33) [reset = 0x0A]

V33APCHCNTis shown in Figure 6-43 and described in Table 6-24.

Return to Summary Table.

Register domain: RESET

Figure 6-43. V33APCHCNT Register

7	6	5	4	3	2	1	0
	RESERVED_V33	APCHCNT[3:0]		RESE	RVED	CTLV33/	APCH[1:0]
R/W-0h			R/V	V-2h	R/V	V-2h	

Bit	Field	Туре	Reset	Description
7-4	RESERVED_V33APCHCNT[3:0]	R/W	0h	
3-2	RESERVED	R	2h	
1-0	CTLV33APCH[1:0]	R/W	2h	Mode control (V33APCH) 0h = Disabled 1h = Enabled 2h = Enabled 3h = Enabled

Table 6-24. V33APCHCNT Register Field Descriptions

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6.6.23 V18ACNT Register (address = 0x34) [reset = 0x2A]

V18ACNT is shown in Figure 6-44 and described in Table 6-25.

Return to Summary Table.

Register domain: RESET

Figure 6-44. V18ACNT Register

7	6	5	4	3	2	1	0
V18ALVSEL[1:0]		V18AVSEL[1:0]		AOACCNTV18A[1:0]		CTLV18A[1:0]	
R/W-0h		R/W-2h		R/W	V-2h	R/W-2h	

Bit	Field	Туре	Reset	Description
7-6	V18ALVSEL[1:0]	R/W	0h	V18A low power mode output voltage set point Set at assertion of SLP_S0
				0h = Disabled, voltage stays at value set by V18AVSEL[1:0]
				1h = Vnom – 4%
				2h = Vnom – 3%
				3h = Vnom – 2%
5-4	V18AVSEL[1:0]	R/W	2h	Output voltage select
				0h = Vnom + 3 %
				1h = Vnom + 2 %
				2h = Vnom
				3h = Vnom - 2 %
3-2	AOACCNTV18A[1:0]	R/W	2h	Mode control for exit standby (rising edge of SLP_S0) Changes bits on exit
				0h = No change in bits; fast change mode disabled
				1h = Auto Mode, automatic transition from PFM to PWM
				2h = Auto Mode, automatic transition from PFM to PWM
				3h = Forced PWM operation
1-0	CTLV18A[1:0]	R/W	2h	Mode control (V18A)
				0h = Converter disabled
				1h = Auto Mode, (automatic transition from PFM to PWM)
				2h = Auto Mode, (automatic transition from PFM to PWM)
				3h = Forced PWM operation

Table 6-25. V18ACNT Register Field Descriptions

6.6.24 V18U25UCNT Register (address = 0x35) [reset = 0x0A]

V18U25UCNT is shown in Figure 6-45 and described in Table 6-26.

Return to Summary Table.

Register domain: RESET

Figure 6-45. V18U25UCNT Register

7	6	5	4	3	2	1	0
RESERVED_V18U25UCNT[3:0]			RESERVED_AOACCNTV18U25 U		CTLV18U25U[1:0]		
R-0h				R-2h		R/W-2h	

Table 6-26. V18U25UCNT Register Field Descriptions

Bit	Field	Туре	Reset	Description
7-4	RESERVED_V18U25UCNT[3:0]	R	0h	
3-2	RESERVED_AOACCNTV18U25U	R	2h	
1-0	CTLV18U25U[1:0]	R/W	2h	Mode control (V18U25U) 0h = Disabled 1h = Enabled 2h = Enabled
				3h = Enabled

6.6.25 VDDQCNT Register (address = 0x36) [reset = 0x3A]

VDDQCNT is shown in Figure 6-46 and described in Table 6-27.

Return to Summary Table.

Register domain: RESET

Figure 6-46. VDDQCNT Register

7	6	5	4	3	2	1	0
VDDQLVSEL	VDDQVSEL[2:0]		AOACCNT	[VDDQ[1:0]	CTLVD	DQ[1:0]	
R/W-0h	R/W-3h		R/V	V-2h	R/V	V-2h	

Bit	Field	Туре	Reset	Description
7	VDDQLVSEL	R/W	0h	VDDQ low <u>power</u> mode output voltage set point - set at assertion of SLP_S0
				0h = Disabled, voltage stays at value set by VDDQVSEL
				1h = Vnom – 3%
6-4	VDDQVSEL[2:0]	R/W	3h	Output voltage select
				0h = Vnom + 3%
				1h = Vnom + 2%
				2h = Vnom + 1%
				3h = Vnom + 0%
				4h = Vnom – 1%
				5h = Vnom – 2%
				6h = Vnom – 3%
				7h = Vnom – 4%
3-2	AOACCNTVDDQ[1:0]	R/W	2h	Mode control for exit standby (rising edge of $\overline{\text{SLP}_{S0}}$) Changes bits on exit
				0h = no change in bits; fast change mode disabled
				1h = Auto Mode, automatic transition from PFM to PWM
				2h = Auto Mode, automatic transition from PFM to PWM
				3h = forced PWM operation
1-0	CTLVDDQ[1:0]	R/W	2h	Mode control (VDDQ)
				0h = Converter disabled
				1h = Auto Mode, automatic transition from PFM to PWM
				2h = Auto Mode, automatic transition from PFM to PWM
				3h = Forced PWM operation

Table 6-27. VDDQCNT Register Field Descriptions

6.6.26 V105ACNT Register (address = 0x37) [reset = 0x0A]

V105ACNT is shown in Figure 6-47 and described in Table 6-28.

Return to Summary Table.

Register domain: RESET

Figure 6-47. V105ACNT Register

7	6	5	4	3	2	1	0	
V105ALVSEL[1:0]		V105AV	V105AVSEL[1:0]		AOACCNTV105A[1:0]		CTLV105A[1:0]	
R/W-0h		R/V	V-0h	R/V	V-2h	R/W	V-2h	

Bit	Field	Туре	Reset	Description
7-6	V105ALVSEL[1:0]	R/W	Oh	V105A low power mode output voltage set point Set at assertion of SLP_S0
				0h = Disabled, voltage stays at value set by V105AVSEL[1:0]
				1h = Vnom – 4%
				2h = Vnom – 3%
				3h = Vnom – 2%
5-4	V105AVSEL[1:0]	R/W	0h	Output voltage select
				0h = Vnom + 5 % (1.05 V)
				1h = Vnom (1 V)
				2h = Vnom -2.5 % (0.975 V)
				3h = Vnom – 5 % (0.95 V)
3-2	AOACCNTV105A[1:0]	R/W	2h	Mode control for exit standby (rising edge of $\overline{\text{SLP}_{S0}}$) Changes bits on exit
				0h = No change in bits D[1:0], fast change mode disabled
				1h = Auto Mode, automatic transition from PFM to PWM
				2h = Auto Mode, automatic transition from PFM to PWM
				3h = Forced PWM operation
1-0	CTLV105A[1:0]	R/W	2h	Mode control (V105A)
				0h = Converter disabled
				1h = Auto Mode, automatic transition from PFM to PWM
				2h = Auto Mode, automatic transition from PFM to PWM
				3h = Forced PWM operation

Table 6-28. V105ACNT Register Field Descriptions

6.6.27 V5ACNT Register (address = 0x38) [reset = 0x2A]

V5ACNT is shown in Figure 6-48 and described in Table 6-29.

Return to Summary Table.

Register domain: RESET

Figure 6-48. V5ACNT Register

			-		-		
7	6	5	4	3	2	1	0
RESERVED_V	5ALVSEL[1:0]	RESERVED_	V5AVSEL[1:0]	RESERVED	AOACCNTV5A[1:0]	RESERVED_	CTLV5A[1:0]
R-0)h	R-	2h		R-2h	R-	2h

Bit	Field	Туре	Reset	Description
7-6	RESERVED_V5ALVSEL[1:0]	R	0h	V5A low power mode output voltage set point Set at assertion of SLP_S0
				0h = Disabled, voltage stays at value set by V5AVSEL[1:0]
				1h = Vnom – 4%
				2h = Vnom – 3%
				3h = Vnom – 2%
5-4	RESERVED_V5AVSEL[1:0]	R	2h	Output voltage select
				0h = Vnom + 3 %
				1h = Vnom + 2 %
				2h = Vnom
				3h = Vnom – 2 %
3-2	RESERVED_AOACCNTV5A[1:0]	R	2h	Mode control for exit standby (rising edge of SLP_S0) Changes bits on exit
				0h = No change in bits; fast change mode disabled
				1h = Auto Mode, (automatic transition from PFM to PWM)
				2h = Auto Mode, (automatic transition from PFM to PWM)
				3h = Forced PWM operation
1-0	RESERVED_CTLV5A[1:0]	R	2h	Mode control (V5A)
				0h = Converter disabled
				1h = Auto Mode, (automatic transition from PFM to PWM)
				2h = Auto Mode, (automatic transition from PFM to PWM)
				3h = Forced PWM operation

Table 6-29. V5ACNT Register Field Descriptions

6.6.28 VRMODECTRL Register (address = 0x3B) [reset = 0x3F]

VRMODECTRL is shown in Figure 6-49 and described in Table 6-30.

Return to Summary Table.

Register domain: RESET

Figure 6-49. VRMODECTRL Register

7 6	5	4	3	2	1	0
RESERVED_VRMODECTRL[1:0]	V33APCH_LP M	RESERVED_V CCIO_LPM	RESERVED_V 5A_LPM	VDDQ_LPM	V105A_LPM	VPRIMCORE_ LPM
R-0h	R/W-1h	R/W-1h	R/W-1h	R/W-1h	R/W-1h	R/W-1h

Table 6-30. VRMODECTRL Register Field Descriptions

Bit	Field	Туре	Reset	Description
7-6	RESERVED_VRMODECTRL[1:0]	R	0h	
5	V33APCH_LPM	R/W	1h	Force low power mode (Auto mode). This feature is only used if forcing PWM in the CTLV33APCH[1:0] bits of the V33APCHCNT register.
				0h = Force Auto mode when $\overline{\text{STANDBY}}$ ($\overline{\text{SLP}_S0}$) is asserted (low). This overrides the setting of the V33APCHCNT register, bits CTLV33APCH[1:0] when STANDBY is low.
				$\begin{array}{llllllllllllllllllllllllllllllllllll$
4	RESERVED_VCCIO_LPM	R	1h	Force low power mode (Auto mode). This is only used if forcing PWM in CTLVCCIO[1:0] bits of VCCIOCNT register.
				0h = Force Auto mode when $\overline{\text{STANDBY}}$ ($\overline{\text{SLP}_S0}$) is asserted (low). This overrides the setting of the VCCIOCNT register, bits CTLVCCIO[1:0] when $\overline{\text{STANDBY}}$ is low.
				$\begin{array}{llllllllllllllllllllllllllllllllllll$
3	RESERVED_V5A_LPM	R	1h	Force low power mode (Auto mode). This is only used if forcing PWM in CTLVPRIMCORE[1:0] register.
				0h = Force Auto mode when $\overline{\text{STANDBY}}$ ($\overline{\text{SLP}_{S0}}$) is asserted (low). This overrides the setting of the VPRIMCORECNT register, bits CTLVPRIMCORE[1:0] when $\overline{\text{STANDBY}}$ is low.
				$\begin{array}{llllllllllllllllllllllllllllllllllll$
2	VDDQ_LPM	R/W	1h	Force low power mode (Auto mode). This is only used if forcing PWM in CTLVDDQ[1:0] bits in VDDQCNT register.
				0h = Force Auto mode when $\overline{\text{STANDBY}}$ (SLP_S0) is asserted (low). This overrides the setting of the VDDQCNT register, bits CTLVDDQ[1:0] when $\overline{\text{STANDBY}}$ is low}
				$\begin{array}{l} 1h = Mode \mbox{ set by CTLVDDQ[1:0] bits when } \overline{\mbox{STANDBY}} \\ (\overline{\mbox{SLP}_S0}). \mbox{ Does what is setting of register bits CTLVDDQ[1:0]} \\ when \mbox{STANDBY is low.} \end{array}$



	Table 6-30.	VRMODECTRL	Register Field	Descriptions	(continued)	
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Bit	Field	Туре	Reset	Description
1	V105A_LPM	R/W	1h	Force low power mode (Auto mode). This is only used if forcing PWM in CTLV105A [1:0] bits in V105ACNTregister. $0h = Force Auto mode when STANDBY (SLP_SO)$ is asserted
				(low). This overrides th <u>e setting</u> of the V105ACNT register, bits CTLV105A [1:0] when STANDBY is low.
				$\frac{1h = Mode}{(SLP_S0). Does}$ what is setting of register bits CTLV105A[1:0] when STANDBY is low.
0	VPRIMCORE_LPM	R/W	1h	Force low power mode (Auto mode). This is only used if forcing PWM in CTLV5A [1:0] bits in V5ACNT register.
				0h = Force Auto mode when $\overline{\text{STANDBY}}$ (SLP_S0) is asserted (low). This overrides the setting of the V5A register, CNT bits CTLVV33ADSW[1:0] when STANDBY is low.
				1h = Mode set by CTLV5A [1:0] bits when $\overline{\text{STANDBY}}$ ($\overline{\text{SLP}_S0}$). Does what is setting of register bits CTLV5A [1:0] when STANDBY is low.

6.6.29 DISCHCNT1 Register (address = 0x3C) [reset = 0x00]

DISCHCNT1 is shown in Figure 6-50 and described in Table 6-31.

Return to Summary Table.

Register domain: RESET

Figure 6-50. DISCHCNT1 Register

7	6	5 4 3				1	0
RESERVED_DISCHCNT1[5:0]						VCCIODI	SCHG[1:0]
							N-0h

Table 6-31. DISCHCNT1 Register Field Descriptions

Bit	Field	Туре	Reset	Description
7-2	RESERVED_DISCHCNT1[5:0]	R	0h	
1-0	VCCIODISCHG[1:0]	R/W	0h	VCCIO discharge resistance $0h = >1000 \text{ k}\Omega$ $1h = 125 \Omega$ $2h = 225 \Omega$ $3h = 550 \Omega$

6.6.30 DISCHCNT2 Register (address = 0x3D) [reset = 0x00]

DISCHCNT2 is shown in Figure 6-51 and described in Table 6-32.

Return to Summary Table.

Register domain: RESET

Figure 6-51. DISCHCNT2 Register

7	6	5	4	3	2	1	0
V5ADIS	CHG[1:0]	V33APCHDISCHG[1:0]		V33PCHDISCHG[1:0]		V18ADISCH[1:0]	
R/\	R/W-0h R/W-0h		R/W	/-0h	R/W	/-0h	

Bit	Field	Туре	Reset	Description
7-6	V5ADISCHG[1:0]	R/W	0h	V5A discharge resistance
				0h = No discharge
				1h = 100 Ω
				$2h = 200 \Omega$
				$3h = 500 \ \Omega$
5-4	V33APCHDISCHG[1:0]	R/W	0h	V33A_PCH discharge resistance
				0h = No discharge
				1h = 100 Ω
				$2h = 200 \Omega$
				3h = 500 Ω
3-2	V33PCHDISCHG[1:0]	R/W	0h	V33A_PCH discharge resistance at VSA
				0h = No discharge
				1h = 100 Ω
				2h = 200 Ω
				$3h = 500 \ \Omega$
1-0	V18ADISCH[1:0]	R/W	0h	V18A discharge resistance
				$0h = 860 \ \Omega$
				1h = 100 Ω
				2h = 200 Ω
				3h = 500 Ω

Table 6-32. DISCHCNT2 Register Field Descriptions

6.6.31 DISCHCNT3 Register (address = 0x3E) [reset = 0x00]

DISCHCNT3 is shown in Figure 6-52 and described in Table 6-33.

Return to Summary Table.

Register domain: RESET

Figure 6-52. DISCHCNT3 Register

7	6	5	4	3	2	1	0
V18U25L	V18U25UDISCHG[1:0] VDDQDISCHG[1:		SCHG[1:0]	V105ADIS	SCHG[1:0]	VPRIMCOR	EDISCH[1:0]
R/W-0h R/W-0		/-0h	R/W	/-0h	R/W	/-0h	

Bit	Field	Туре	Reset	Description
7-6	V18U25UDISCHG[1:0]	R/W	0h	V1.8U_2.5U discharge resistance at VSB
				0h = No discharge
				1h = 100 Ω
				2h = 200 Ω
				3h = 500 Ω
5-4	VDDQDISCHG[1:0]	R/W	0h	VDDQ discharge resistance at FBVR4P
				0h = >1000 kΩ
				1h = 125 Ω
				2h = 225 Ω
				3h = 550 Ω
3-2	V105ADISCHG[1:0]	R/W	0h	V105A discharge resistance at FBVR1P
				0h = >1000 kΩ
				1h = 125 Ω
				2h = 225 Ω
				3h = 550 Ω
1-0	VPRIMCOREDISCH[1:0]	R/W	0h	VPRIMCORE discharge resistance
				0h = >1000 kΩ
				1h = 150 Ω
				2h = 250 Ω
				3h = 575 Ω

Table 6-33. DISCHCNT3 Register Field Descriptions

6.6.32 DISCHCNT4 Register (address = 0x3F) [reset = 0x00]

DISCHCNT4 is shown in Figure 6-53 and described in Table 6-34.

Return to Summary Table.

Register domain: RESET

Figure 6-53. DISCHCNT4 Register

					-		
7	6	5	4	3	2	1	0
RESERVED_DISCHCNT4[1:0] V33SDISCHG[1:0]		V18SDIS	CHG[1:0]	V105SDI	SCH[1:0]		
R	R-0h R/W-0h		R/W	/ -0h	R/W	'-0h	

Bit	Field	Туре	Reset	Description
7-6	RESERVED_DISCHCNT4[1:0]	R	0h	
5-4	V33SDISCHG[1:0]	R/W	0h	V3.3S discharge resistance at VSE
				0h = No discharge
				1h = 100 Ω
				2h = 200 Ω
				$3h = 500 \ \Omega$
3-2	V18SDISCHG[1:0]	R/W	0h	V18S discharge resistance at VSF
				0h = No discharge
				1h = 100 Ω
				2h = 200 Ω
				3h = 500 Ω
1-0	V105SDISCH[1:0]	R/W	0h	V105S discharge resistance at VSG
				0h = No discharge
				1h = 100 Ω
				2h = 200 Ω
				3h = 500 Ω

Table 6-34. DISCHCNT4 Register Field Descriptions

6.6.33 PWRGDCNT1 Register (address = 0x40) [reset = 0x5F]

PWRGDCNT1 is shown in Figure 6-54 and described in Table 6-35.

Return to Summary Table.

Register domain: RESET

Figure 6-54. PWRGDCNT1 Register

7	6	5	4	3	2	1	0
RESERVED_P WRGDCNT1	RSMRSTN_I	PWRGD[1:0]	PCH_PW	ROK[1:0]	DEL	_ALL_SYS_PWR0	GD[2:0]
R-0h	R/W	/-2h	R/W	-3h		R/W-7h	

Bit	Field	Туре	Reset	Description
7	RESERVED_PWRGDCNT1	R	0h	
6-5	RSMRSTN_PWRGD[1:0]	R/W	2h	Delay of RSMRSTN_PWRGD (RTC = 30.5 μ s ± 10%)
				0h = No Delay
				1h = 164x RTC (5.5 ms)
				2h = 360x RTC (11 ms)
				3h = 721x RTC (22 ms)
4-3	PCH_PWROK[1:0]	R/W	3h	Delay of PCH_PWROK compared to ALL_SYS_PWRGD (RTC = $30.5 \ \mu s \pm 10\%$)
				0h = 82x RTC (2.5 ms)
				1h = 164x RTC (5 ms)
				2h = 328x RTC (10 ms)
				3h = 656x RTC (20 ms)
2-0	DEL_ALL_SYS_PWRGD[2:0]	R/W	7h	Delay of SYS_PWR_OK compared to ALL_SYS_PWRGD (RTC = 30.5 μs \pm 10%)
				0h = 82x RTC (2.5 ms)
				1h = 164x RTC (5 ms)
				2h = 328x RTC (10 ms)
				3h = 492x RTC (15 ms)
				4h = 656x RTC (20 ms)
				5h = 1640x RTC (50 ms)
				6h = 2460x RTC (75 ms)
				7h = 3280x RTC (100 ms)

Table 6-35. PWRGDCNT1 Register Field Descriptions

6.6.34 VREN Register (address = 0x41) [reset = 0x00]

VREN is shown in Figure 6-55 and described in Table 6-36.

Return to Summary Table.

Register domain: RESET

Figure 6-55. VREN Register

7	6	5	4	3	2	1	0
	RESERVED_VREN[5:0]						EC_DS4
			R/W-0h	R/W-0h			

Table 6-36. VREN Register Field Descriptions

Bit	Field	Туре	Reset	Description
7-2	RESERVED_VREN[5:0]	R/W	0h	
1	EC_SLP_S4	R/W	0h	0h = Disable 1h = Enable
0	EC_DS4	R/W	0h	0h = Disable 1h = Enable

6.6.35 REGLOCK Register (address = 0x42) [reset = 0x00]

REGLOCK is shown in Figure 6-56 and described in Table 6-37.

Return to Summary Table.

Register domain: RESET

Figure 6-56. REGLOCK Register

7	6	5	4	3	2	1	0
	RESERVED[6:0]						
	R-0h						

Table 6-37. REGLOCK Register Field Descriptions

Bit	Field	Туре	Reset	Description
7-1	RESERVED[6:0]	R	0h	
0	CNTLOCK	R/W	Oh	Locks all VxCNT registers 0h = All VxCNT registers are unlocked and can be overwritten 1h = All VxCNT registers are locked and cannot be overwritten

6.6.36 VRENPINMASK Register (address = 0x43) [reset = 0x00]

VRENPINMASK is shown in Figure 6-57 and described in Table 6-38.

Return to Summary Table.

Register domain: RESET

Figure 6-57. VRENPINMASK Register

7	6	5	4	3	2	1	0
MVPRIMCORE EN	MV105AEN	MVDDQEN	MV18U25UEN	MV18AEN	MV33APCHEN	MV5AEN	MVCCIOEN
R/W-0h	R/W-0h	R/W-0h	R/W-0h	R/W-0h	R/W-0h	R/W-0h	R/W-0h

Table 6-38. VRENPINMASK Register Field Descriptions

Bit	Field	Туре	Reset	Description
7	MVPRIMCOREEN	R/W	0h	VPRIMCORE enable pin mask
				0h = VR enable pin controls VR enable
				1h = VR enable pin masked VxCTLV controls VR enable
6	MV105AEN	R/W	0h	
				V105A enable pin mask
				0h = VR enable pin controls VR enable
				1h = VR enable pin masked VxCTLV controls VR enable
5	MVDDQEN	R/W	0h	VDDQ enable pin mask
				0h = VR enable pin controls VR enable
				1h = VR enable pin masked VxCTLV controls VR enable
4	MV18U25UEN	R/W	0h	V18U25U enable pin mask
				h = VR enable pin controls VR enable
				1h = VR enable pin masked VxCTLV controls VR enable
3	MV18AEN	R/W	0h	V18A enable pin mask
				0h = VR enable pin controls VR enable
-		DAM	0	1h = VR enable pin masked VxCTLV controls VR enable
2	MV33APCHEN	R/W	0h	V33APCH enable pin mask
				0h = VR enable pin controls VR enable
				1h = VR enable pin masked VxCTLV controls VR enable
1	MV5AEN	R/W	0h	V5A enable pin mask
				0h = VR enable pin controls VR enable
				1h = VR enable pin masked VxCTLV controls VR enable
0	MVCCIOEN	R/W	0h	
Ŭ			5.1	VCCIO enable pin mask
				0h = VR enable pin controls VR enable
				1h = VR enable pin masked VxCTLV controls VR enable

6.6.37 RSTCTRL Register (address = 0x48) [reset = 0x1C]

RSTCTRL is shown in Figure 6-58 and described in Table 6-39.

Return to Summary Table.

Register domain: RTC

Figure 6-58. RSTCTRL Register

			-		-		
7	6	5	4	3	2	1	0
RESERVED_RSTCTRL[2:0]		TRST[1:0]		VTHRST[2:0]			
	R-0h		R/W	/-3h		R/W-4h	

Table 6-39. RSTCTRL Register Field Descriptions

Bit	Field	Туре	Reset	Description
7-5	RESERVED_RSTCTRL[2:0]	R	0h	
4-3	TRST[1:0]	R/W	3h	Reset time duration
				0h = 20 ms
				1h = 40 ms
				2h = 80 ms
				3h = 200 ms
2-0	VTHRST[2:0]	R/W	4h	Reset voltage threshold
				0h = 1.4 V
				1h = 1.5 V
				2h = 1.6 V
				3h = 1.7 V
				4h = 2.4 V
				5h = 2.6 V
				6h = 2.8 V
				7h = 3 V

6.6.38 SDWNCTRL Register (address = 0x49) [reset = 0x00]

SDWNCTRL is shown in Figure 6-59 and described in Table 6-40.

Return to Summary Table.

Register domain: RESET

Figure 6-59. SDWNCTRL Register

7	6	5	4	3	2	1	0
		RESE	RVED_SDWNCT	RL[6:0]			SDWN
			R-0h				R/W-0h

Table 6-40. SDWNCTRL Register Field Descriptions

Bit	Field	Туре	Reset	Description
7-1	RESERVED_SDWNCTRL[6:0]	R	0h	
0	SDWN	R/W	0h	Forced emergency reset, bit is self clearing 0h = No action
				1h = Force emergency reset

6.6.39 VDLMTCRT Register (address = 0x51) [reset = 0x05]

VDLMTCRT is shown in Figure 6-60 and described in Table 6-41.

Return to Summary Table.

Register domain: RESET

Figure 6-60. VDLMTCRT Register

7	6	5	4	3	2	1	0
RESERVED_V DLMTCRT	VDLMTCOMP	TDBNCVDLN	MTCRT[1:0]		VDLMTC	CRTH[3:0]	
R/W-0h	R/W-0h	R/W-	-0h		R/V	V-5h	

Bit	Field	Туре	Reset	Description
7	RESERVED_VDLMTCRT	R/W	0h	
6	VDLMTCOMP	R/W	0h	Critical supply voltage comparator for VDCSNS pin input voltage sense. Connect voltage divider resistors from VIN to detect when input voltage is low
				0h = disable
				1h = enable
5-4	TDBNCVDLMTCRT[1:0]	R/W	0h	Supply voltage monitor debounce of VDCSNS input voltage sense pin
				0h = No Deglitch
				1h = 10 μs
				2h = 1x RTC (30 μs)
				3h = 2x RTC (60 μs)
3-0	VDLMTCRTH[3:0]	R/W	5h	Critical supply voltage falling threshold on VDCSNS pin. Connect voltage divider resistors from VIN to detect when input voltage is low. For 2S should be 4X top resistor, X bottom resistor. (rising hysteresis = 20 mV)
				0h = No limit
				1h = 1.2 V
				2h = 1.18 V
				3h = 1.16 V
				4h = 1.14 V
				5h = 1.12 V
				6h = 1.1 V
				7h = 1.08 V
				8h to Fh = Not applicable

Table 6-41. VDLMTCRT Register Field Descriptions

6.6.40 ACOKDBDM Register (address = 0x69) [reset = 0x0F]

ACOKDBDM is shown in Figure 6-61 and described in Table 6-42.

Return to Summary Table.

Register domain: RESET

Figure 6-61. ACOKDBDM Register

7	6	5	4	3	2	1	0
	RESERVED_AC	COKDBDM[3:0]		ACOKDB[1:0]			DM[1:0]
	R/W	′-0h		R/V	V-3h	R/V	V-3h

Bit	Field	Туре	Reset	Description
7-4	RESERVED_ACOKDBDM[3:0]	R/W	0h	
3-2	ACOKDB[1:0]	R/W	3h	Adapter detection debounce time
				0h = 81 μs
				1h = 10 ms
				2h = 20 ms
				3h = 30 ms
1-0	ACOKDM[1:0]	R/W	3h	Adapter detection mode
				0h = reserved
				1h = low-to-high
				2h = high-to-low
				3h = both, low-to-high and high-to-low

Table 6-42. ACOKDBDM Register Field Descriptions

6.6.41 LOWBATTDET Register (address = 0x6A) [reset = 0xF8]

LOWBATTDET is shown in Figure 6-62 and described in Table 6-43.

Return to Summary Table.

Register domain: RESET

Figure 6-62. LOWBATTDET Register

7	6	5	4	3	2	1	0
LOWBAT	TDB[1:0]	LOWBATT2_E N	LOWBATT1_E N	ACIN_EN	RESER	VED_LOWBATTI	DET[2:0]
R/W	'-3h	R/W-1h	R/W-1h	R/W-1h		R/W-0h	

Table 6-43. LOWBATTDET Register Field Descriptions

Bit	Field	Туре	Reset	Description
7-6	LOWBATTDB[1:0]	R/W	3h	Low battery detection debounce time
				$0h = 4 RTC periods (120 \ \mu s)$
				1h = 32 RTC periods (960 μs)
				2h = 64 RTC periods (1920 μs)
				3h = 128 RTC periods (3840 μs)
5	LOWBATT2_EN	R/W	1h	Low battery two detection enable
				0h = Disable
				1h = Enable
4	LOWBATT1_EN	R/W	1h	Low battery One detection Enable
				0h = Disable
				1h = Enable
3	ACIN_EN	R/W	1h	AC IN Comparator
				0h = Disable
				1h = Enable
2-0	RESERVED_LOWBATTDET[2:0]	R/W	0h	

6.6.42 SPWRSRCINT Register (address = 0x6F) [reset = 0x00]

SPWRSRCINT is shown in Figure 6-63 and described in Table 6-44.

Return to Summary Table.

Register domain: RESET

Figure 6-63. SPWRSRCINT Register

7	6	5	4	3	2	1	0
RESERVED1_ SPWRSRCINT	SLOWBATT2	SLOWBATT1	SACOK		RESERVED_SF	WRSRCINT[3:0]	
R-0h	R-0h	R-0h	R-0h		R-	-0h	

Table 6-44. SPWRSRCINT Register Field Descriptions

Bit	Field	Туре	Reset	Description
7	RESERVED1_SPWRSRCINT	R	0h	
6	SLOWBATT2	R	Oh	LOWBATT2 detection status 0h = BATT2 above threshold 1h = BATT2 below threshold
5	SLOWBATT1	R	Oh	LOWBATT1 detection status 0h = BATT1 above threshold 1h = BATT1 below threshold
4	SACOK	R	Oh	AC adapter (ACOK) detection status 0h = Adapter removed 1h = Adapter inserted
3-0	RESERVED_SPWRSRCINT[3:0]	R	0h	

6.6.43 CLKCTRL1 Register (address = 0xD0) [reset = 0x00]

CLKCTRL1 is shown in Figure 6-64 and described in Table 6-45.

Return to Summary Table.

Register domain: RTC

Figure 6-64. CLKCTRL1 Register

7	6	5	4	3	2	1	0
		RESE	RVED_CLKCTRL	.1[6:0]			ECWAKEEN
			R/W-0h				R/W-0h

Table 6-45. CLKCTRL1 Register Field Descriptions

Bit	Field	Туре	Reset	Description
7-1	RESERVED_CLKCTRL1[6:0]	R/W	0h	
0	ECWAKEEN	R/W	0h	1-Hz clock 0h = Clock OFF
				1h = Clock ON

6.6.44 COMPA_REF Register (address = 0xDD) [reset = 0xB6]

COMPA_REF is shown in Figure 6-65 and described in Table 6-46.

Return to Summary Table.

Register domain: RESET

Figure 6-65. COMPA_REF Register

7	6	5	4	3	2	1	0	
COMPA_Mode		COMPA_DVS[3:0]				COMPA_VSEL[2:0]		
R/W-1h		 R/W-6h				R/W-6h		

Bit	Field	Туре	Reset	Description
7	COMPA_Mode	R/W	1h	Comparator mode:
				0h = PGOOD mode
				1h = Comparator mode
6-3	COMPA_DVS[3:0]	R/W	6h	Comparator window voltage shifting: % deviation from VSEL if VSEL ≠ 1 V or second voltage option if VSEL = 1 V
				0h = + 3% or 1.05 V
				1h = + 2% or 1 V
				2h = + 1% or 0.975 V
				3h = + 0% or 0.95 V
				4h = - 1% or 0.9 V
				5h = - 2% or 0.875 V
				6h = - 3% or 0.85 V
				7h = - 4% or 0.8 V
				8h = 0.75 V
				9h = 0.7 V
2-0	COMPA_VSEL[2:0]	R/W	6h	Comparator window voltage select:
				0h = 1 V
				1h = 1.2 V
				2h = 1.5 V
				3h = 1.8 V
				4h = 1.1 V
				5h = 1.35 V
				6h = 3.3 V
				7h = 2.5 V

Table 6-46. COMPA_REF Register Field Descriptions

6.6.45 COMPB_REF Register (address = 0xDE) [reset = 0x1B]

COMPB_REF is shown in Figure 6-66 and described in Table 6-47.

Return to Summary Table.

Register domain: RESET

Figure 6-66. COMPB_REF Register

7	6	5	4	3	2	1	0	
COMPB_Mode		COMPB_DVS[3:0]				COMPB_VSEL[2:0]		
R/W-0h		R/W-3h				R/W-3h		

Bit	Field	Туре	Reset	Description
7	COMPB_Mode	R/W	0h	Comparator mode:
				0h = PGOOD mode
				1h = Comparator mode
6-3	COMPB_DVS[3:0]	R/W	3h	Comparator window voltage shifting: % deviation from VSEL if VSEL ? 1 V or second voltage option if VSEL = 1 V
				0h = + 3% or 1.05 V
				1h = + 2% or 1 V
				2h = + 1% or 0.975 V
				3h = + 0% or 0.95 V
				4h = - 1% or 0.9 V
				5h = - 2% or 0.875 V
				6h = - 3% or 0.85 V
				7h = - 4% or 0.8 V
				8h = 0.75 V
				9h = 0.7 V
2-0	COMPB_VSEL[2:0]	R/W	3h	Comparator window voltage select:
				Oh = 1 V
				1h = 1.2 V
				2h = 1.5 V
				3h = 1.8 V
				4h = 1.1 V
				5h = 1.35 V
				6h = 3.3 V
				7h = 2.5 V

Table 6-47. COMPB_REF Register Field Descriptions

6.6.46 PWFAULT_MASK1 Register (address = 0xE5) [reset = 0x01]

PWFAULT_MASK1 is shown in Figure 6-67 and described in Table 6-48.

Return to Summary Table.

Register domain: RESET

Figure 6-67. PWFAULT_MASK1 Register

7	6	5	4	3	2	1	0
VCCIO_FLTms K	V5A_FLTmsK	V33APCHFLT msk	V33ADSWFLT msk	V18A_FLTmsK	V18U25U_FLT msK	VDDQ_FLTms K	V13_FLTmsK
R/W-0h	R/W-0h	R/W-0h	R/W-0h	R/W-0h	R/W-0h	R/W-0h	R/W-1h

Table 6-48. PWFAULT_MASK1 Register Field Descriptions

Bit	Field	Туре	Reset	Description
7	VCCIO_FLTmsK	R/W	0h	VCCIO power fault masked
				0h = Not masked
				1h = Masked
6	V5A_FLTmsK	R/W	0h	V5A power fault masked
				0h = Not masked
				1h = Masked
5	V33APCHFLTmsk	R/W	0h	V33APCH power fault masked
				0h = Not masked
				1h = Masked
4	V33ADSWFLTmsk	R/W	0h	V33ADSW power fault masked
				0h = Not masked
				1h = Masked
3	V18A_FLTmsK	R/W	0h	V18A power fault masked
				0h = Not masked
				1h = Masked
2	V18U25U_FLTmsK	R/W	0h	V18U25U power fault masked
				0h = Not masked
				1h = Masked
1	VDDQ_FLTmsK	R/W	0h	VDDQ power fault masked
				0h = Not masked
				1h = Masked
0	V13_FLTmsK	R/W	1h	V13 power fault masked
				0h = Not masked
				1h = Masked

6.6.47 PWFAULT_MASK2 Register (address = 0xE6) [reset = 0x00]

PWFAULT_MASK2 is shown in Figure 6-68 and described in Table 6-49.

Return to Summary Table.

Register domain: RESET

Figure 6-68. PWFAULT_MASK2 Register

7	6	5	4	3	2	1	0
	RESERVED_PWFAULT_MASK2[5:0]						VPRIMCORE_ FLTmsK
			R/W-0h	R/W-0h			

Table 6-49. PWFAULT_MASK2 Register Field Descriptions

Bit	Field	Туре	Reset	Description
7-2	RESERVED_PWFAULT_MASK2[5: 0]	R-1	0h	Read always returns 1
1	V105A_FLTmsK	R/W	Oh	V105A power fault masked 0h = Not masked 1h = Masked
0	VPRIMCORE_FLTmsK	R/W	0h	VPRIMCORE power fault masked 0h = Not masked 1h = Masked

6.6.48 PGOOD_STAT1 Register (address = 0xE7) [reset = 0x00]

PGOOD_STAT1 is shown in Table 6-50 and described in Table 6-51.

Return to Summary Table.

Register domain: RESET

Table 6-50. PGOOD STAT1 Register

				_			
7	6	5	4	3	2	1	0
V13_PGOOD	VDDQ_PGOO	V18U25U_PGO	V18A_PGOOD	V33ADSW_PG	V33APCH_PG	VPRIMCORE_	VCCIO_PGOO
	D	OD		OOD	OOD	PGOOD	D
R-0h	R-0h	R-0h	R-0h	R-0h	R-0h	R-0h	R-0h

Table 6-51. PGOOD_STAT1 Register Field Descriptions

Bit	Field	Туре	Reset	Description
7	V13_PGOOD	R	0h	V13 power-good status
				0h = Fail
				1h = Pass
6	VDDQ_PGOOD	R	0h	VDDQ power-good status
				Oh = Fail
				1h = Pass
5	V18U25U_PGOOD	R	0h	
				V18U25U power-good status
				0h = Fail
				1h = Pass
4	V18A_PGOOD	R	0h	V18A power-good status
				0h = Fail
				1h = Pass
3	V33ADSW_PGOOD	R	0h	V33ADSW power-good status
				0h = Fail
				1h = Pass
2	V33APCH_PGOOD	R	0h	V33APCH power-good status
				Oh = Fail
				1h = Pass
1	VPRIMCORE_PGOOD	R	0h	
			0.1	VPRIMCORE power-good status
				0h = Fail
				1h = Pass
0	VCCIO_PGOOD	R	0h	VCCIO power-good status
				0h = Fail
				1h = Pass

6.6.49 PGOOD_STAT2 Register (address = 0xE8) [reset = 0x00]

PGOOD_STAT2 is shown in Figure 6-69 and described in Table 6-52.

Return to Summary Table.

Register domain: RESET

Figure 6-69. PGOOD_STAT2 Register

			-		-		
7	6	5	4	3	2	1	0
RESEF	RVED_PGOOD_ST	AT2[2:0]	V5A_PG	V105A_PGOO D	V105A_SPGD	V18A_SPGD	V33ADSW_SP GD
	R-0h		R-0h	R-0h	R-0h	R-0h	R-0h

Table 6-52. PGOOD_STAT2 Register Field Descriptions

Bit	Field	Туре	Reset	Description
				besonption
7-5	RESERVED_PGOOD_STAT2[2:0]	R-1	0h	Read always returns 1
4	V5A_PG	R	0h	V5A power-good status
				0h = Fail
				1h = Pass
3	V105A_PGOOD	R	0h	V105A power-good status
				0h = Fail
				1h = Pass
2	V105A_SPGD	R	0h	V105AS power-good status
				0h = Fail
				1h = Pass
1	V18A_SPGD	R	0h	V18AS power-good status
				0h = Fail
				1h = Pass
0	V33ADSW_SPGD	R	0h	V33ADSWS power-good status
				0h = Fail
				1h = Pass

6.6.50 MISC_BITS Register (address = 0xE9) [reset = 0x02]

MISC_BITS is shown in Figure 6-70 and described in Table 6-53.

Return to Summary Table.

Register domain: RESET

Figure 6-70. MISC_BITS Register

7	6	5	4	3	2	1	0
V13_PIN_OVR	MV13EN	V33APCH_PIN _OVR	MV33APCHEN	msLP_S3ZPG	msLP_SUSZP G	BC_ACOK_EN	V13DISCHG
R/W-0h	R/W-0h	R/W-0h	R/W-0h	R/W-0h	R/W-0h	R/W-1h	R/W-0h

Table 6-53. MISC_BITS Register Field Descriptions

Bit	Field	Туре	Reset	Description
7	V13_PIN_OVR	R/W	0h	V13 ENABLE pin override
				0h = V13 is OFF if MV13EN is 1
				1h = V13 is ON if MV13EN is 1
6	MV13EN	R/W	0h	
				V13 enable pin mask
				0h = DDR_VT_CTRL pin controls V13
5		B/W	0h	1h = V13_EN_PIN bit controls V13
5	V33APCH_PIN_OVR	H/VV	Un	V33APCH ENABLE pin override
				0h = V33ADSW pin controls V33ADSW
				1h = V33ADSW is ON if VREN PIN MASK = 0
4	MV33APCHEN	R/W	0h	V33APCH enable pin mask
				0h = VR enable pin controls VR enable
				1h = VR enable pin masked VxCTLV controls VR enable
3	msLP_S3ZPG	R/W	0h	SLP_S3Z is part of the power good tree
				0h = SLP_S3Z is part of power good tree
				1h = SLP_S3Z is masked and set to 1 (not part of the power good tree)
2	msLP_SUSZPG	R/W	0h	SLP_SUSZ is part of the power good tree
				0h = SLP_SUSZ is part of power good tree
				1h = SLP_SUSZ is masked and set to 1 (not part of the power good tree)
1	BC_ACOK_EN	R/W	1h	Enables BC_ACOK output out of LVA pin. The input is ACOK pin, instead of ENLVA pin.
				0h = LVA pin is not BC_ACOK, and ENLVA is the input for LVA output, behaving as a general purpose level shifter.
				1h = LVA pin is BC_ACOK, and ACOK is the input, and ENLVA is not functional. BC_ACOK is a level shifted version of ACOK.
0	V13DISCHG	R/W	0h	V0.6DX discharge resistance (V13)
				0h = no discharge
				$1h = 100 \Omega$

6.6.51 STDBY_CTRL Register (address = 0xEA) [reset = 0xFE]

STDBY_CTRL is shown in Figure 6-71 and described in Table 6-54.

Return to Summary Table.

Register domain: RTC

Figure 6-71. STDBY_CTRL Register

7	6	5	4	3	2	1	0
	RESERVED_STDBY_CTRL[4:0]					QLSLPS0_ACT IVE	QLSLPS0_ACT IVE
		R-Fh	R/W-1h	R/W-1h	R/W-0h		

Table 6-54. STDBY_CTRL Register Field Descriptions

			_	
Bit	Field	Туре	Reset	Description
7-3	RESERVED_STDBY_CTRL[4:0]	R	1Fh	Read always returns 1
2	EN_VCOMP_10U	R/W	1h	VCOMP current source control bit:
				0h = Disable
				1h = Enable
1	VCOMPEN	R/W	1h	VCOMP enable control bit:
				0h = Disable
				1h = Enable
0	QLSLPS0_ACTIVE	R/W	0h	SLP_S0 and DDR_VTT_CTRL detect logic control
				0h = Normal Operation DELAY_ALL_SYS_PG is used in QSTANDBY (SLP_S0)
				1h = DELAY_ALL_SYS_PG is ignored for QSTANDBY (SLP_S0)

6.6.52 TEMPCRIT Register (address = 0xEB) [reset = 0x00]

TEMPCRIT is shown in Figure 6-72 and described in Table 6-55.

Return to Summary Table.

Register domain: RTC

Figure 6-72. TEMPCRIT Register

			-		-		
7	6	5	4	3	2	1	0
RESERVED_TE	MPCRIT[1:0]	LDO1_CRIT	VR5_CRIT	VR4_CRIT	VR3_CRIT	VR2_CRIT	VR1_CRIT
R-0	h	R/W1C-0h	R/W1C-0h	R/W1C-0h	R/W1C-0h	R/W1C-0h	R/W1C-0h

Bit	Field	Туре	Reset	Description
7-6	RESERVED_TEMPCRIT[1:0]	R	0h	Read always returns 0
5	LDO1_CRIT	R/W1C	0h	LDO1 critical temperature
				0h = Not asserted
				1h = Asserted, regulator at critical temperature, write 1 to clear
4	VR5_CRIT	R/W1C	0h	VR5 critical temperature
				0h = Not asserted
				1h = Asserted, regulator at critical temperature, write 1 to clear
3	VR4_CRIT	R/W1C	0h	VR4 critical temperature
				0h = Not asserted
				1h = Asserted, regulator at critical temperature, write 1 to clear
2	VR3_CRIT	R/W1C	0h	VR3 critical temperature
				0h = Not asserted
				1h = Asserted, regulator at critical temperature, write 1 to clear
1	VR2_CRIT	R/W1C	0h	VR2 critical temperature
				0h = Not asserted
				1h = Asserted, regulator at critical temperature, write 1 to clear
0	VR1_CRIT	RR/W1C	0h	VR1 critical temperature
				0h = Not asserted
				1h = Asserted, regulator at critical temperature, write 1 to clear

Table 6-55. TEMPCRIT Register Field Descriptions

6.6.53 TEMPHOT Register (address = 0xEC) [reset = 0x00]

TEMPHOT is shown in Figure 6-73 and described in Table 6-56.

Return to Summary Table.

Register domain: RTC

Figure 6-73. TEMPHOT Register

		•		•		
7 6	5	4	3	2	1	0
RESERVED_TEMPHOT[1:0]	LDO1_HOT	VR5_HOT	VR4_HOT	VR3_HOT	VR2_HOT	VR1_HOT
R-0h	R/W1C-0h	R/W1C-0h	R/W1C-0h	R/W1C-0h	R/W1C-0h	R/W1C-0h

Table 6-56. TEMPHOT Register Field Descriptions

Bit	Field	Туре	Reset	Description
7-6	RESERVED_TEMPHOT[1:0]	R	0h	Read always returns 0
5	LDO1_HOT	R/W1C	0h	LDO1 hot temperature
				0h = Not asserted
				1h = Asserted, write 1 to clear
4	VR5_HOT	R/W1C	0h	VR5 hot temperature
				0h = Not asserted
				1h = Asserted, write 1 to clear
3	VR4_HOT	R/W1C	0h	VR4 hot temperature
				0h = Not asserted
				1h = Asserted, write 1 to clear
2	VR3_HOT	R/W1C	0h	VR3 hot temperature
				0h = Not asserted
				1h = Asserted, write 1 to clear
1	VR2_HOT	R/W1C	0h	VR2 hot temperature
				0h = Not asserted
				1h = Asserted, write 1 to clear
0	VR1_HOT	R/W1C	0h	VR1 hot temperature
				0h = Not asserted
				1h = Asserted, write 1 to clear

6.6.54 VREN_PIN_OVR Register (address = 0xEE) [reset = 0x0]

VREN_PIN_OVR is shown in Figure 6-74 and described in Table 6-57.

Return to Summary Table.

Register domain: RESET

Figure 6-74. VREN_PIN_OVR Register

7	6	5	4	3	2	1	0
VPRIMCORE_ PIN_OVR	V105A_PIN_O VR	VDDQ_PIN_OV R	V18U25U_PIN_ OVR	V18A_PIN_OV R	V33APCH_PIN _OVR	V5A_PIN_OVR	VCCIO_PIN_O VR
R/W-0h	R/W-0h	R/W-0h	R/W-0h	R/W-0h	R/W-0h	R/W-0h	R/W-0h

Table 6-57. VREN_PIN_OVR Register Field Descriptions

Bit	Field	Туре	Reset	Description
7	VPRIMCORE_PIN_OVR	R/W	0h	VPRIMCORE ENABLE pin override
				0h = VPRIMCORE pin controls VPRIMCORE
				1h = VPRIMCORE is ON if VREN PIN MASK = 0
6	6 V105A_PIN_OVR		0h	V105A ENABLE pin override
				0h = V105A pin controls V105A
				1h = V105A is ON if VREN PIN MASK = 0
5	VDDQ_PIN_OVR	R/W	0h	VDDQ ENABLE pin override
				0h = VDDQ pin controls VDDQ
				1h = VDDQ is ON if VREN PIN MASK = 0
4	V18U25U_PIN_OVR	R/W	0h	V18U25U ENABLE pin override
				0h = V18U25U pin controls V18U25U
				1h = V18U25U is ON if VREN PIN MASK = 0
3	V18A_PIN_OVR	R/W	0h	V18A ENABLE pin override
				0h = V18A Pin controls V18A
				1h = V18A is ON if VREN PIN MASK = 0
2	V33APCH_PIN_OVR	R/W	0h	V33APCH ENABLE pin override
				0h = V33APCH pin controls V33APCH
				1h = V33APCH is ON if VREN PIN MASK = 0
1	V5A_PIN_OVR	R/W	0h	V5A ENABLE pin override
				0h = V5A pin controls V5A
				1h = V5A is ON if VREN PIN MASK = 0
0	VCCIO_PIN_OVR	R/W	0h	VCCIO ENABLE pin override
				0h = VCCIO pin controls VCCIO
				1h = VCCIO is ON if VREN PIN MASK = 0

7 Applications, Implementation, and Layout

NOTE

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

7.1 Application Information

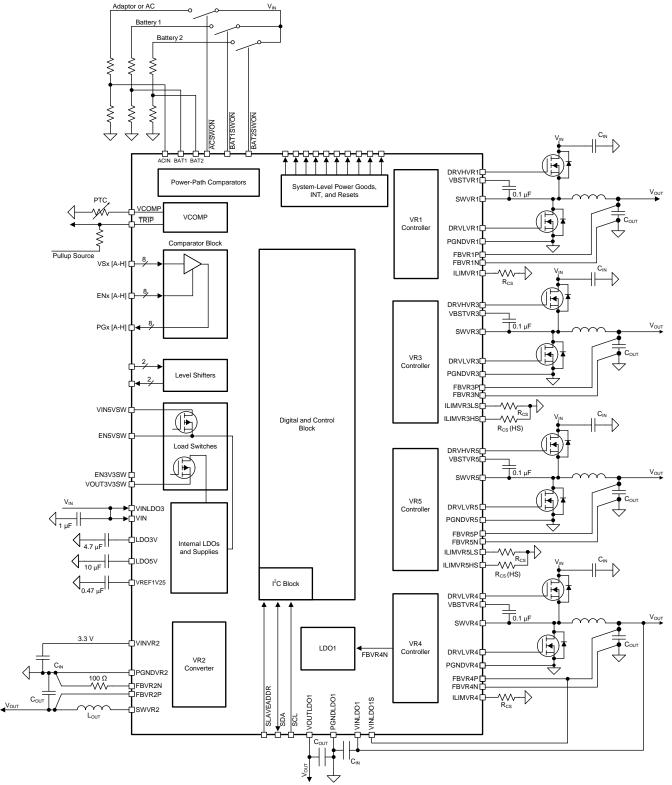
The TPS650932 can be used in several different applications from computing to industrial interfacing and more. This section describes the general application information and provides a detailed description of powering the Intel Cannon Lake system with the TPS650932 device.

7.2 Typical Application

The TPS650932 can be used in any system that requires multiple voltage rails. A DC supply voltage from 5.4 V to 21 V is required. If the supply voltage is less than this range, then a small boost can be added to the system to supply the VIN and VINLDO3.

Along with the five DC-DCs and one LDO, the TPS650932 device has eight general-purpose comparators, two level shifters, one board temperature-monitoring system, and three power-path comparators. The temperature-monitoring system and power-path comparators can be used as simple comparators if desired, increasing the total number of comparators available for use on the TPS650932 to 12.





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Figure 7-1. Simplified General Block Diagram

7.2.1 Design Requirements

The TPS650932 device requires decoupling capacitors on the supply pins. Follow the specifications in the *Section 5.14* table for the recommended capacitance on these supplies.

The controllers, converter, LDO, and some other features can be adjusted to meet the application requirements. The *Section 7.2.2* section describes how to design and adjust the external components to achieve the desired performance.

7.2.2 Detailed Design Procedure

7.2.2.1 Controller Design Procedure

Designing the controller is performed in several steps: designing the output filter, selecting the FETs, bootstrap capacitor, and input capacitors, and setting the current limits.

The VR1 and VR4 controllers require the VREG supply and capacitors. The VREG pin should be connected to the 5-V LDO. A $1-\mu$ F, X5R, 20%, 10-V or similar capacitor should be used for decoupling.

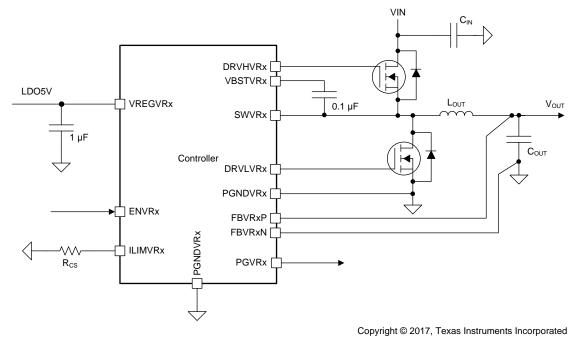


Figure 7-2. Controller Diagram

7.2.2.1.1 Selecting the Inductor

An inductor must be placed between the external FETs and the output capacitors. The inductor and output capacitors together make the double-pole which contributes to stability. Additionally, the inductor is directly responsible for the output ripple, efficiency, and transient performance. As the inductance increases, the ripple current decreases which, typically, increases efficiency. However, as the inductance increases, the transient performance decreases. The selected inductor must be rated for an appropriate saturation current, core losses, and DC resistance (DCR).

Use Equation 1 to calculate the recommended inductance for the controller.

$$L = \frac{V_{OUT} \times (V_{IN} - V_{OUT})}{V_{IN} \times f_{SW} \times I_{OUT} \max \times K_{IND}}$$

where

• K_{IND} is the ratio of I_{Lripple} to I_{OUTmax}.

TI recommends setting K_{IND} from 0.2 to 0.4.

Use Equation 2 to calculate the peak current for the inductor in steady state operation, I_{Lmax} , with the selected inductance value. The rated saturation current of the inductor must be higher than the I_{Lmax} current.

$$I_{Lmax} = I_{OUTmax} + \left(\frac{\left[V_{IN} - V_{OUT}\right] \times V_{OUT}}{2 \times V_{IN} \times f_{SW} \times L}\right)$$
(2)

7.2.2.1.2 Selecting the FETs

This controller is designed to drive NMOS FETs. Typically, the lowest R_{DSon} value for the high-side and low-side FETs is best, however; the FETs, inductor, and output capacitors must be sized appropriately because as the R_{DSon} for the low-side FET decreases, the minimum current limit increases. TI recommends using the CSD87381P or CSD87330Q3D for the controllers.

7.2.2.1.3 Bootstrap Capacitor

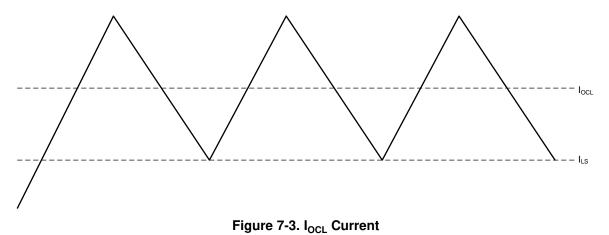
To ensure that the internal high-side gate drivers are supplied with a stable low-noise supply voltage, a capacitor must be connected between the VBSTVRx pins and the respective SWVRx pins. TI recommends using ceramic capacitors with a value of 0.1 μ F as the converters and the controllers. A 0.1- μ F, size 0402, 10-V capacitor was used for the controllers for testing.

TI recommends reserving a small resistor in series with the bootstrap capacitor in case the turnon or turnoff of the FETs must be slowed to reduce voltage ringing on the switch node. This practice is common for controller design.

7.2.2.1.4 Setting the Current Limits

The controller has a *valley current-limit topology*, also known as a *low-side current limit*. This type of current limit works by limiting the current only when the low-side FET is on. If the current sourced by the low-side FET is greater than the set low-side current limit, I_{LS} , then the controller holds the low-side FET on and the high-side FET off until the current through the low-side FET decreases below the set I_{LS} value. The low-side FET is allowed to turn off and the high-side FET to turn on only when the current through the low-side FET is less than the I_{LS} values.

A fast current increase is limited by the maximum on time for the high-side FET. This limiting forces the low-side FET to turn on every period. When the low-side FET turns on, the low-side current limit can control the FETs until the current decreases below the I_{LS} value. The maximum on time for the high-side FET limits the current increase to the maximum on time multiplied by the di/dt of the inductor until the low-side FET is switched on.



The I_{OCL} current is the average of the peak and valley currents as shown in Figure 7-3.

The low-side current limit for the controllers is set by a resistor, R_{CS} , at the ILIMVRx pin. A current, I_{TRIP} , is sourced across the R_{CS} resistor to set the voltage for the current-limit comparator. Use Equation 3 to determine the value of the R_{CS} resistor.

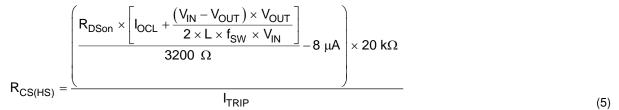
$$R_{CS(LS)} = \frac{8 \times R_{DSon} \times 1.3 \times \left(I_{OCL} - \frac{\left[V_{IN} - V_{OUT}\right] \times V_{OUT}}{2 \times L \times f_{SW} \times V_{IN}}\right)}{I_{TRIP}}$$
(3)

TI recommends setting I_{OCL} to 130% of I_{OUTmax} and using a resistor with ±1% or less tolerance for best results. Because the current limit occurs when the inductor current is near its maximum, TI recommends using the saturation derating of the inductor when calculating the value of R_{CS} .

A minimum and maximum value of I_{OCL} can be achieved for the given parameters used in Equation 3. To ensure that the R_{CS} resistor has been sized correctly, Equation 4 must be true across the application temperature range.

$$V_{\rm CSmin} < I_{\rm TRIP} \times R_{\rm CS} < V_{\rm CSmax} \tag{4}$$

If the controller has a high-side current limit then, use Equation 5 to calculate the high-side R_{CS} resistor ($R_{CS(HS)}$). The high-side current limit must be set higher than the low-side current limit. Again, because the current limit occurs when the inductor current is near its maximum, TI recommends using the saturation derating of the inductor when calculating the value of R_{CS} .



7.2.2.1.5 Selecting the Input Capacitors

Because of the nature of the switching converter and controller with a pulsating input current, a low-ESR input capacitor is required for best input voltage filtering and to minimize the interference with other circuits caused by high input-voltage spikes. For the controller, TI recommends 12 μ F of input capacitance for most applications. To achieve the low-ESR requirement, use a ceramic capacitor. However, the voltage rating and DC-bias characteristic of ceramic capacitors must be considered. The value of the input capacitor to achieve the recommended input capacitance. TI recommends placing a ceramic capacitor as close as possible to the respective VINx and PGNDx pins of the FETs.

The preferred capacitors for the controllers are two muRata GRM21BR61E106MA73: 10 μ F, 0805, 25 V, ±20% or similar.



7.2.2.2 Converter Design Procedure

Designing the converter is performed in two steps: designing the output filter and selecting the input capacitors. The converter must be supplied by a 3.3-V source which can be provided by the TPS650932 controllers.

The converter requires the VREG supply and capacitors. The VREG supply should be connected to the 5-V LDO and a $1-\mu$ F, X5R, 20%, 10-V or similar capacitor should be used for decoupling.

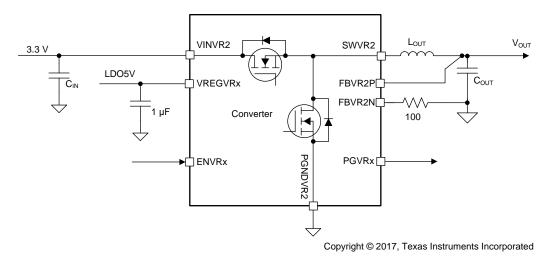


Figure 7-4. Converter Diagram

7.2.2.2.1 Selecting the Inductor

An inductor is required to be placed between the SWVRx and the output capacitors. The inductor and output capacitors together make the double-pole which contributes towards stability. In addition, the inductor is directly responsible for the output ripple, efficiency, and transient performance. With an increase in inductance used the ripple current decreases which, typically increases efficiency. However, with an increase in inductance used, the transient performance decreases. Finally, the inductor selected has to be rated for appropriate saturation current, core losses and DC resistance (DCR).

Use Equation 6 to calculate the recommended inductance for the controller.

$$L = \frac{V_{OUT} \times (V_{IN} - V_{OUT})}{V_{IN} \times f_{SW} \times I_{OUTmax} \times K_{IND}}$$

where

• K_{IND} is the ratio of I_{Lripple} to I_{OUTmax}.

TI recommends setting K_{IND} from 0.2 to 0.4.

Use Equation 7 to calculate the peak current for the inductor in steady state operation, I_{Lmax} , with the selected inductance value. The rated saturation current of the inductor must be higher than the I_{Lmax} current.

$$I_{Lmax} = I_{OUTmax} + \left(\frac{\left[V_{IN} - V_{OUT}\right] \times V_{OUT}}{2 \times V_{IN} \times f_{SW} \times L}\right)$$
(7)

Table 7-1 lists a selection of recommended inductors for the converter.

Table 7-1. F	Recommended	Inductors
--------------	-------------	-----------

MANUFACTURER	PART NUMBER	VALUE	SIZE	HEIGHT
Cyntec	PIFE32251B-R68MS	0.68 μH	3.2 mm × 2.5 mm	1.2 mm
Cyntec	PIFE32251B-R47MS	0.47 μH	3.2 mm × 2.5 mm	1.2 mm

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(6)

7.2.2.2.2 Selecting the Output Capacitors

TI recommendes ceramic capacitors with low-ESR values which provide the lowest output-voltage ripple. The output capacitor requires either an X7R or X5R dielectric. Y5V and Z5U dielectric capacitors, aside from their wide variation in capacitance over temperature, become resistive at high frequencies.

At light-load currents, the converter operates in power-save mode and the output-voltage ripple is dependent on the output-capacitor value and the PFM peak-inductor current. Higher output-capacitor values minimize the voltage ripple in PFM Mode. To achieve the specified regulation performance and low output-voltage ripple, the DC-bias characteristic of ceramic capacitors must be considered. The effective capacitance of ceramic capacitors drops with increasing DC-bias voltage.

TI recommends using small ceramic capacitors placed as close as possible to the inductor and the respective PGND pins of the device for the output capacitors of the DC-DC converters. If, for any reason, the application requires the use of large capacitors that can not be placed close to the device, use a smaller ceramic capacitor in parallel with the large capacitor. Place the small capacitor as close as possible to the inductor and the respective PGND pins of the device.

T recommended capacitor to use with the DC-DC converters is the muRata GRM188R60J226MEAO: 22 μ F, 0603, 6.3 V, ±20% or similar. This capacitor was selected to achieve the highest derated capacitance in a small 0603 package. If the selected output voltage is greater than 3.3 V then TI recommends using the muRata GRM21BR61A226ME44: 22 μ F, 0805, 10 V, ± 20%, or similar. This capacitor is recommended to maintain the actual capacitance as DC bias increases.

7.2.2.2.3 Selecting the Input Capacitors

Because of the nature of the switching converter and controller with a pulsating input current, a low-ESR input capacitor is required for best input voltage filtering and to minimize the interference with other circuits caused by high input-voltage spikes. For the controller, TI recommends 12 μ F of input capacitance for most applications. To achieve the low-ESR requirement, use a ceramic capacitor. However, the voltage rating and DC-bias characteristic of ceramic capacitors must be considered. The value of the input capacitor to achieve the recommended input capacitance. TI recommends placing a ceramic capacitor as close as possible to the respective VINx and PGNDx pins of the device.

The preferred capacitors for the controllers are two muRata GRM21BR61E106MA73: 10 μ F, 0805, 25 V, ±20% or similar.

7.2.2.3 LDO Design Procedure

The LDO must support the fast load transients from the DDR memory for termination. Therefore, maintaining a high amount of capacitance with low ESR on the LDO outputs and inputs is important, for which ceramic capacitors are ideal.

The preferred output capacitor for the LDO is muRata GRM188R60J476M: 47 μ F, 0603, 6.3 V, ±20% or similar.

The preferred input capacitor for the LDO is muRata GRM155R60J106ME44: 10 μ F, 0402, 6.3 V, ±20% or similar.

7.2.2.4 Board Temperature Monitoring Design Procedure

Board temperature monitoring requires only one thermistor if only one sense point is desired. The temperature monitoring can be scaled by adding as many thermistors as sense points desired. Connect a PTC thermistor that has an exponential coefficient curve from the VCOMP pin to GND and a pullup resistor to desired voltage source on the TRIPZ pin. Place the thermistor where desired. If multiple sense points are desired, string the thermistors together in a series connection while placing the thermistors where desired as shown in Figure 7-5.

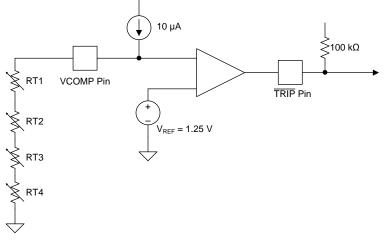


Figure 7-5. Board Temperature Monitoring Circuit Example

The thermistors should have low-room and mid-temperature resistance from 1 k Ω to 10 k Ω . The hot-point resistance should be approximately 10 times the mid-temperature resistance from 100 k Ω to 200 k Ω . An internal 10-µA current source provides a voltage across the thermistors. When this voltage exceeds the comparator threshold of 1.25 V, the TRIPZ pin switches to low which indicates a hot board temperature. Therefore, the resistance required for hot board temperature is 125 k Ω . Select thermistors that align this resistance with the desired setpoint of the hot temperature.

The recommended thermistors for this feature is the muRata PRF15BG102RB6RC.

7.2.2.5 Power-Path Design Procedure

The TPS650932 device has power-path comparators and outputs to control the power-path switches. To set the threshold to the desired value, connect a voltage divider to the adaptor and batteries. The outputs of the comparators require a pullup resistor because the comparator outputs are open-drain outputs. In order for the power-path comparators to work without supplying VIN, connect the VINPP pin to the monitored power rails by using a diode to select the highest voltage among the sources.

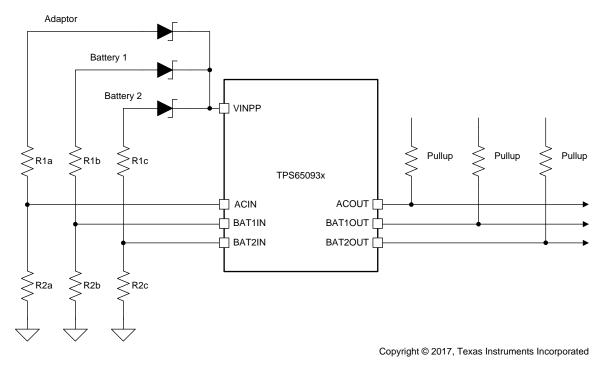


Figure 7-6. Power-Path Comparators and VINPP Supply

For example, measuring a battery and an adaptor is helpful to decide when to switch from the battery to the adaptor. The desired threshold voltages 9 V and 6 V respectively. Use Equation 8 to calculate the resistors required to set each threshold. The R1a and R2a resistors are required to set the 9-V. The R1b and R1a resistors are required to set the 6-V threshold.

$$R1 = R2 \times \left(\frac{V_{IN}}{V_{THRESHOLD}} - 1\right)$$
(8)

1



7.2.3 Application Curves

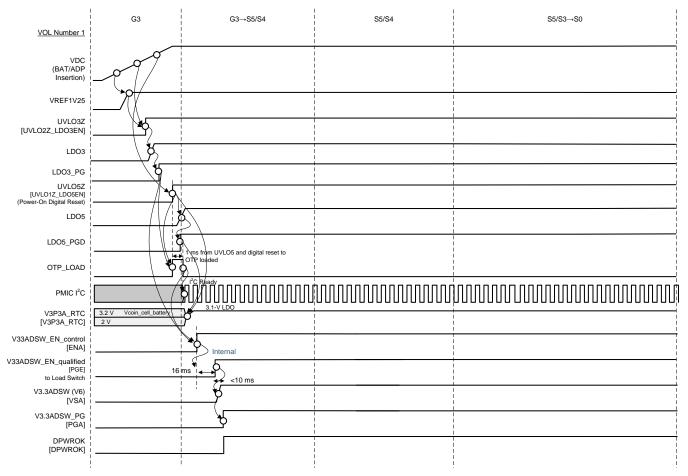
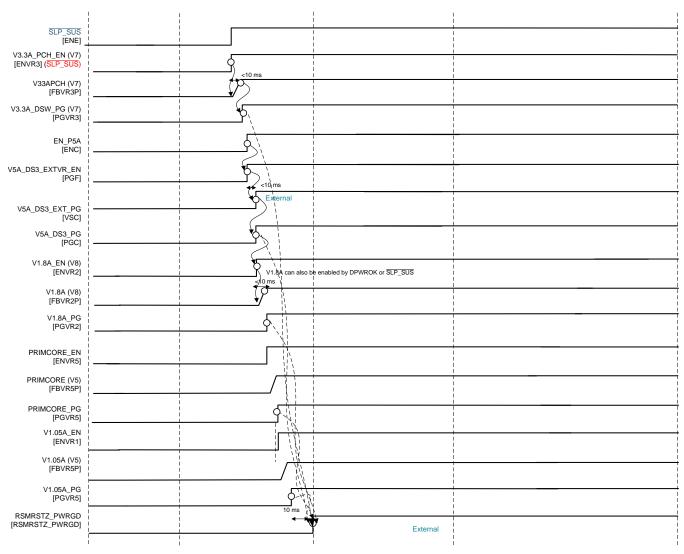


Figure 7-7. Timing Diagram

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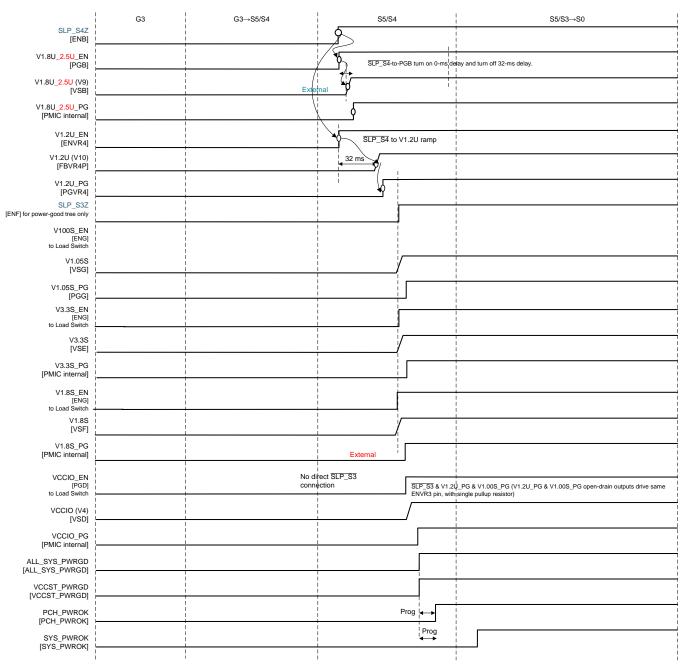
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TPS650932

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DPWROK (PMIC internal logic to open-drain DPWROK pin)		}	See ⁽¹⁾
		Λ	DPWROK signal to the PMIC VR enable signals
V33PCHEN (ENVR3)	Internally Qualified		1 Q
V5ADS3_EN (PGF) PMIC to External EN_V5ADS3	3_VR		2
VCCIO_EN (V6) (PGD)			2
V33DSW_EN_control (ENA) PMIC to Load Switch EN			}
V1.8A_EN (V8) (ENVR2)	Internally Qualified		φ
V1.8U_2.5U_EN (PGB) PMIC to Load Switch EN			
V1.1U_EN (ENVR4)	Internally Qualified		P
V105A_EN (ENVR1)	Internally Qualified	/}	
VCCPRIMCORE_EN (ENVR5)	Internally Qualified		

(1) DPWROK is the PMIC internal-logic signal controlling the PMIC open-drain DPWROK pin. If the DPWROK pin is connected to ground, then this will not be visible to the user; instead, the user would see the external net P_DPWROK from the external DPWROK pin always low.

Figure 7-10. Emergency Reset Sequence Timing Diagram



7.2.4 Layout

7.2.4.1 Layout Guidelines

For all switching power supplies, layout is an important step in the design, especially at high peak currents and high switching frequencies. If the layout is not performed carefully, the regulator could show stability problems as well as electromagnetic interference (EMI) problems. Therefore, use wide and short traces for the main current path and for the power-ground tracks. The input capacitor, output capacitor, and the inductor should be placed as close as possible to the device. Use a common ground node for the power ground and a different node for the control ground to minimize the effects of ground noise. Connect these ground nodes at any place close to one of the ground pins of the device.

The TPS650932 device is available in a 7-mm by 7-mm nFBGA package (ZAJ) with a 0.5-mm ball pitch.

7.2.4.1.1 Fanout for ZAJ using Type 4 Routing

This small, 7-mm \times 7-mm package uses the Type 4 routing technique to decrease system-board area as much as possible. This Type 4 routing has vias in pad, blind and buried vias, and a minimum trace width, or spacing, of 4 mm.

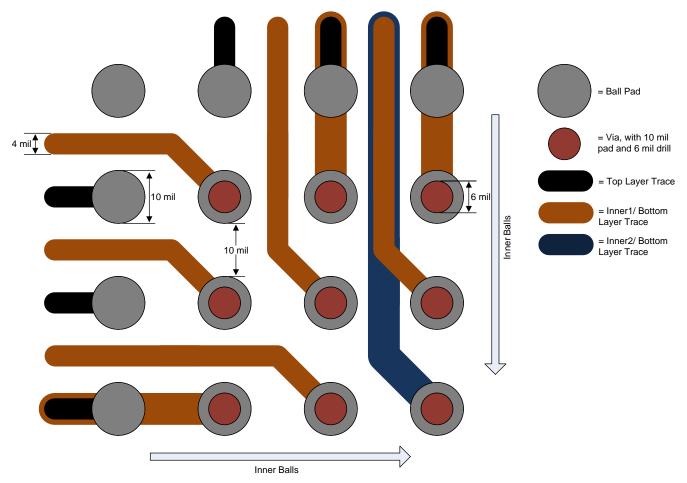


Figure 7-11. Fanout for ZAJ Package Using Type 4 Routing



7.2.4.1.2 Layout Checklist

The general layout checklist is:

- Locate all inductors, input and output capacitors, and FETs for the converters and controller on the same board layer as the device.
- Place feedback connection points near the output capacitors and minimize the control feedback loop as much as possible to achieve the best regulation performance.
- Place bootstrap capacitors from the SWVRx to VBSTVRx pins close to the device.
- Route the DRVLVRx signals on the same layer as the device and the FETs. Minimize the length and parasitic inductance of the trace as much as possible.
- Each converter and controller should have a separate ground, and each ground should connect separately to the common ground. The input capacitors, output capacitors, and FET grounds for each VRx converter and controller must be connected to the ground plane for the respective VRx rail. Because the PGNDs for each rail do not connect to each other or AGND, using the PGNDVRx pins for the input and output capacitors for each VRx rail is required. This ground plane should connect in one place to the common ground close to the input and output capacitor ground pads. Figure 7-12 shows a visual representation of the converter layout scheme.
- The input and output capacitors of the internal reference regulators must be close to the device pins.
- Route the FBVRxP and FBVRxN signals as a differential pair.

7.2.4.1.3 Controller Layout

The routing of the controllers is critical to the performance of the power supply. To reduce the risk of the controller effecting other sensitive circuits on the board, TI recommends placing all of the controller components on the same layer as the PMIC. In addition to component placement, the DRV, SW, and PGND signals should be routed on the same layer or as few of layers possible. TI recommends placing the FETs as close as possible to the PMIC, however; placing the input capacitors within a minimal distance from the VIN and PGND pads of the FETs is imperative. The feedback signals should be routed differentially to the furthest output capacitor, which should be placed close to the load. Do not route the feedback or any sensitive analog signals under the inductor, next to the SW node, or between C_{IN} and the FETs because of the high frequency switching from the edges.

If the FETs of the controller are placed far away from the PMIC, the layout of the DRV, SW, and PGND signals becomes extremely critical. The loop inductance of the traces must be minimized as much as possible. To minimize these traces, pair the DRVH and SW traces together and pair the DRVL and PGND traces together. The PGND trace is best routed as a plane. To reduce the loop inductance of the DRVL trace, the DRVL trace should be routed one layer above the PGND trace. Generally, the SW, DRVL and DRVH traces should be 20 mm or larger assuming the PGND is a plane underneath the DRVL trace.



7.2.4.2 Layout Example

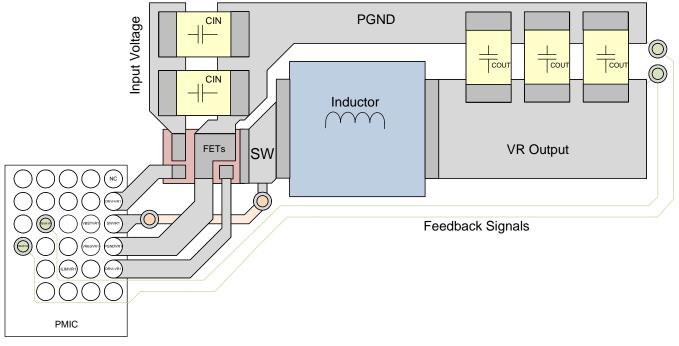


Figure 7-12. Controller Layout Diagram

7.2.4.3 Thermal Considerations

Implementation of integrated circuits in low-profile and fine-pitch surface-mount packages typically requires special attention to power dissipation. Many system-dependent issues such as thermal coupling, airflow, added heat sinks and convection surfaces, and the presence of other heat-generating components affect the power-dissipation limits of a given component.

Balancing thermal performance can be performed by improving the power dissipation capability of the PCB design and introducing airflow in the system.

For more information on how to use the thermal parameters in the dissipation ratings table, refer to *Thermal Characteristics of Linear and Logic Packages Using JEDEC PCB Designs* and the *Semiconductor and IC Package Thermal Metrics*.

7.3 Power Supply Recommendations

Any power supply capable of delivering the required input power is acceptable provided that the source is within the recommended operating conditions for the VIN and VINLDO3 pins. The input voltage for the VR2 converter must always be 3.3 V. The input voltage of the controllers can vary from the VIN and VINLDO3 voltage. Ensure that the VINPP input is connected to the VIN pin or floated but is not grounded.

7.4 Do's and Don'ts

- Always float or connect the VINPP pin to the same voltage as the VIN pin. Never ground the VINPP pin.
- Connect the enable to ground and float the output if a voltage regulator is not used.

8 Device and Documentation Support

8.1 Device Support

8.1.1 Third-Party Products Disclaimer

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8.1.2 Development Support

For frequently asked questions (FAQs) about the TPS650932 device, refer to the TPS65083x FAQs (http://e2e.ti.com/support/power_management/pmu/w/design_notes/2898.tps65083x-faqs)

8.2 Documentation Support

8.2.1 Related Documentation

For related documentation refer to:

- Texas Instruments, CSD87330Q3D Synchronous Buck NexFET™ Power Block data sheet
- Texas Instruments, CSD87381P Synchronous Buck NexFET™ Power Block II data sheet
- Texas Instruments, Thermal Characteristics of Linear and Logic Packages Using JEDEC PCB Designs application report
- Texas Instruments, Semiconductor and IC Package Thermal Metrics application report

8.3 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. In the upper right corner, click on *Alert me* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

8.4 Community Resources

The following links connect to TI community resources. Linked contents are provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

TI E2E[™] Online Community The TI engineer-to-engineer (E2E) community was created to foster collaboration among engineers. At e2e.ti.com, you can ask questions, share knowledge, explore ideas and help solve problems with fellow engineers.

Design Support *TI's Design Support* Quickly find helpful E2E forums along with design support tools and contact information for technical support.

8.5 Trademarks

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8.6 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

8.7 Glossary

TI Glossary This glossary lists and explains terms, acronyms, and definitions.



9 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.



3-Aug-2017

PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package	Pins	Package	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Device Marking	Samples
	(1)		Drawing		Qty	(2)	(6)	(3)		(4/5)	
TPS650932ZAJR	PREVIEW	NFBGA	ZAJ	168	2000	Green (RoHS & no Sb/Br)	SNAGCU	Level-3-260C-168 HR	-40 to 85	TPS650932	

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

⁽²⁾ RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <= 1000ppm threshold. Antimony trioxide based flame retardants must also meet the <= 1000ppm threshold requirement.

⁽³⁾ MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

⁽⁴⁾ There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead/Ball Finish - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

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PACKAGE MATERIALS INFORMATION

P1

(mm)

12.0

w

(mm)

16.0

Pin1

Quadrant

Q1

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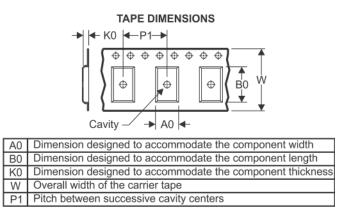
TAPE AND REEL INFORMATION



TPS650932ZAJR

NFBGA

ZAJ



QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



330.0

16.4

7.3

7.3

1.5

*All dimensions are nominal									
Device	Package Type	Package Drawing		Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	,

2000

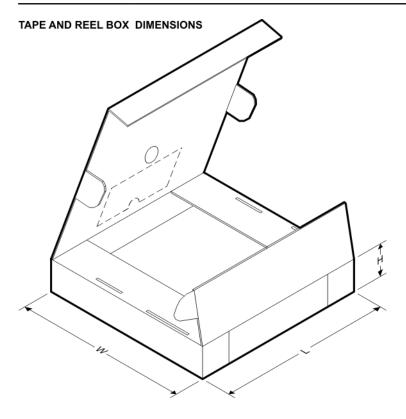
168

TEXAS INSTRUMENTS

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PACKAGE MATERIALS INFORMATION

3-Aug-2017



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TPS650932ZAJR	NFBGA	ZAJ	168	2000	336.6	336.6	31.8

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